



RIT Detector Virtual Workshop

Photon Counting with InGaAsP Single Photon Avalanche Diodes

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Mark A. Itzler

Princeton Lightwave Inc.
Cranbury, NJ 08512 USA

mitzler@princetonlightwave.com
www.princetonlightwave.com

Colleagues and Collaborators

PLI Colleagues:

Xudong Jiang
Mark Entwistle
Mark Owens
Krystyna Slomkowski
Ketan Patel
Bora Onat
Sabbir Rangwala

External Colleagues & Collaborators:

Sergio Cova.....*Politecnico di Milano*
Alberto Tosi
Franco Zappa
Massimo Ghioni

Joe Campbell.....*University of Virginia*
Archie Holmes

Bill Farr.....*Jet Propulsion Laboratory*

Mike Krainak.....*NASA/GSFC*

Gary Smith.....*MIT Lincoln Laboratories*
Alex McIntosh
Simon Verghese

Alessandro Restelli.....*NIST/Gaithersburg*
Josh Bienfang

Zhiliang Yuan.....*Toshiba/UK*

Naota Namekata.....*Nihon University*
Shuichiro Inoue

Thomas Jennewein.....*University of Waterloo*
Zhizhong Yan

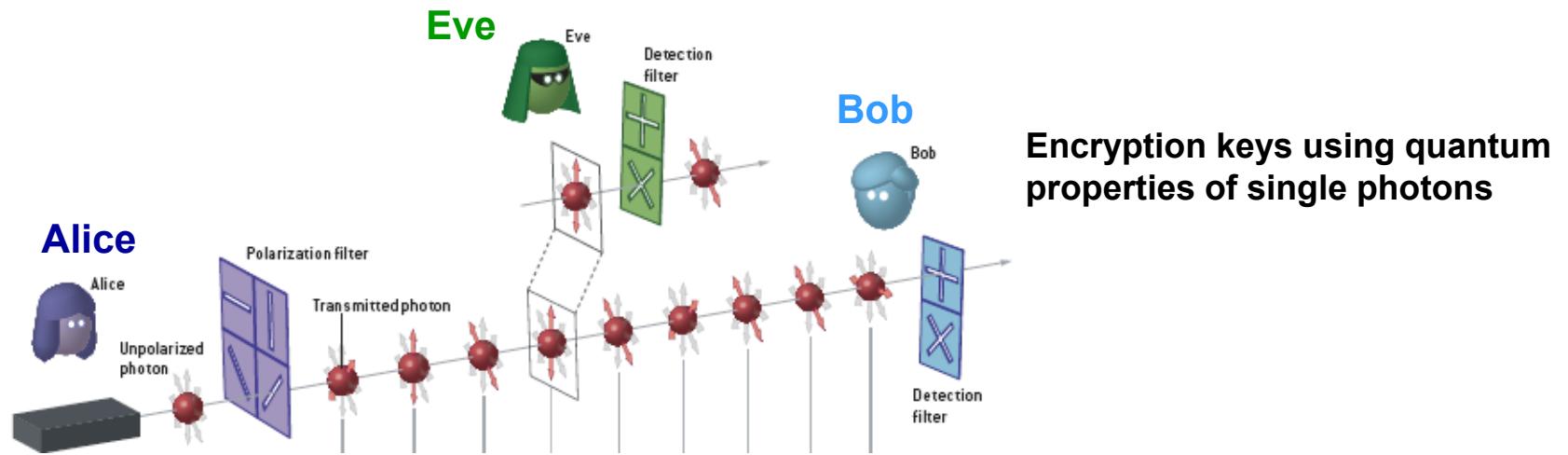
Hugo Zbinden.....*University of Geneva*
Tommaso Lunghi

Workshop Outline

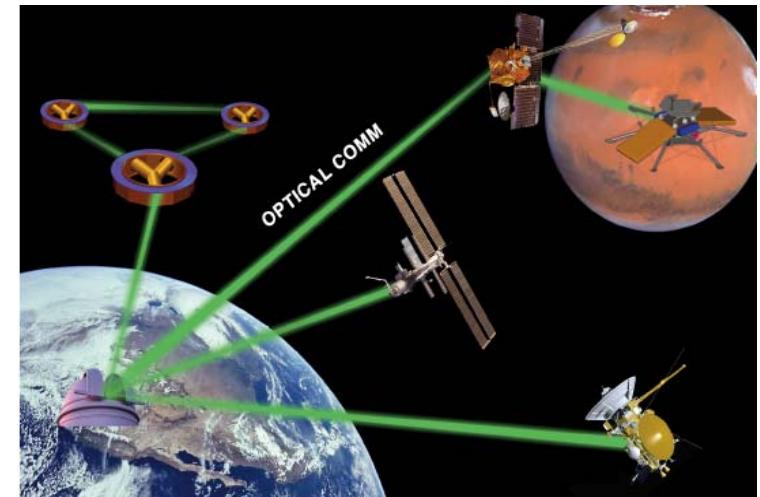
- **Applications and drivers**
- **InGaAsP single photon avalanche diode (SPAD) fundamentals**
 - ◆ SPAD device design and performance parameters
- **High-rate photon counting with InGaAsP SPADs**
 - ◆ Challenges of high-rate counting: transients and afterpulsing
 - ◆ Progress in high-rate counting techniques
- **Free-running operation with self-quenching NFADs**
 - ◆ Integration of negative feedback
 - ◆ Self-quenching avalanche dynamics
- **Scaling to large format SPAD arrays**
 - ◆ Integration for focal plane arrays and FPA performance
- **Future prospects**
 - ◆ High-rate photon counting
 - ◆ “Solid state photomultipliers” based on NFADs
 - ◆ Photon number resolution with SPADs/NFADs
 - ◆ Further scaling and micropixellated arrays

High-rate photon counting SPAD applications

- Exploiting quantum mechanical nature of photons
 - ◆ quantum information processing (e.g., quantum cryptography and computing)

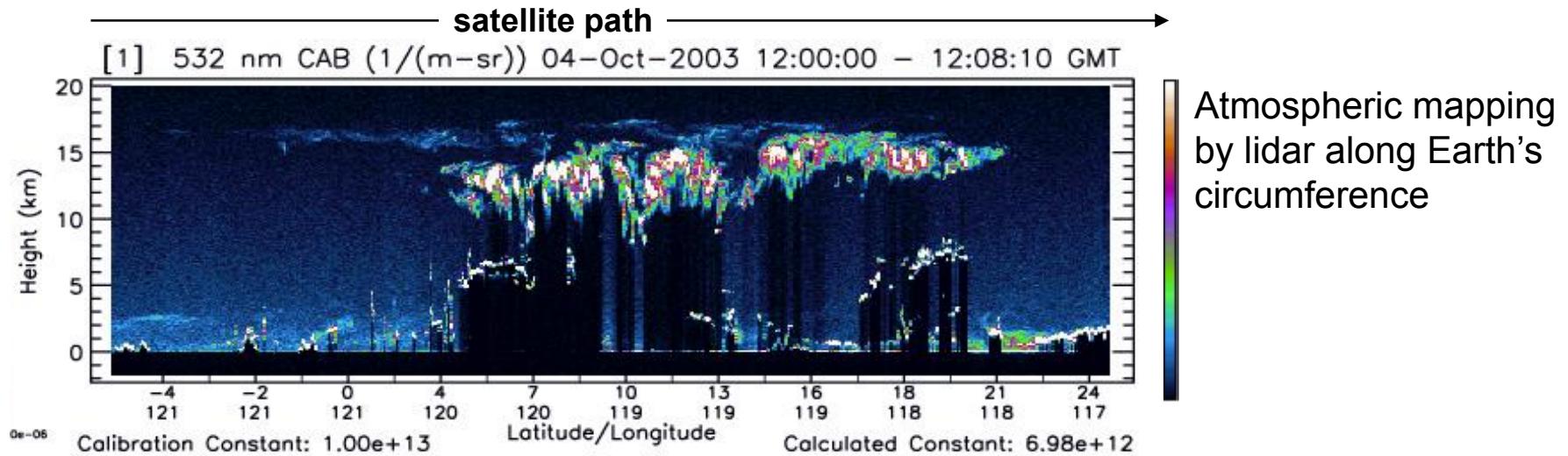


- Free-space communications and single-photon imaging
 - ◆ long-range free-space optical communications
 - ◆ single-photon imaging with high photon arrival rate



“Free-running” SPAD applications

- “**Asynchronous**” applications (no knowledge of photon arrival time)
- **LIDAR measurements for earth science**
 - ◆ Distributed reflection from soft targets (clouds, aerosols)



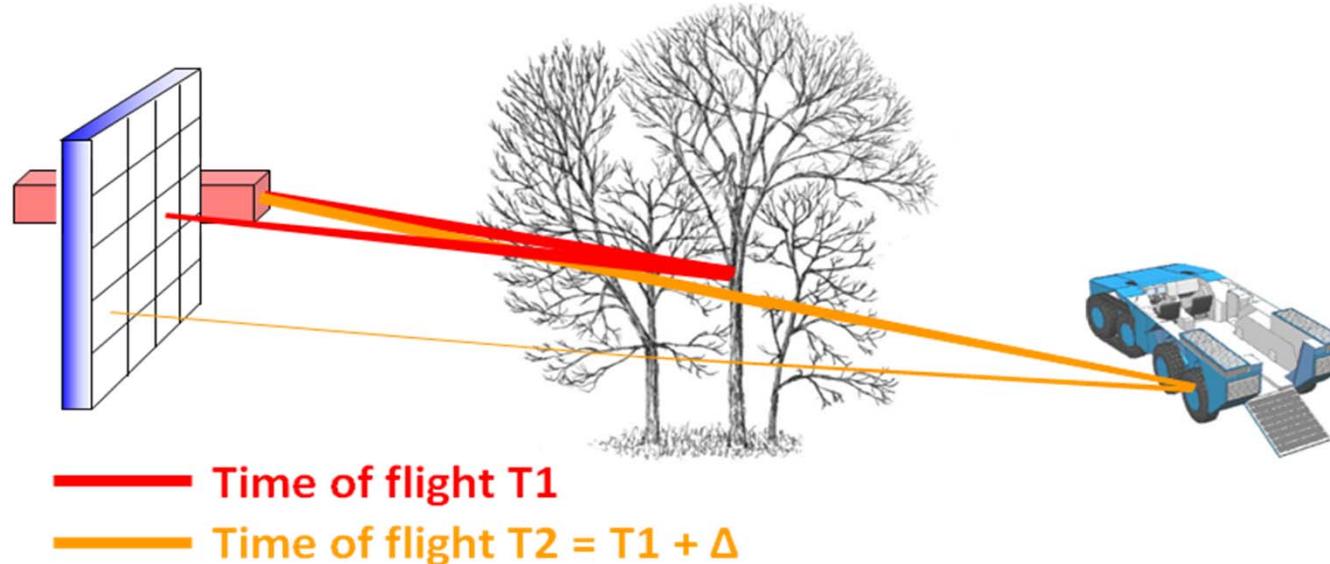
Atmospheric mapping
by lidar along Earth's
circumference

- **Flourescence measurements based on time-correlated SPC**
 - ◆ temporally random single photon emissions

Large-format arrays required for imaging

- **Photon-starved low-light-level imaging applications**
 - ◆ Astronomy and astrophysics
 - ◆ Night vision
- **3-D LADAR (laser radar) imaging**
 - ◆ Perform independent LADAR measurement at every pixel of the imager
 - ◆ Time-of-flight information provides “depth” for generating 3-D point clouds

3-D LADAR imaging concept

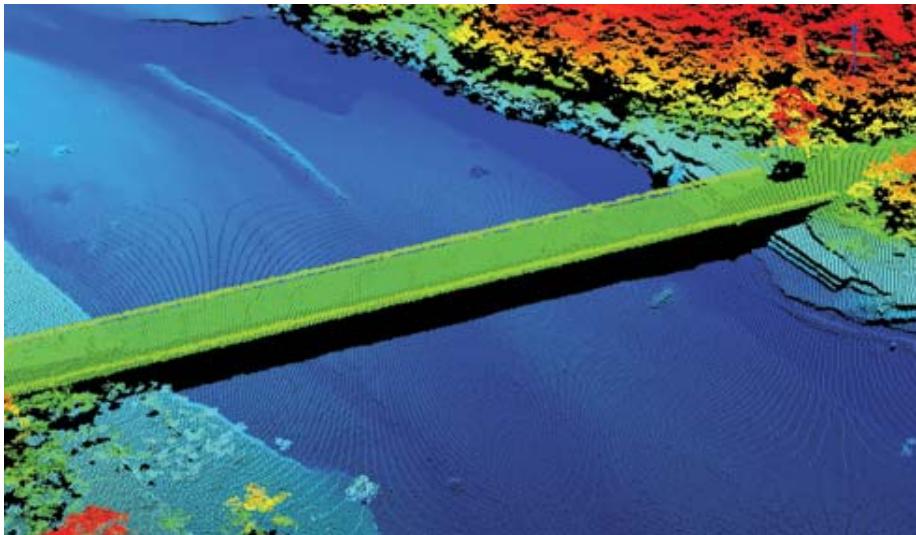


Example of 3-D LADAR mapping applications



- Pioneering development of Geiger-mode APD 3-D LADAR at MIT Lincoln Lab
- Striking demonstrations of technology capability with MIT-LL ALIRT system
 - extensive mapping after Haiti earthquake in 2010
 - pair of 32 x 128 focal plane arrays scanned to obtain imagery

Assess trafficability (roads, bridges, etc.)



Terrain mapping, damage assessment, etc.



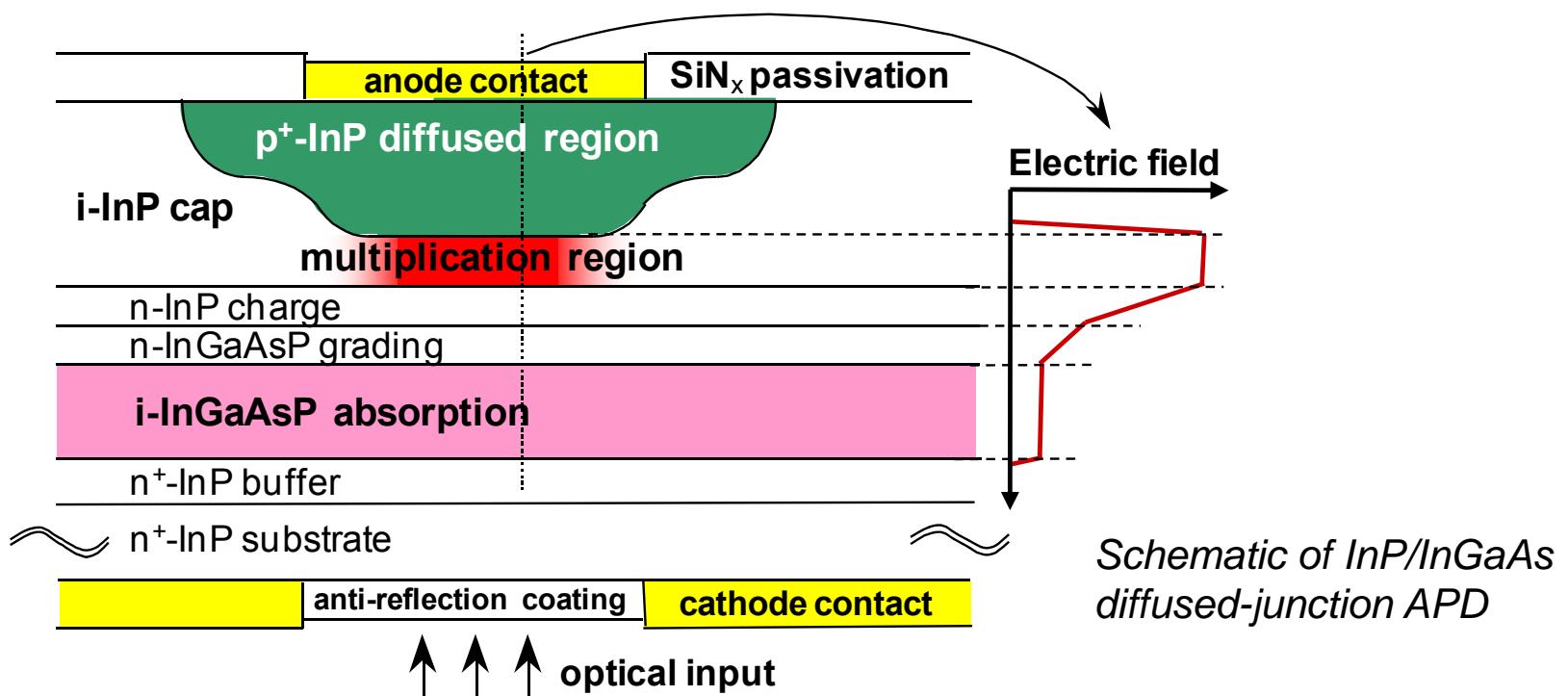
<http://www.ll.mit.edu/news/haitirelief.html>

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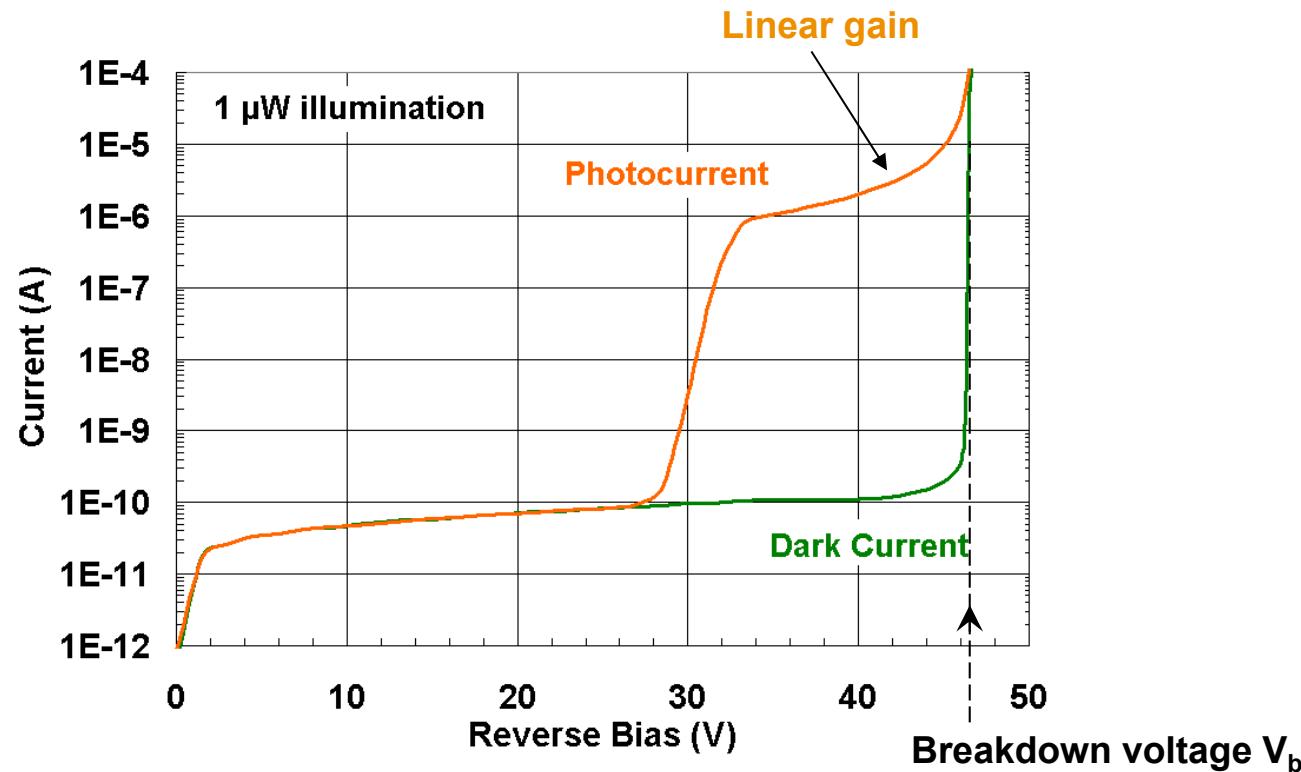
Basic APD design platform

- Low E-field in absorption region → collect carriers, but minimize noise
- High E-field in multiplication region → induce avalanche gain
- PLI has long history with planar-geometry InP/InGaAs APDs
 - Stable and reliable buried p-n junction → very high yield and uniformity
 - Widespread deployment in telecom Rx as linear mode APD (LmAPD)
 - Re-engineered for single photon detection as Geiger mode APD (GmAPD)



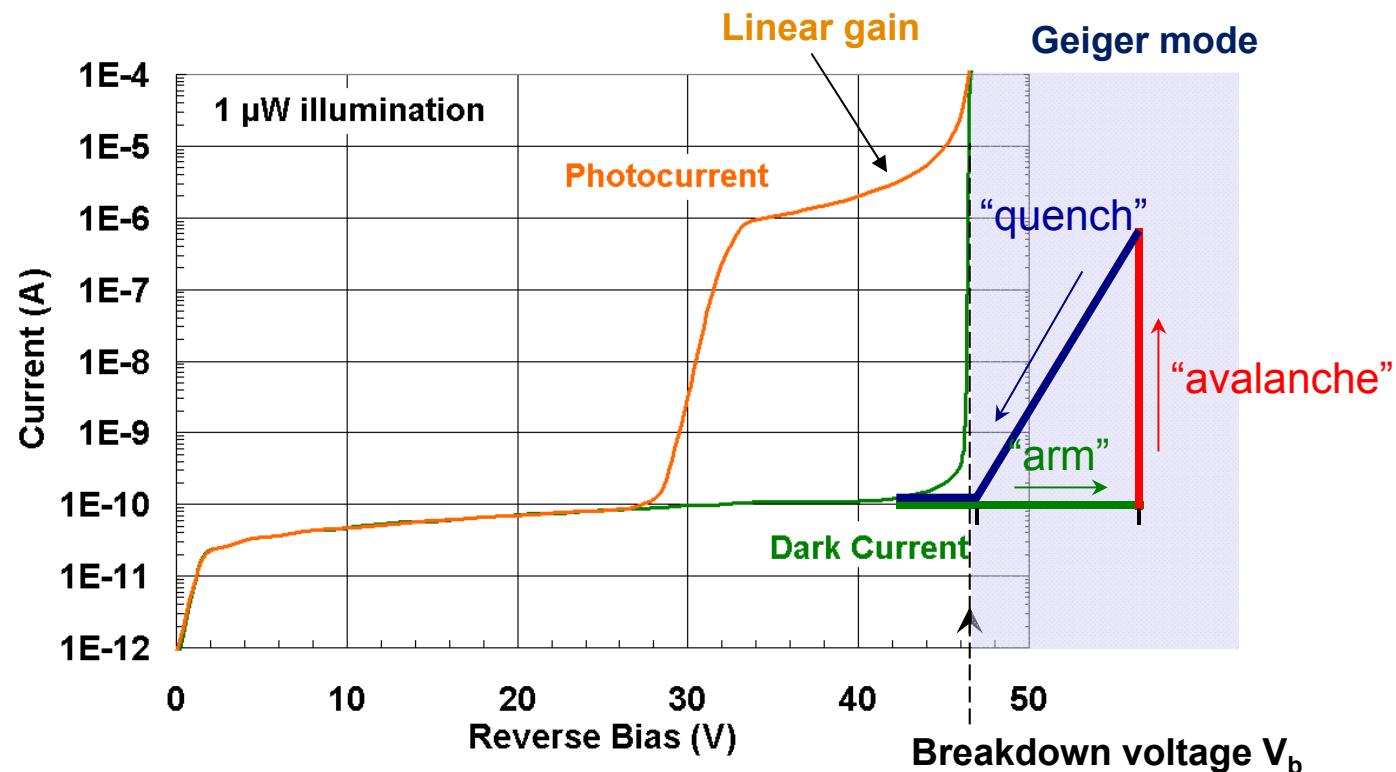
APD I-V Characteristics: Linear & Geiger modes

- Linear mode performance defines behavior below breakdown voltage V_b
 - ◆ Photocurrent below V_b is proportional to input optical power → ANALOG



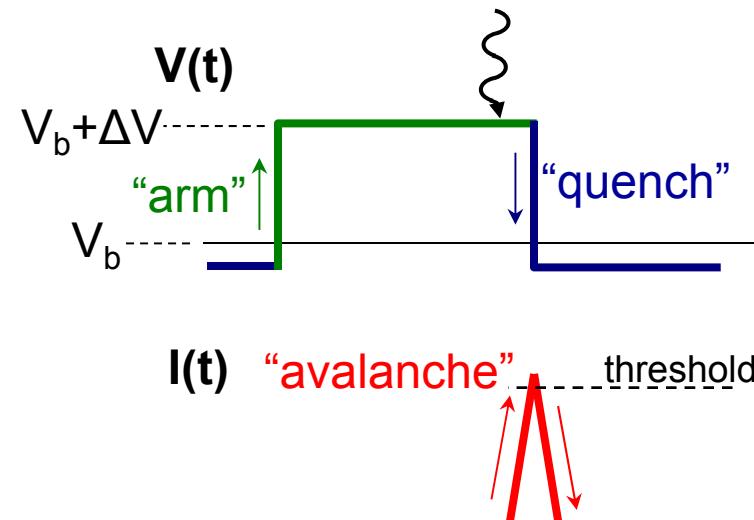
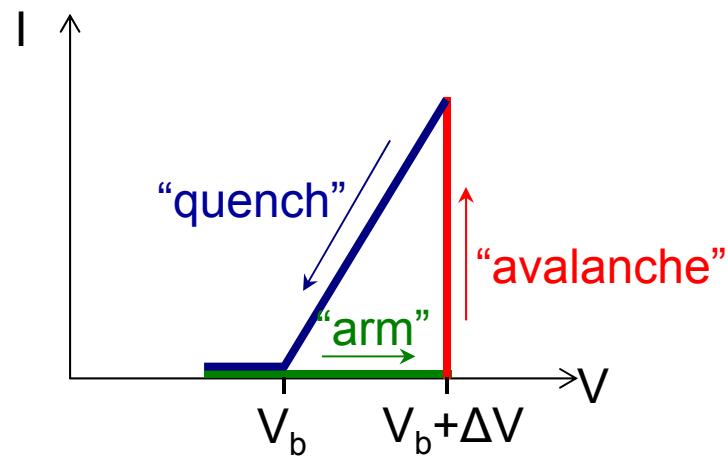
APD I-V Characteristics: Linear & Geiger modes

- **Linear mode performance defines behavior below breakdown voltage V_b**
 - ◆ Photocurrent below V_b is proportional to input optical power → ANALOG
- **Geiger-mode performance has different device functionality**
 - ◆ Operation above V_b can achieve self-sustaining avalanches → DIGITAL



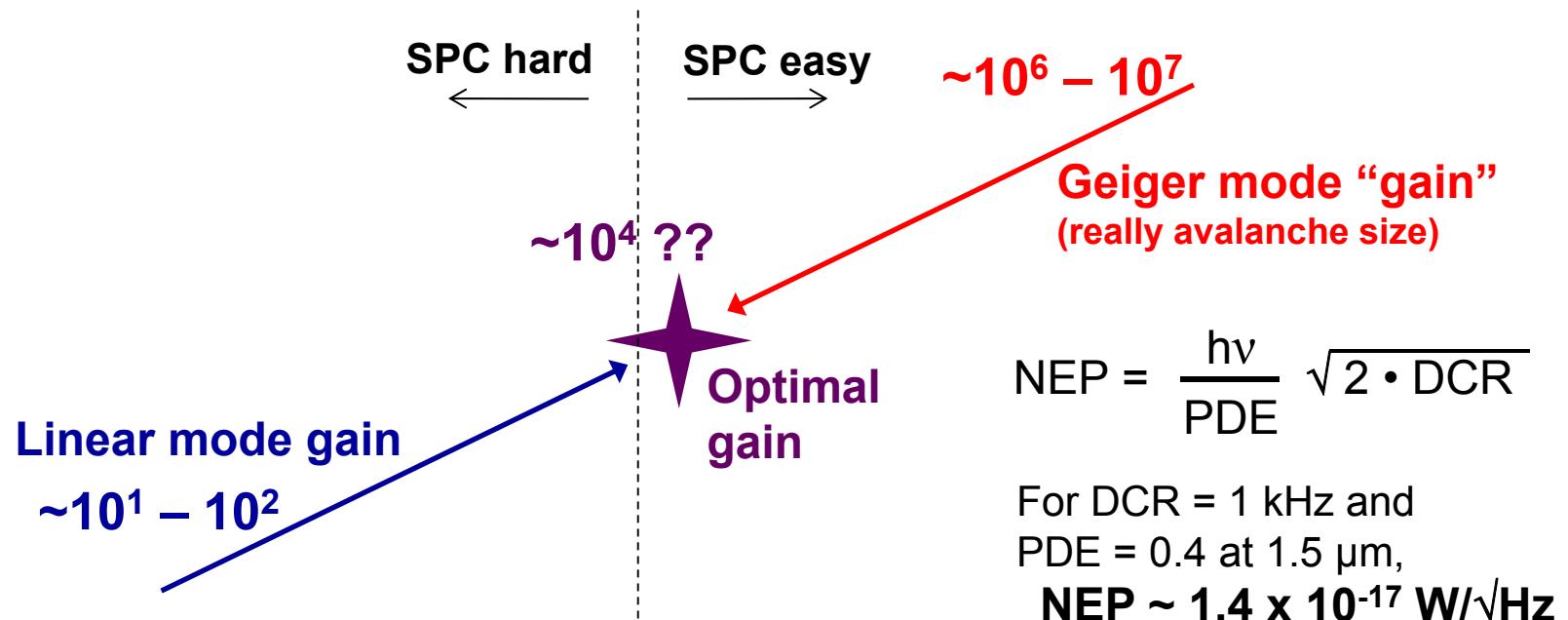
SPADs and Geiger-mode “effective gain”

- SPAD generally viewed as a “photon-activated” switch
 - ◆ Gain not strictly defined since avalanche can be self-sustaining
 - ◆ “Effective gain” dictated by combination of detector + circuit
- GmAPD “gain” \sim # of charges Q that flow per avalanche



Trends in single photon counting with APDs

- Linear mode APDs: need more gain
 - ◆ Challenge to overcome noise of circuitry (analog)
- Geiger mode APDs: need less gain
 - ◆ Large charge flow Q is easy to detect (digital detection process is noiseless)
 - ◆ Challenge is to reduce Q to minimize limitations of afterpulsing and crosstalk
 - Present implementations limited to 1 detection event per pixel per frame



Single photon detectors: with & without photons...



Ideal detector:

Always fires when a photon arrives

Never fires when a photon does not arrive

Photon Detection Efficiency (PDE):

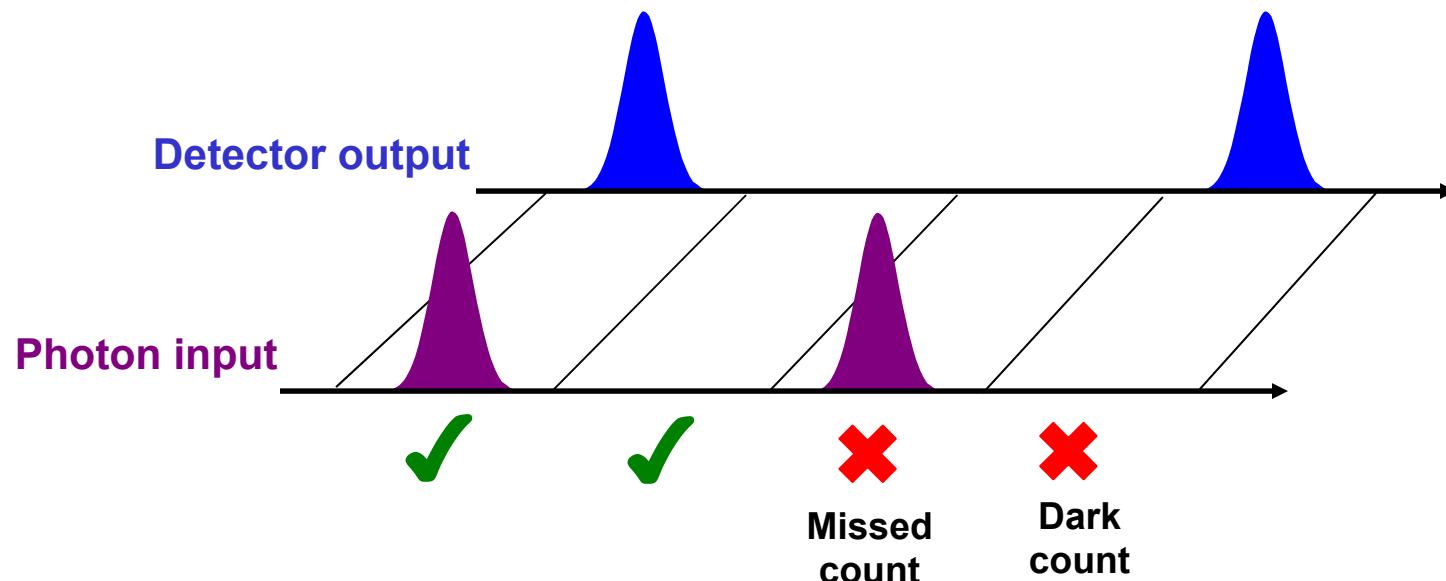
probability that photon arrival causes detector to fire

Dark Count Rate (DCR):

probability that detector fires in absence of photon arrival

$$\text{Prob(Missed count)} = 1 - \text{PDE}$$

Photon arrives	
Yes	No
Yes	✓
No	✗
Detector fires	



SPAD Performance Parameters

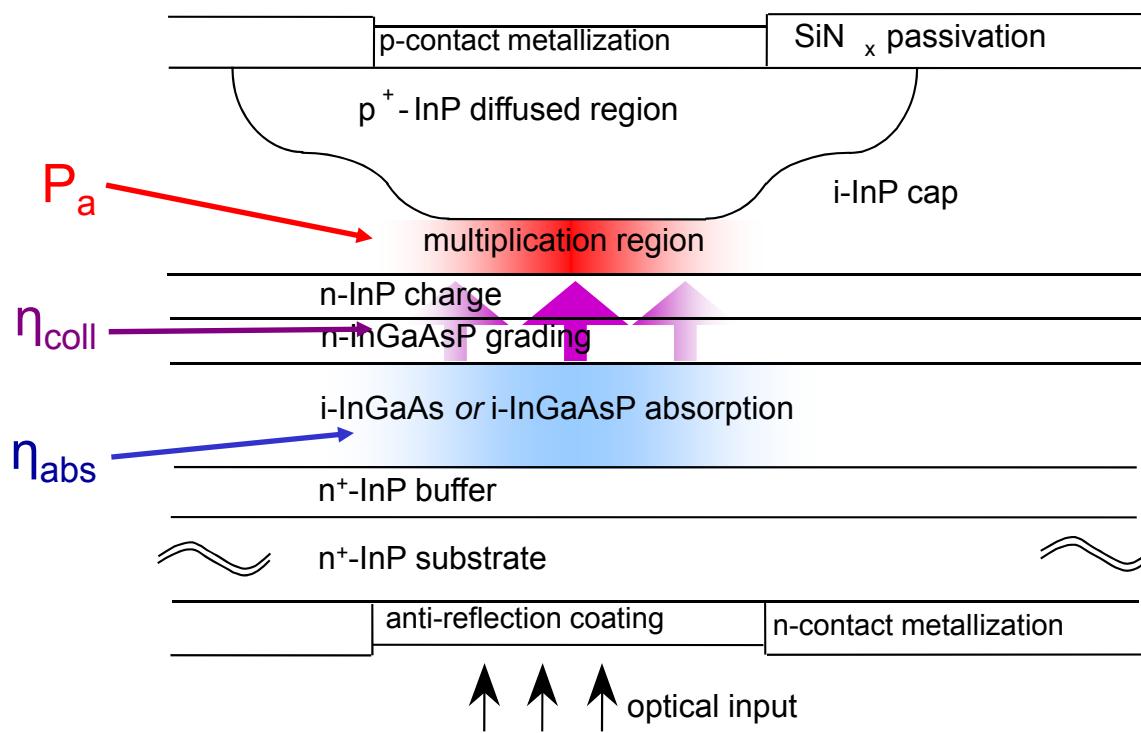
- **Photon detection efficiency (PDE)**: probability of detecting incident photon
- **Dark count rate (DCR)**: probability of “false” detection (no incident photon)
- **Timing jitter (TJ)**: randomness in detection timing
- **Afterpulsing (AP)**: increase in dark count rate following previous detection
 - ♦ Mitigated by sufficient “hold-off” time → ***BUT limits Counting Rate***

Critical performance trade-offs must be managed

- ♦ **Increase overbias:** **DE** ☺ , **TJ** ☻ , **DCR** ☹
- ♦ **Decrease temperature:** **DCR** ☺ , **AP** ☹

Photon Detection Efficiency

- Photon detection efficiency: $PDE = \eta_{abs} \times \eta_{coll} \times P_a$
 - ◆ η_{abs} : probability of photon absorption (i.e., quantum efficiency)
 - ◆ η_{coll} : probability of carrier collection (injection to multiplication region)
 - ◆ P_a : probability that collected carrier initiates detectable avalanche



For well-designed SPADs:

P_a depends on bias;
trade-off with DCR;
improves with wider
multiplier[‡]; >50%

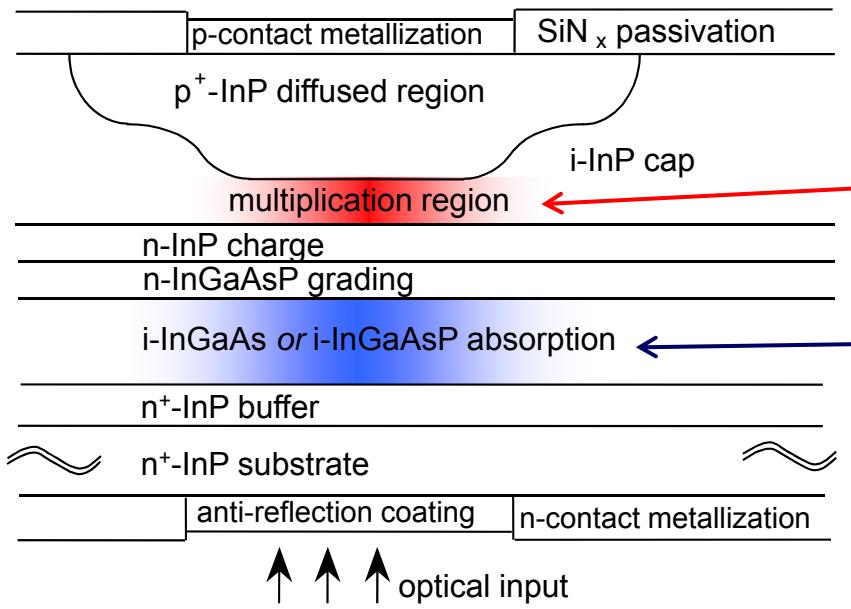
$\eta_{coll} \sim 100\%$

$\eta_{abs} \sim 70 - 90\%$

[‡] Ramirez, Hayat, et al.,
JQE 42, 137 (2006)

Dark Count Rate

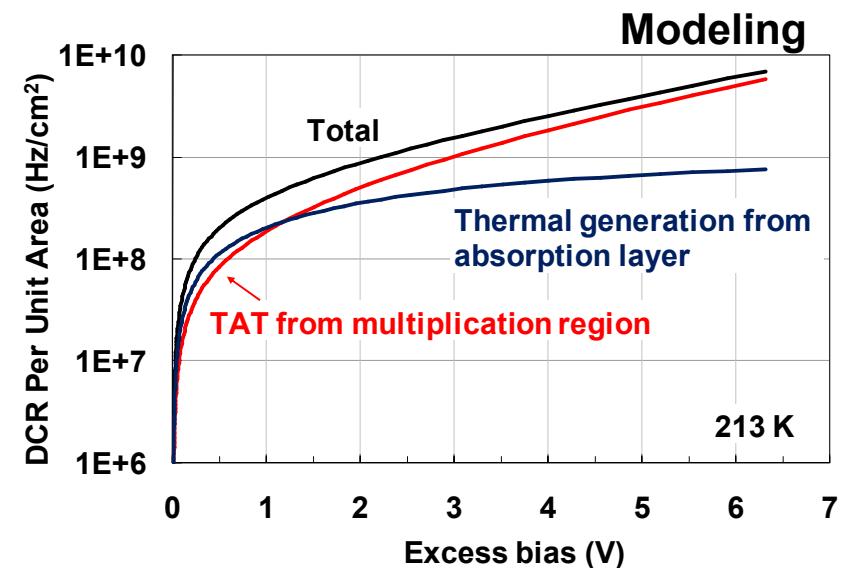
- DCR dominated by two mechanisms in SPAD structure



Trap-assisted tunneling in large-bandgap (~1.35 eV) InP multiplier

Thermal generation in small-bandgap (~0.77 ev) InGaAs absorber

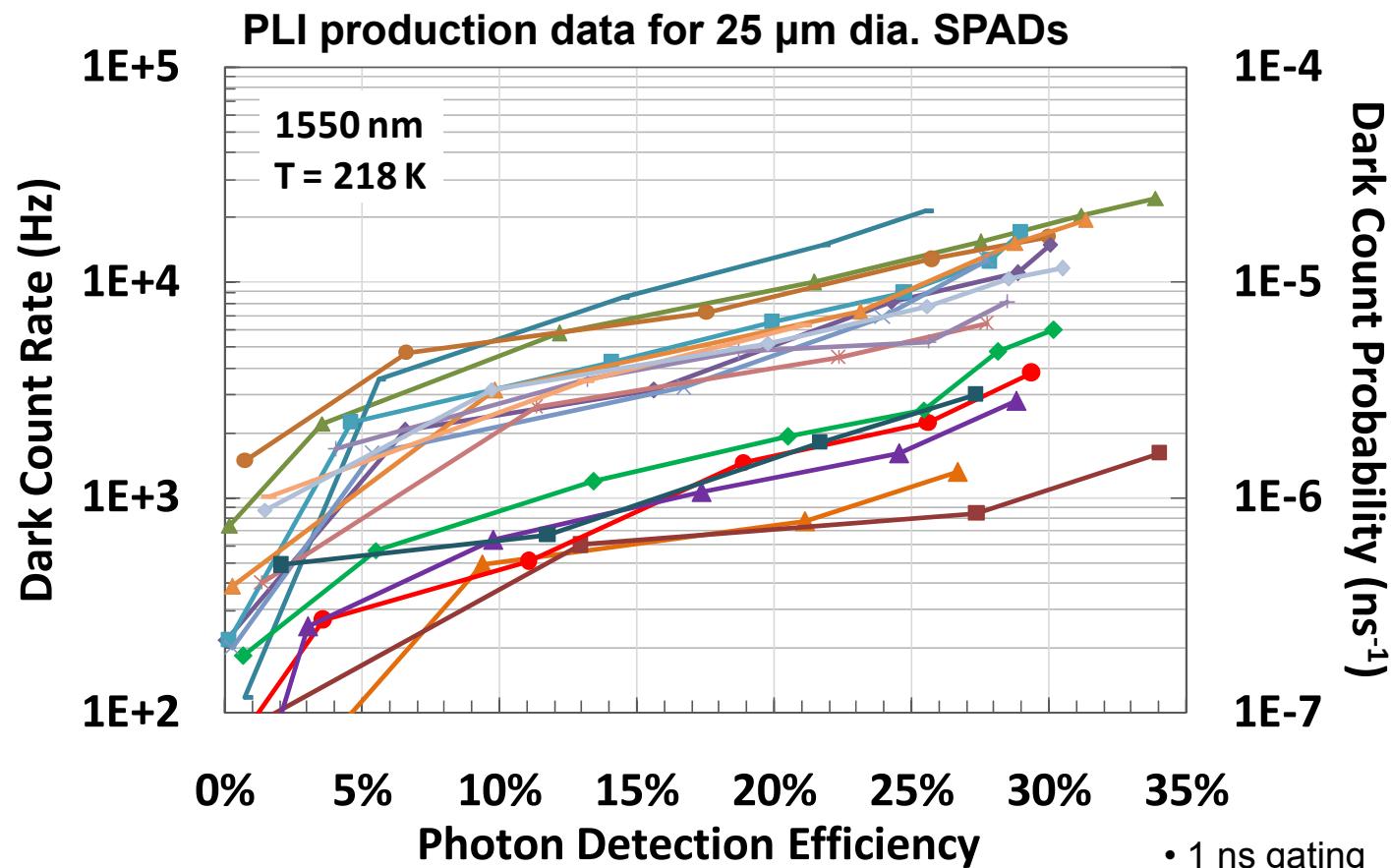
Modeling provides insight into dependence of DCR mechanisms on temperature and bias



Xiang, et al., Proc. SPIE 6771, 677127 (2007) 17

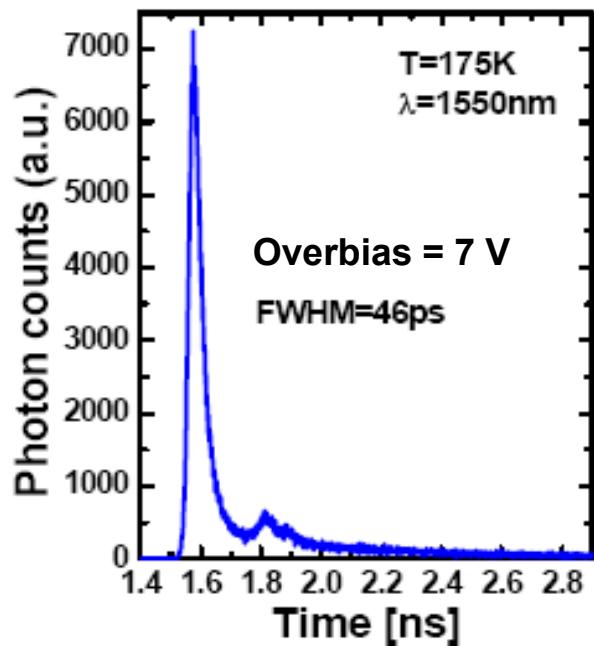
1.5 μm SPAD DCR vs. PDE Performance

- Fundamental trade-off: DCR and PDE both increase with bias
- State-of-the-art DCR: ~1 kHz at 20% PDE, ~2 kHz at 30% PDE
 - ◆ Higher PDE accessible with larger bias

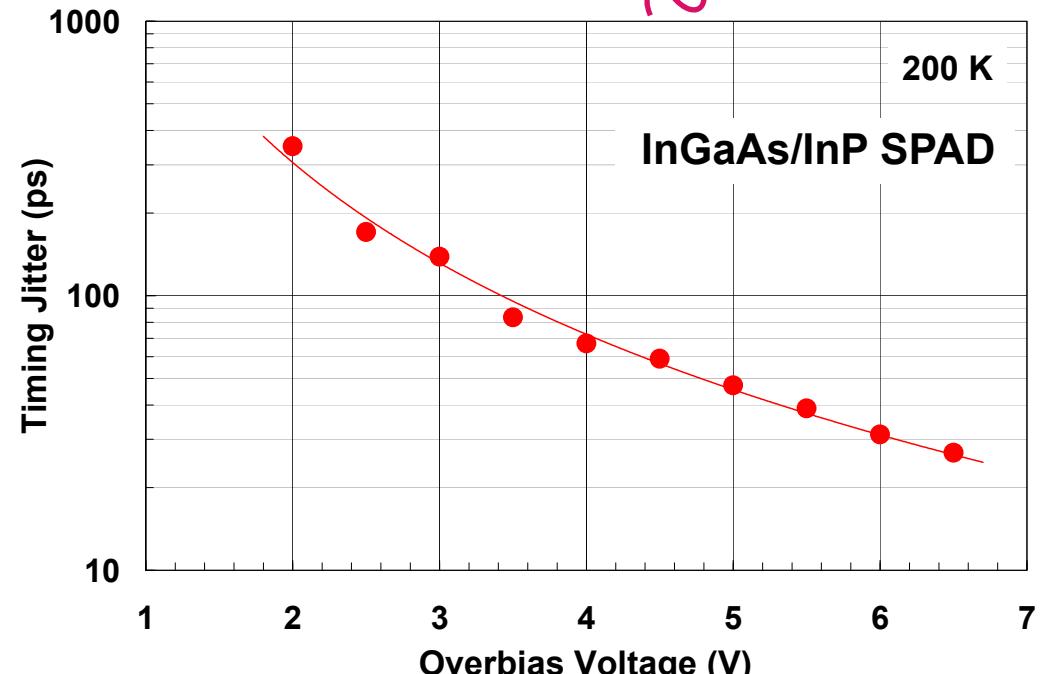


Timing Jitter

- Several factors affect detection timing
- Can be on par with other fast SPC detectors
 - ◆ Silicon SPADs ~ 50 ps
 - ◆ Superconducting SPDs ~ 30 ps
 - ◆ Requires high excess bias
→ DCR and afterpulsing trade-offs
- Jitter often circuit-limited



Zappa, Tosi, Cova, SPIE 65830E (2007)
 M. A. Itzler – RIT Detector Virtual Workshop – 12 Mar 2012



Itzler, et al., J. Modern Opt. 54, 283 (2007)

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Challenges of high-rate photon counting

Two essential challenges for high-rate counting with APDs:

- **Suppress high-frequency transients**
 - ◆ Transients are common artifact of high bandwidth signal modulation
- **Suppress afterpulsing**
 - ◆ Afterpulsing elevates dark counts due to carrier trapping/detrapping
 - ◆ Historical mitigation by long hold-off times not an option at high rates

Must also have sufficient intrinsic device bandwidth

→ not a problem for small-diameter InP/InGaAs APDs up to ~GHz-scale

Transients induced by fast signal modulation

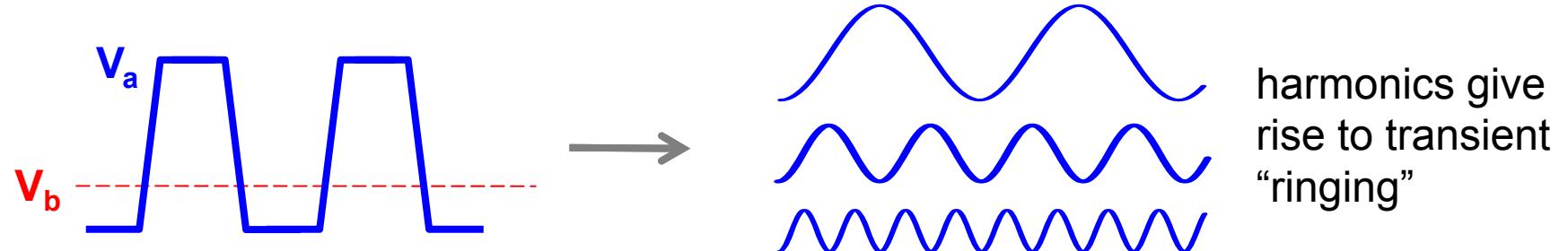


Dominant strategy: create identical transient and subtract

- **Obtain matched transient from another circuit element**
 - ◆ Matched APD detectors (NEC)
 - ◆ Dummy capacitance of appropriate size (Politecnico di Milano)
- **Obtain matched transient from same circuit element**
 - ◆ Matched RF delay lines (IBM → PLI)
 - ◆ Self-differencing by periodic delay and subtract (Toshiba/UK)

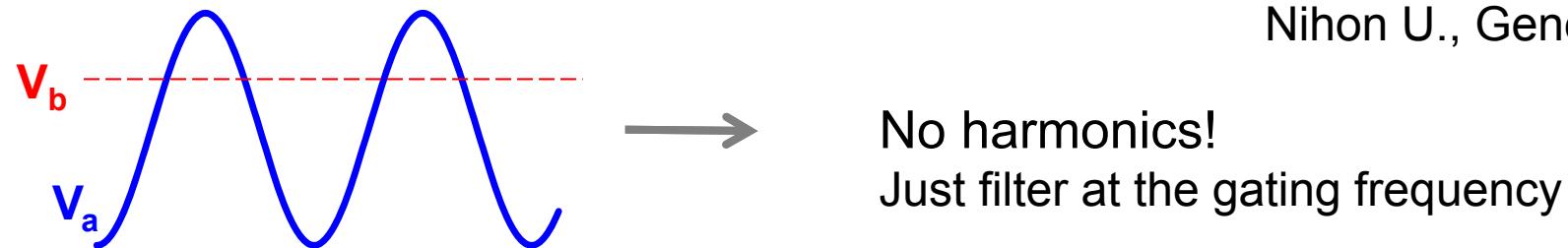
Consider range of modulation techniques

- “High-slew” gating → canonical approach



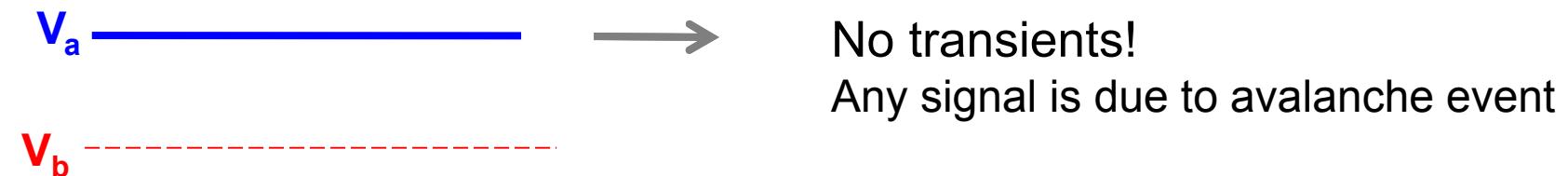
harmonics give
rise to transient
“ringing”

- Single-frequency gating → “sine-wave” gating approach



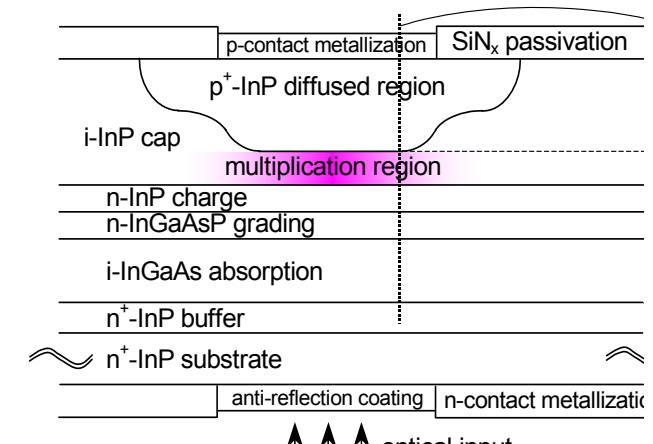
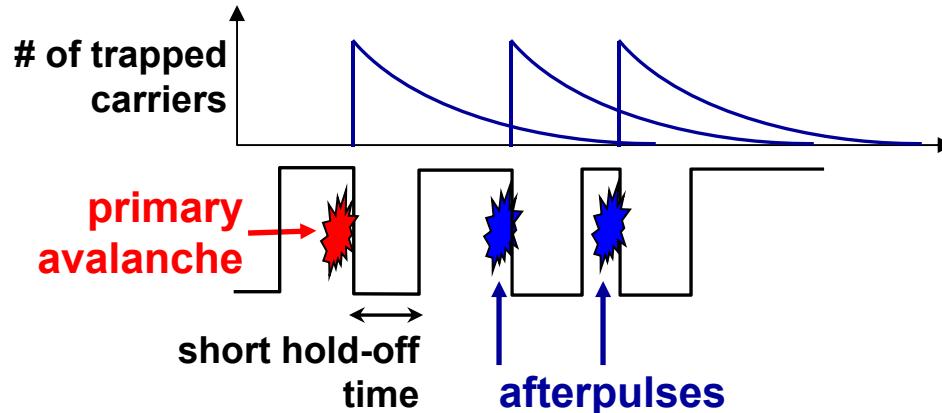
Nihon U., Geneva U.

- “DC” biasing → “self-quenching” approach

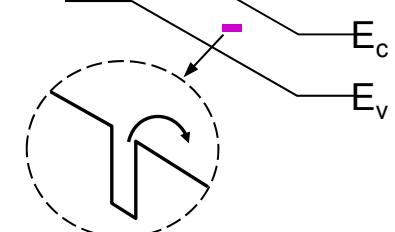


Afterpulsing: increased DCR at high rate

- Single photon detection by avalanche multiplication in SPADs
- Avalanche carriers trapped at defects in InP multiplication region
- Carrier de-trapping at later times initiates “afterpulse” avalanches

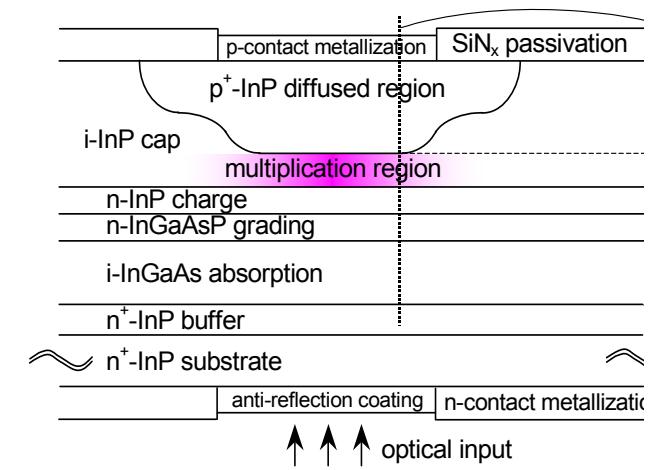
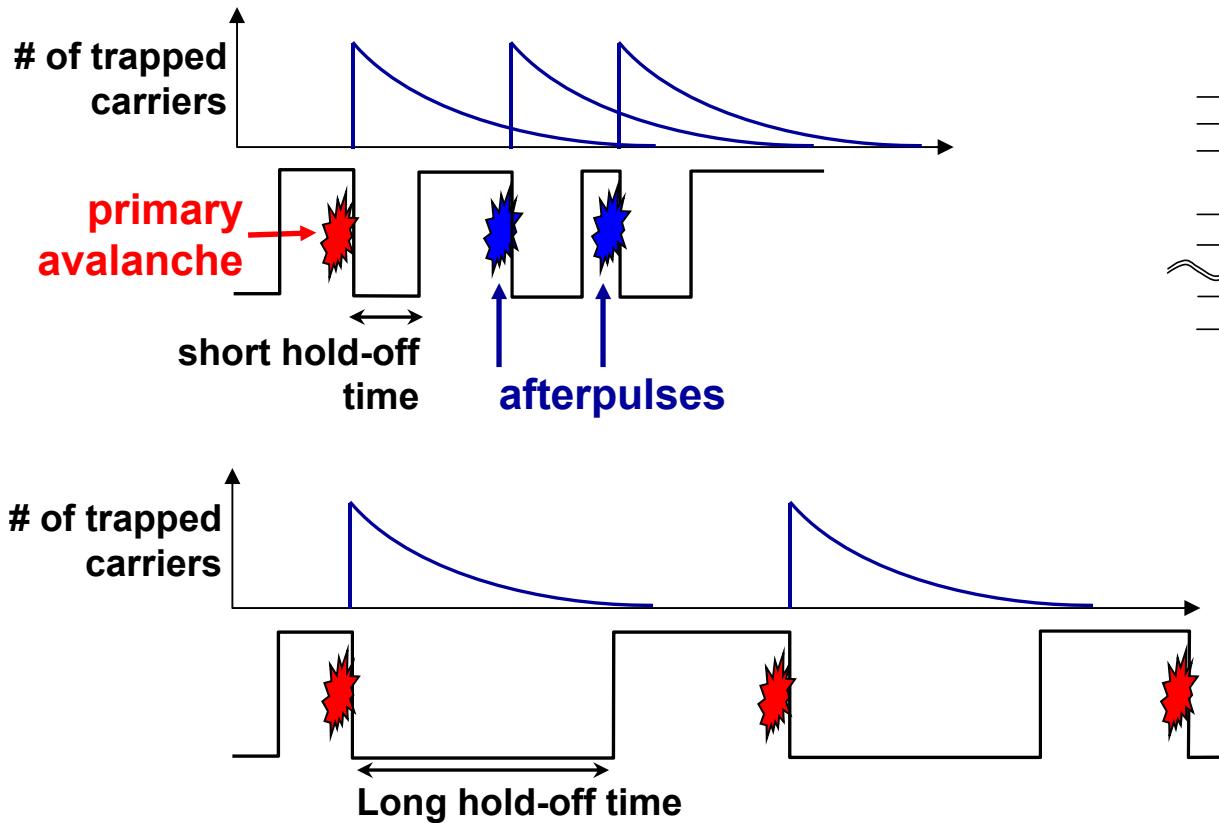


trap sites located in multiplication region

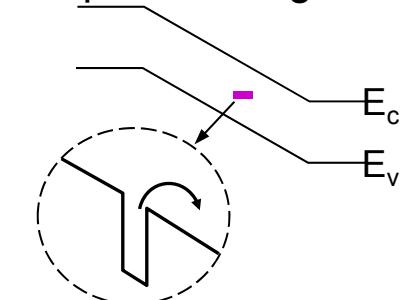


Afterpulsing: increased DCR at high rate

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- Avalanche carriers trapped at defects in InP multiplication region
- Carrier de-trapping at later times initiates “afterpulse” avalanches
- Serious drawback of afterpulsing → limitation on counting rate

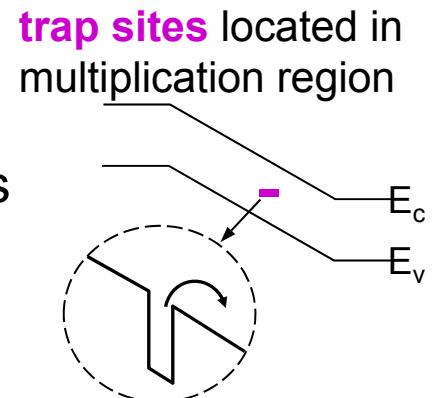


trap sites located in multiplication region



Afterpulsing suppression strategies

- **Sufficient hold-off time before re-arming**
 - low repetition rate
- **Reduce material defects that cause trapping**
 - defects not known; substantial materials challenges
- **Rapid intentional detrapping by applied stimulus**
 - optical stimuli (sub-bandgap) not successful to date
 - thermal stimuli involve thermal time constants, probably too slow
- **Reduce number of trapped carriers**
 - **reduce charge flow per avalanche**
 - requires some form of rapid quenching → **strong “negative feedback”**
 - **consistent with high-speed gating** (short gates reduce charge flow)

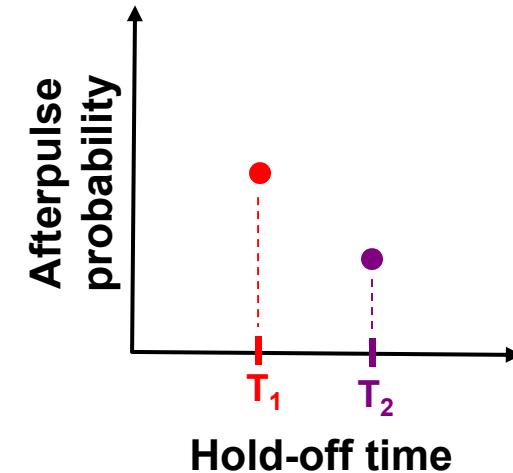
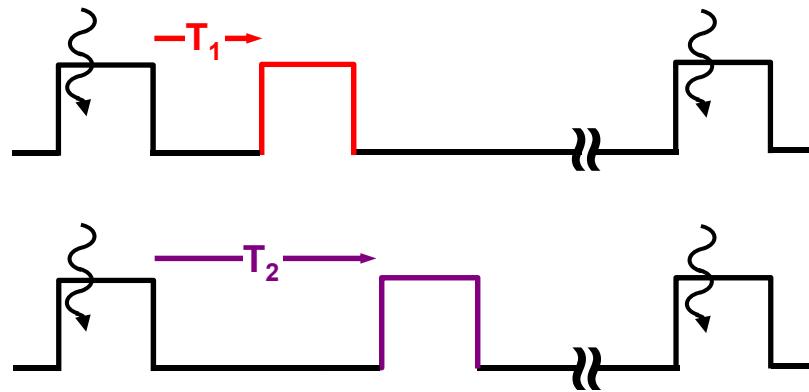


“Double-pulse” afterpulse characterization

- Use “time-correlated carrier counting” technique to measure afterpulses
- Trigger single-photon avalanches in 1st gate
- Measure probability of afterpulse in 2nd gate at T_n
- Use range of T_n to determine dependence of afterpulse probability on time following primary avalanche

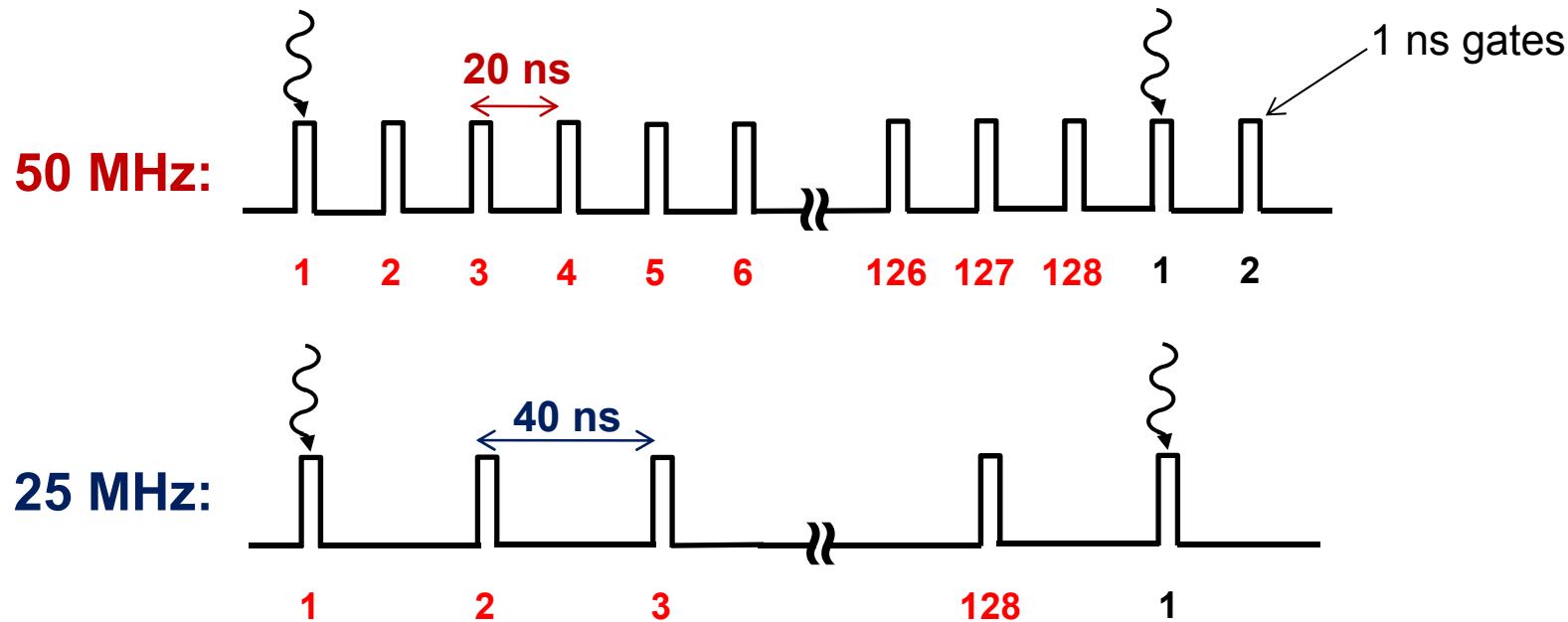
Cova, Lacaita, Ripamonti,
EDL 12, 685 (1991)

Double-pulse (“pump-probe”) method



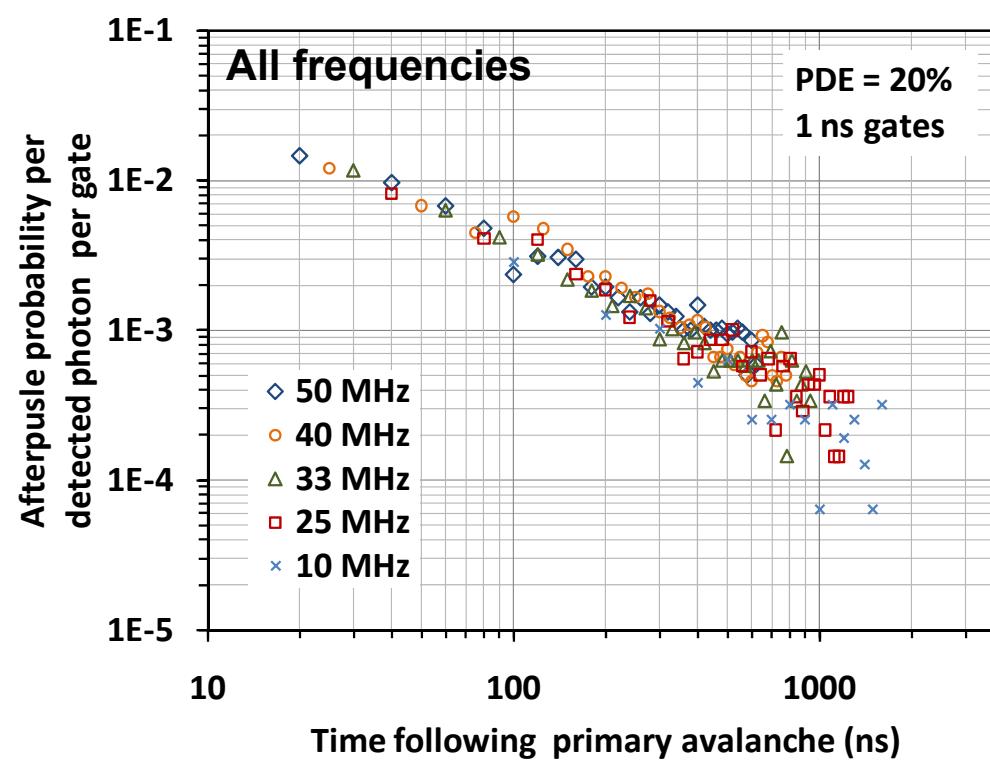
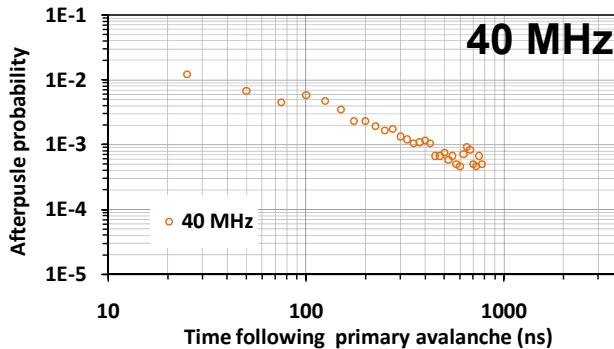
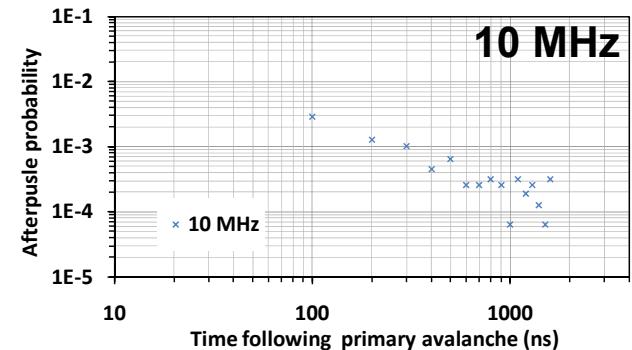
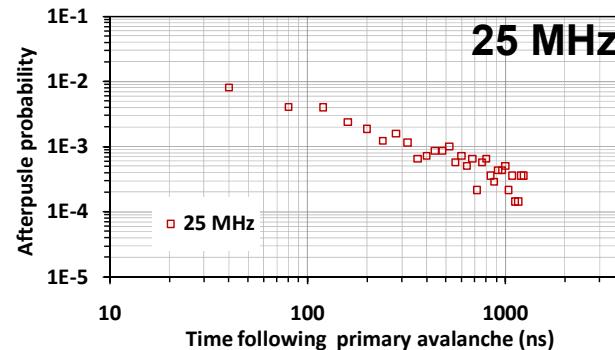
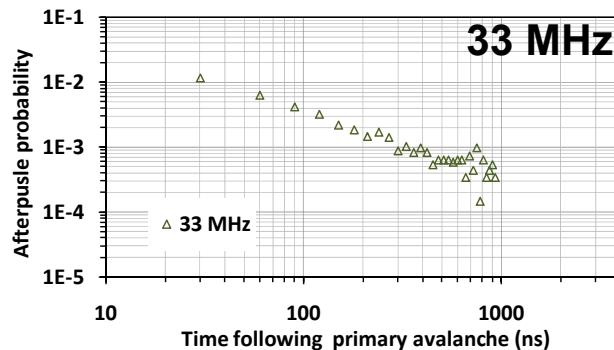
FPGA-based data acquisition

- Use FPGA circuitry to control gating and data collection
- Generalize double-pulse method to many gates
 - Capture afterpulse counts in up to 128 gates following primary avalanche
 - Temporal spacing of gates determined by gate repetition rate
- Allows capture of afterpulse count in any gate after avalanche
 - No need to step gate position as in double-pulse method



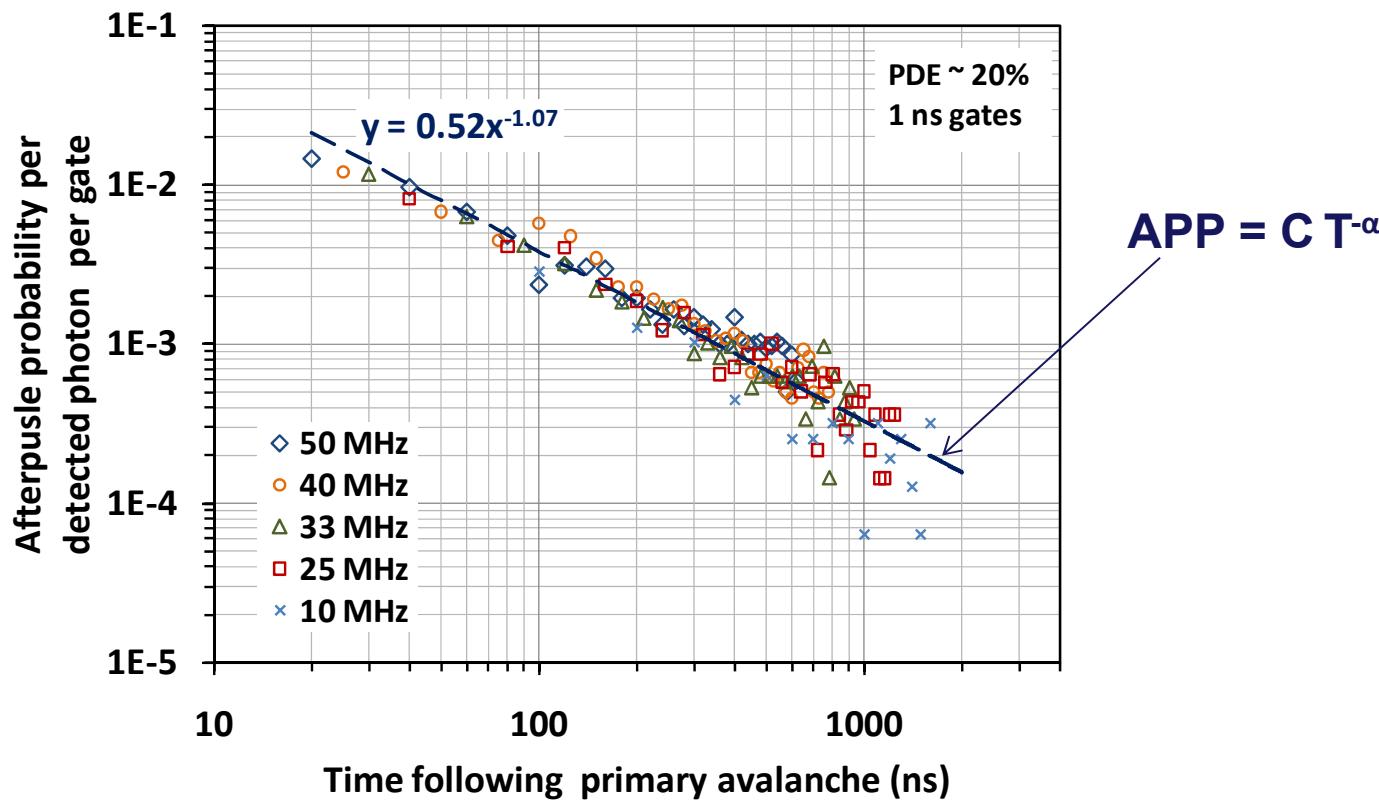
FPGA-based afterpulse measurements

- Obtain afterpulsing probability data at 5 frequencies for 32 gates



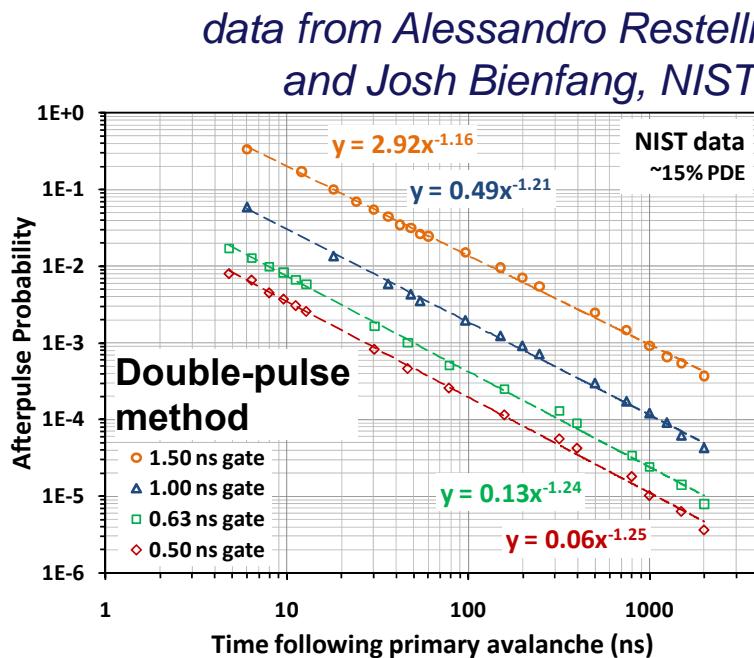
Recent re-interpretation of afterpulsing behavior

- Past fitting has assumed exponentials but is completely arbitrary
- We found good fitting for simple power law $T^{-\alpha}$ with $\alpha \approx -1$
 - Is power law behavior found for other afterpulsing measurements?
 - Is the power law functional form physically significant?

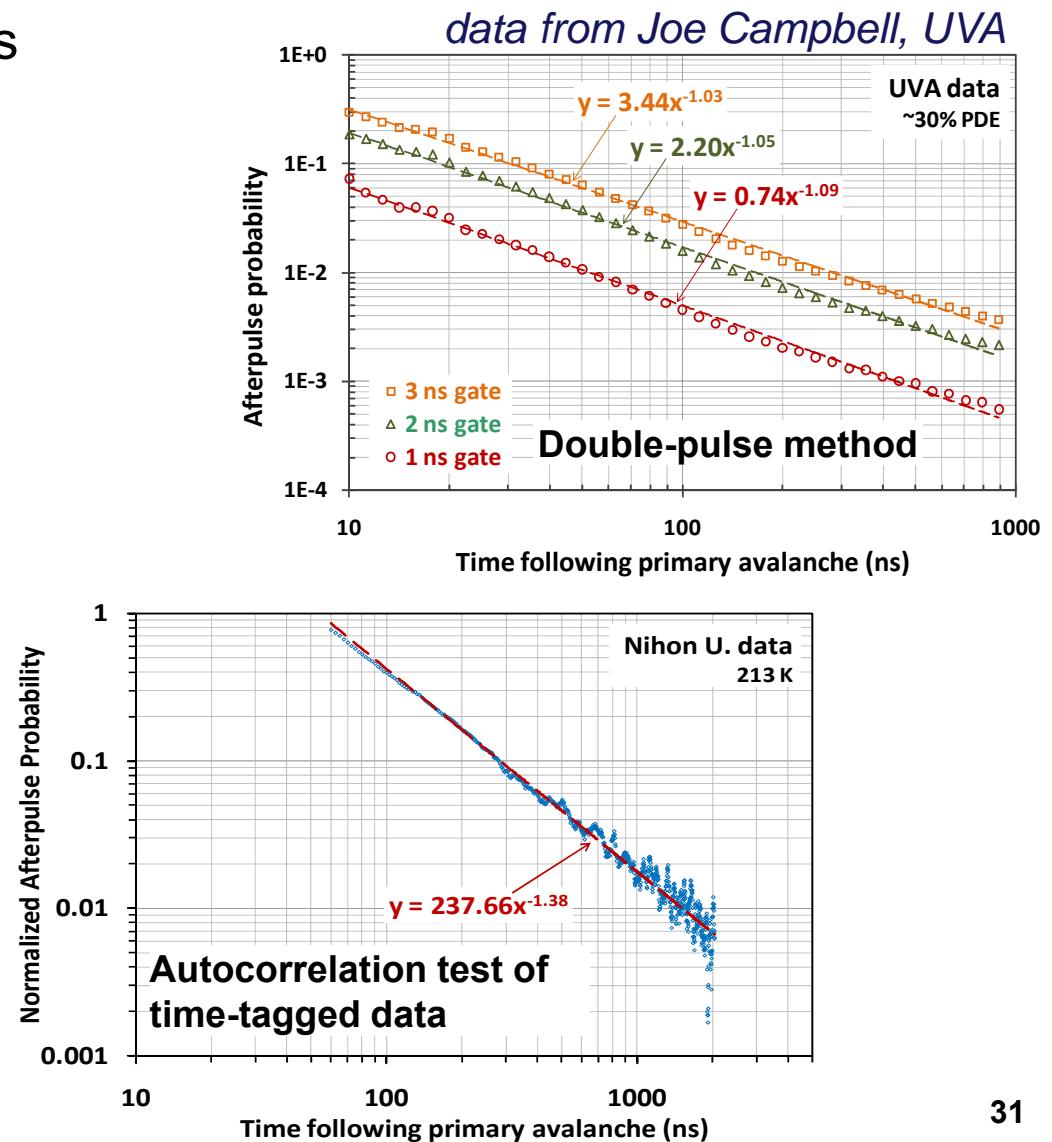


Afterpulsing data from other groups

- Good fits for power law $T^{-\alpha}$ with $\alpha \approx -1.0$ to -1.4
- All data for PLI InGaAsP SPADs

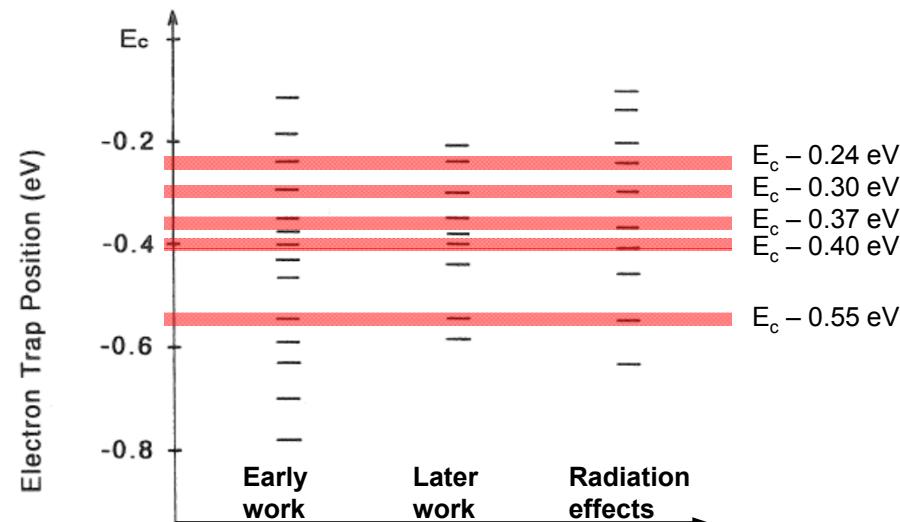
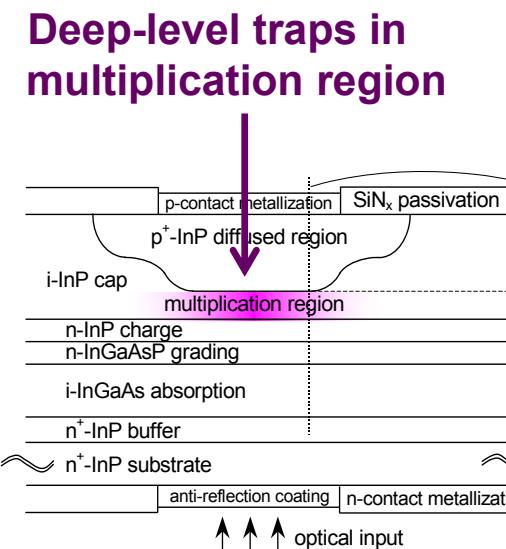


data from Naota Namekata, Nihon U.



Literature on InP trap defects

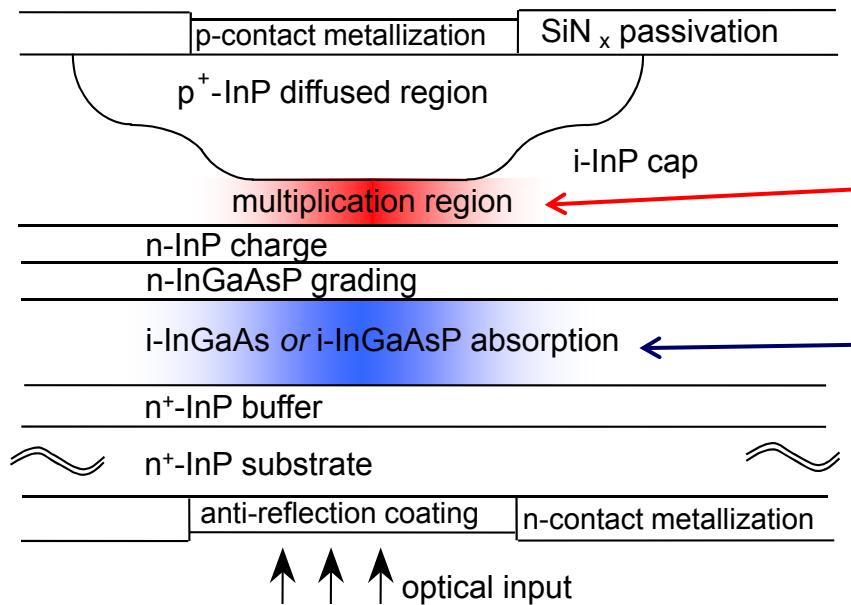
- Literature on defects in InP describes dense spectrum of levels
- Power law behavior consistent with distribution of detrapping times
 - Based on simple model of afterpulsing with distribution of defects
 - Accurate only for specific distribution with $D(\tau) \propto \tau$



W. A. Anderson and K. L. Jiao, in "Indium Phosphide and Related Materials: Processing, Technology, and Devices", A. Katz (ed.) (Artech House, Boston, 1992)

Dark counts: possible connection to afterpulsing?

- Dark counts dominated by two mechanisms in SPAD structure



Trap-assisted tunneling in large-bandgap (~1.35 eV) InP multiplier

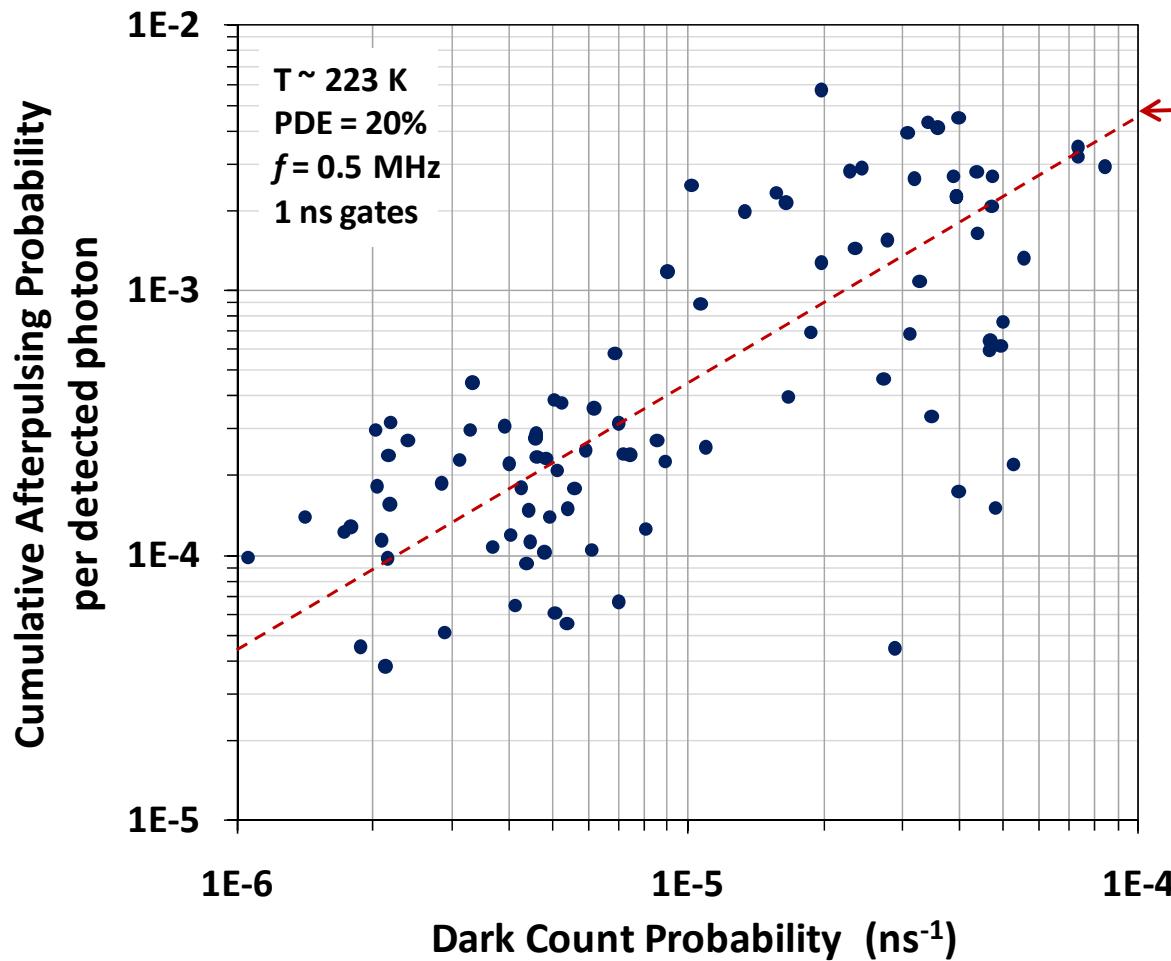
Thermal generation in small-bandgap (~0.77 ev) InGaAs absorber

- Afterpulsing is caused by carrier trapping in multiplier

→ Are TAT-induced dark counts and afterpulses due to same traps?

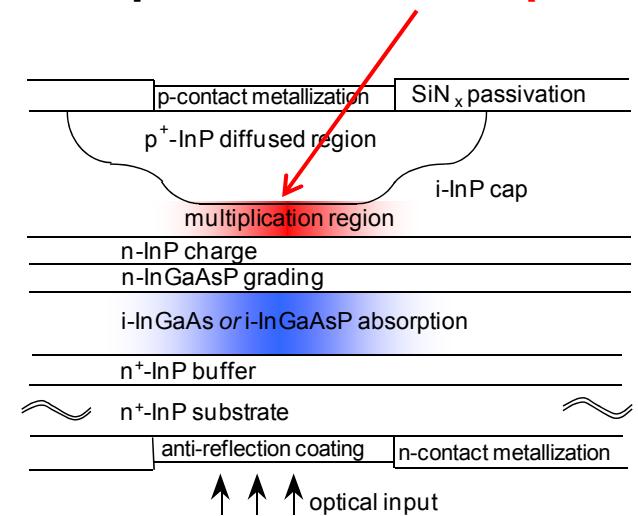
Correlation of afterpulsing with DCR

- First evidence for same traps causing TAT and afterpulsing
 - Scatter is large, so large sample size (~ 100 devices) is required
 - To have low afterpulsing, must have low TAT-induced DCP



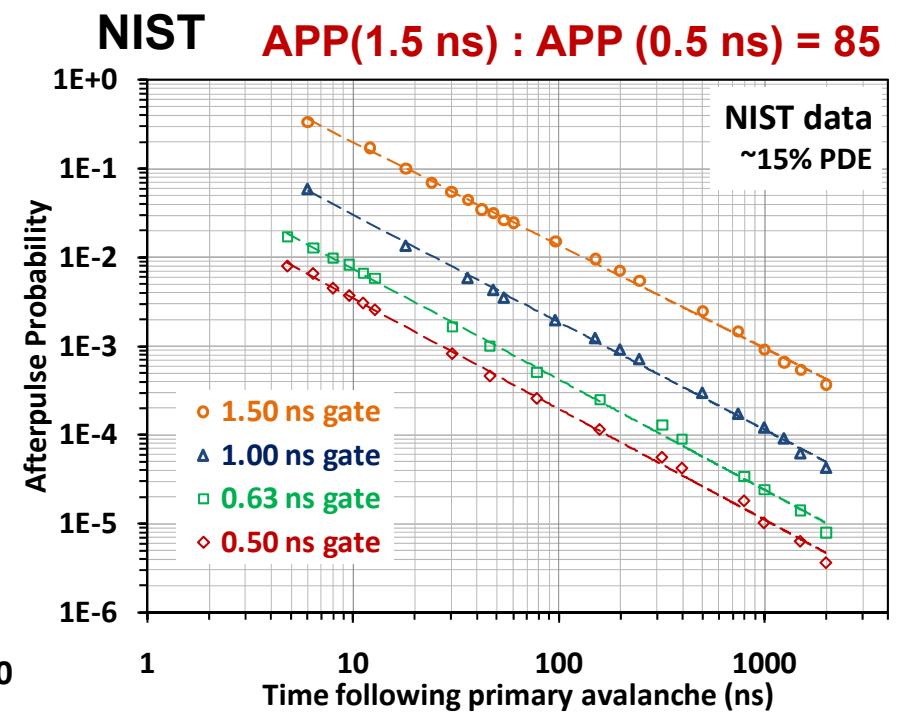
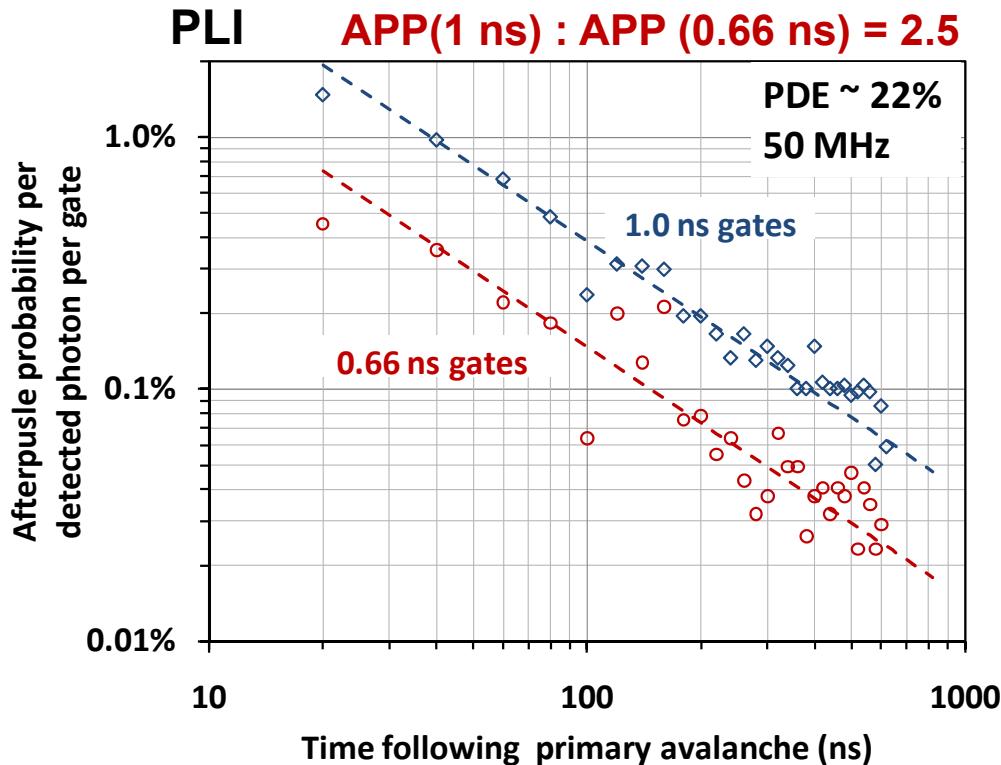
arbitrary power law fit
assuming APP \propto DCP
[Correlation ~ 0.53]

trap defects in multiplier



Afterpulsing reduction with shorter gates

- Two advantages inherent in using shorter gates
 - ◆ Shorter “window” in which afterpulse can be detected → linear in gate width
 - ◆ Charge flow reduction → net reduction in APP is super-linear in gate width
- Enables higher counting rates with “synchronous counting”



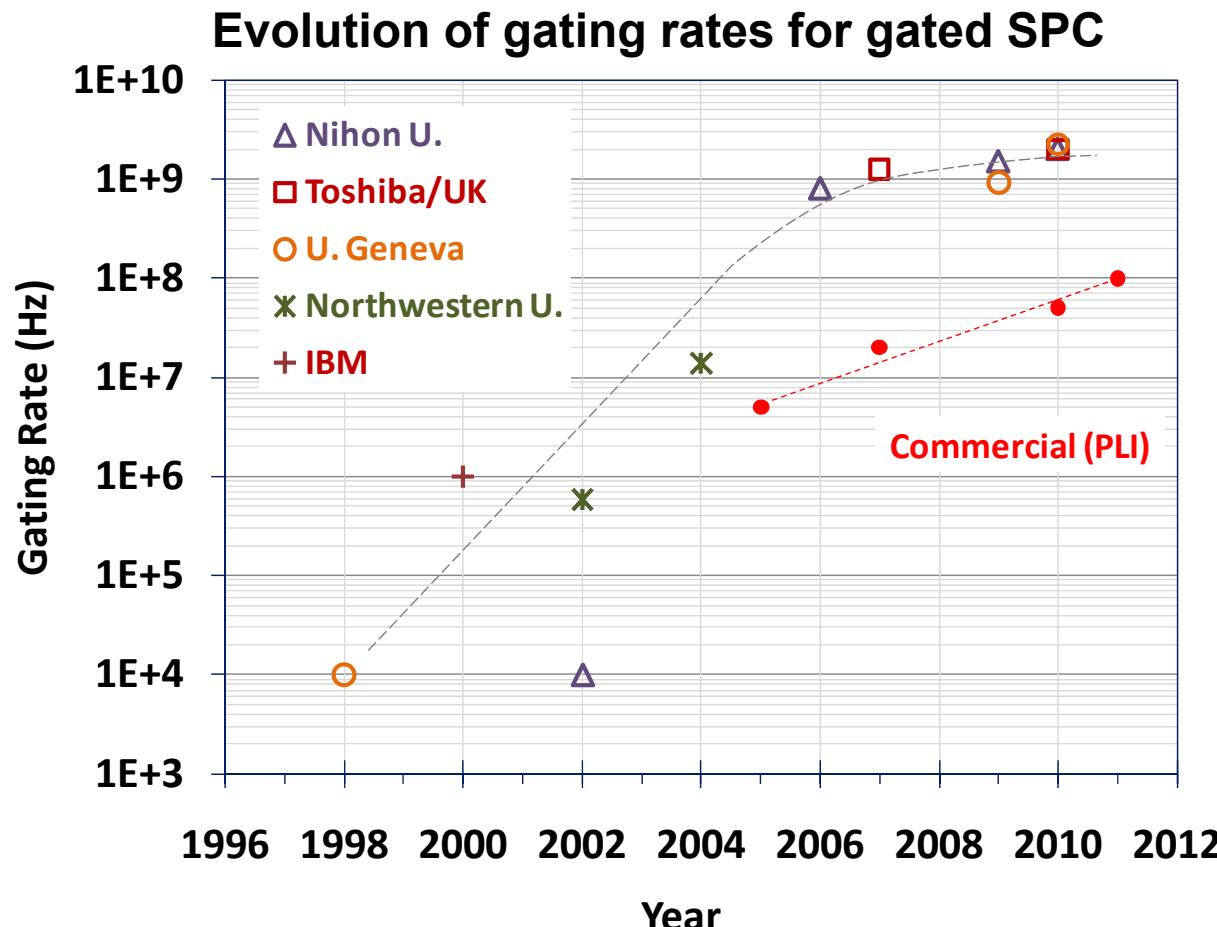
Data from A. Restelli and J. Bienfang

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Evolution of photon counting rate

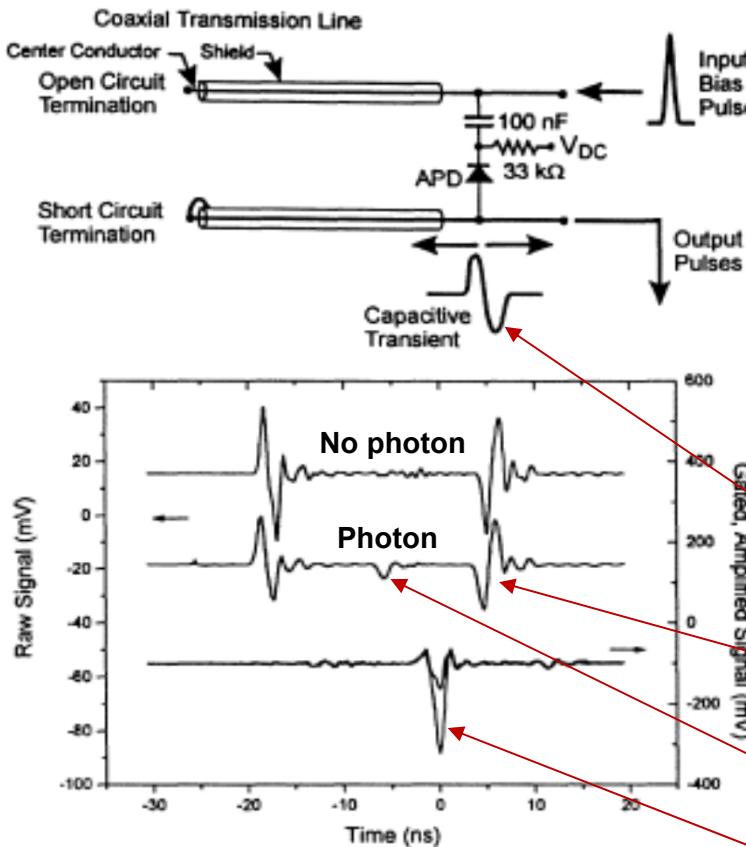
- Higher counting rate → shorter gates → reduced afterpulsing
- Gating rate is most consistent metric with sufficient data
 - ◆ Several rate metrics: System clock, periodic gating rate, actual counting rate



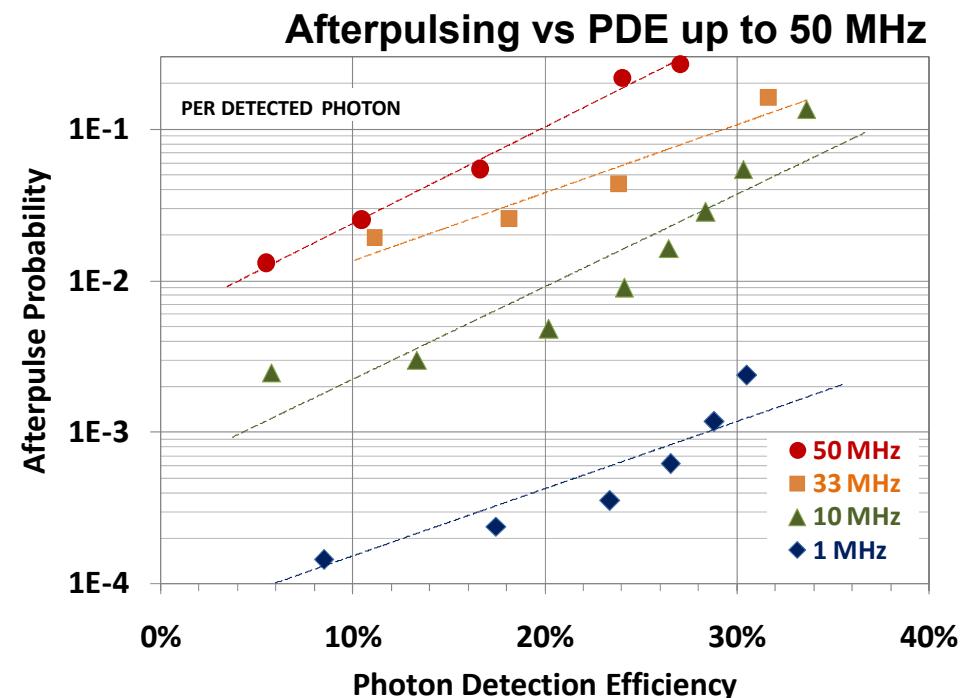
Transient cancellation with RF delay lines

- Precise cancellation for reduced threshold → detect smaller avalanches
- Afterpulsing ~ 3% at 12% PDE at 50 MHz
 - 100 MHz now available commercially

D. Bethune and W. Risk, JQE 36, 340 (2000)



M. A. Itzler – RIT Detector Virtual Workshop – 12 Mar 2012



Cancel transient response coincident
with photon arrival

Temporally gate out leading and
trailing transients

Net signal

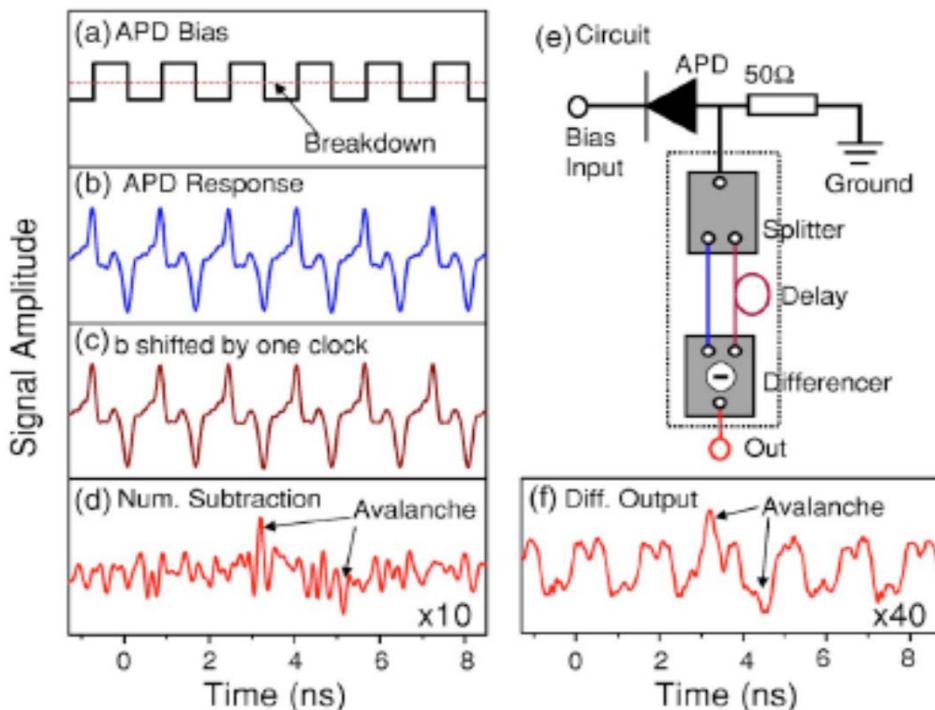
Signal after amplification and temporal gating



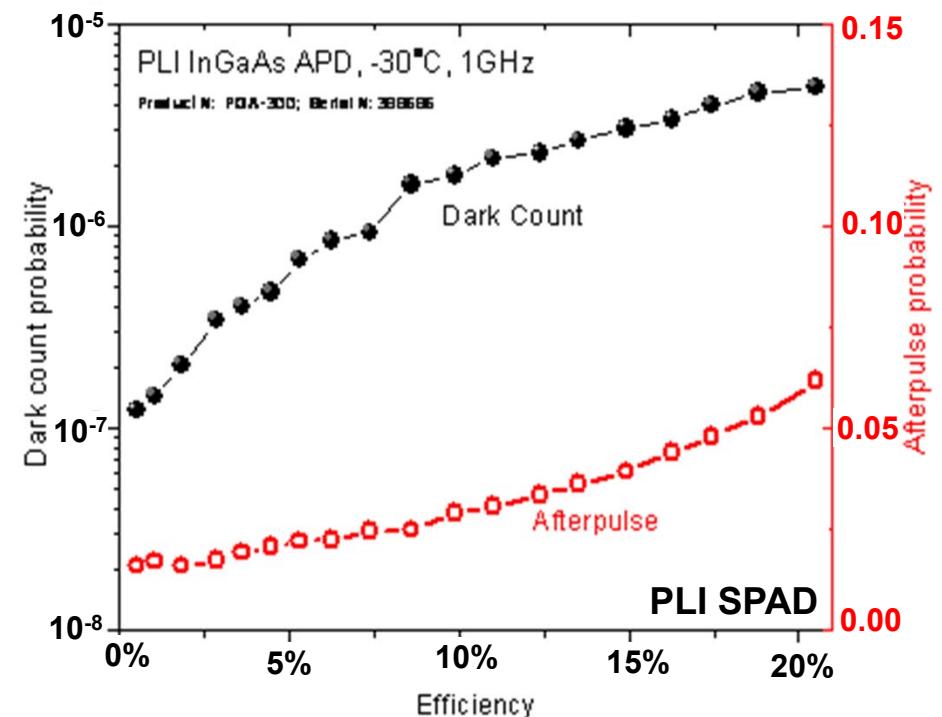
Self-differencing up to 2 GHz

- Toshiba self-differencing technique with GHz gating, sub-ns gates
 - ◆ 2 GHz gate repetition frequency, 50% duty cycle
- Afterpulsing ~1.5% (at 12% PDE) demonstrated at 2 GHz

Yuan, et al., APL 96, 071101 (2010)



Z. Yuan, et al., Appl. Phys. Lett. 91, 041114 (2007)

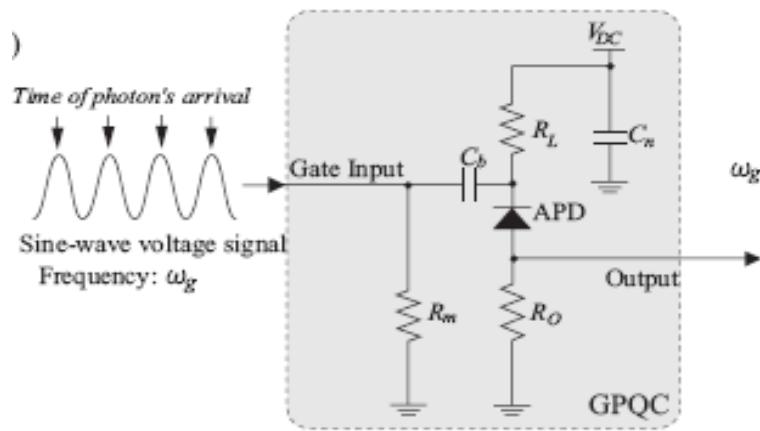


courtesy of Zhiliang Yuan – Toshiba/UK

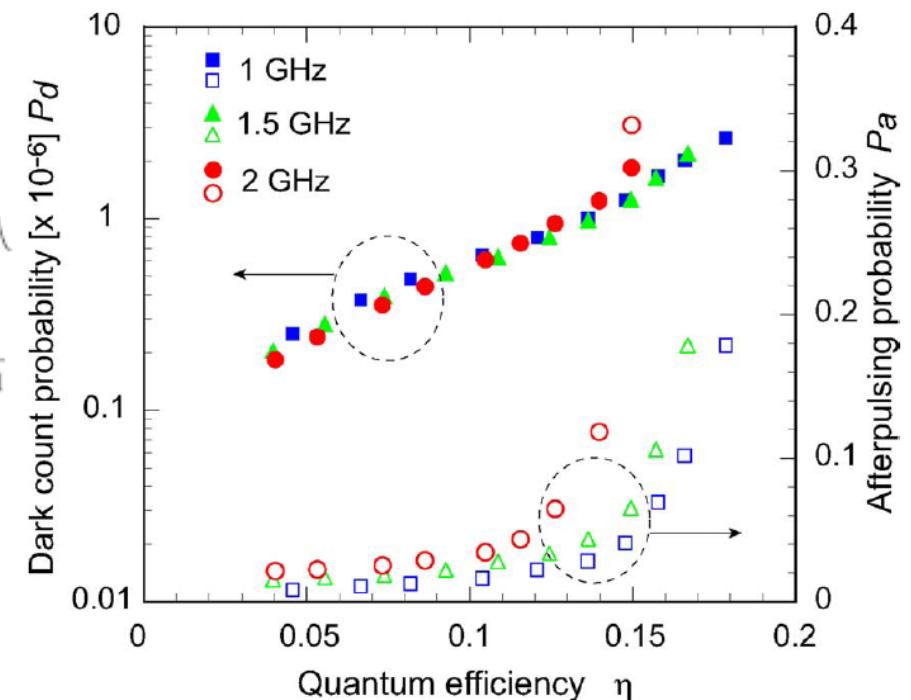
Sub-ns gating at 2 GHz with sine wave gating

- Nihon Univ. sine-wave gating up to 2 GHz, sub-ns gates
 - Strong notch filtering of sine wave bias leaves only avalanche response
- Afterpulsing probability ~5 % (at 12% PDE) at 2 GHz

Sine wave gating and filtering



N. Namekata, S. Sasamori, S. Inoue,
Opt. Expr. 14, 10043 (2007)



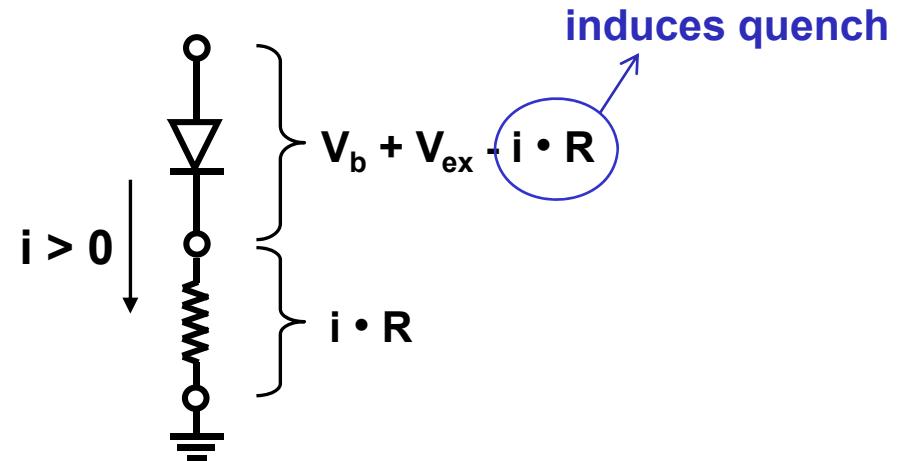
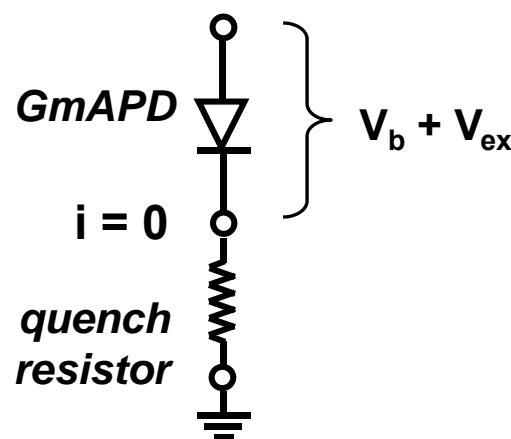
N. Namekata, S. Sasamori, S. Inoue,
PTL 22, 529 (2010)

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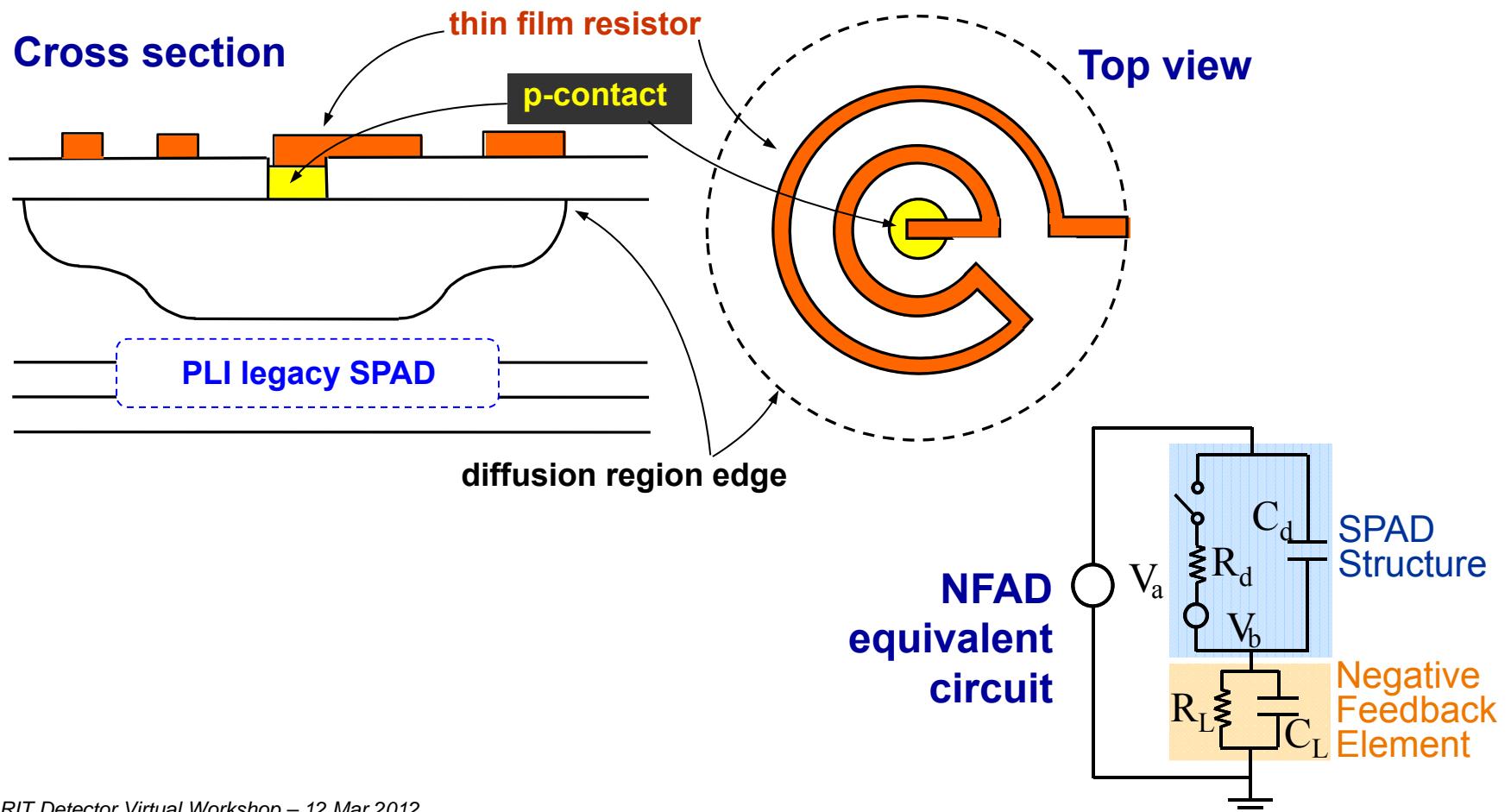
Self-quenching “negative feedback” APD (NFAD)

- **Can we mitigate afterpulsing and crosstalk w/o complexity of short gating?**
- **Reduce avalanche current flow by self-quenching**
 - Introduce “negative feedback” to oppose the positive feedback of avalanche impact ionization process
- **Use passive quenching with “free-running” detector**
 - ◆ Fixed DC bias across GmAPD + Resistor
 - ◆ Current flow through load resistance causes $i \cdot R$ drop → shifts voltage away from SPAD



Self-quenching NFADs device design

- Use monolithic implementation to minimize parasitic effects
 - Surface-integrated thin film resistors
 - Fully compatible with optimal GmAPD designs – no epi-structure tradeoffs



Self-quenching behavior depends on feedback

- Need large R_L to ensure rapid self-quenching and small charge flow Q
 - ◆ Current in junction must fall below threshold value for self-quench to occur
- “Recharge” time following quench has time constant $R_L C_d$

Principal design trade-off:

Large $R_L \rightarrow$ rapid quenching

Small $R_L \rightarrow$ rapid recharging

Device diameter: 25 μm

Discharge (quench):

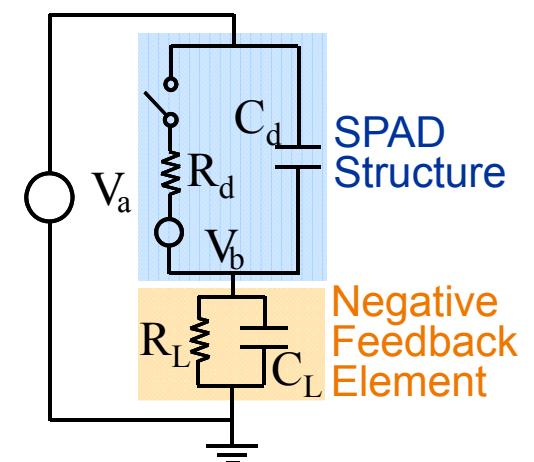
$$\tau \sim R_d C_d \rightarrow (5 \text{ k}\Omega)(100 \text{ fF}) \sim 0.5 \text{ ns}$$

Recharge (re-arm):

$$\tau \sim R_L C_d \rightarrow (0.1 - 1 \text{ M}\Omega)(100 \text{ fF}) \sim 10 - 100 \text{ ns}$$

“Minimum” charge flow:

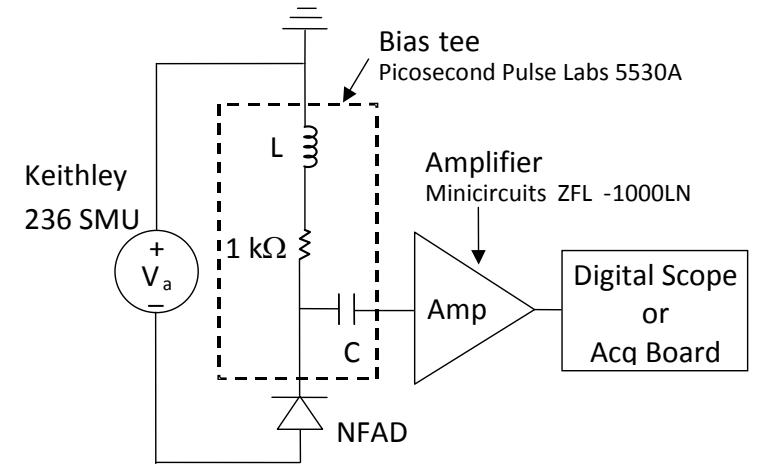
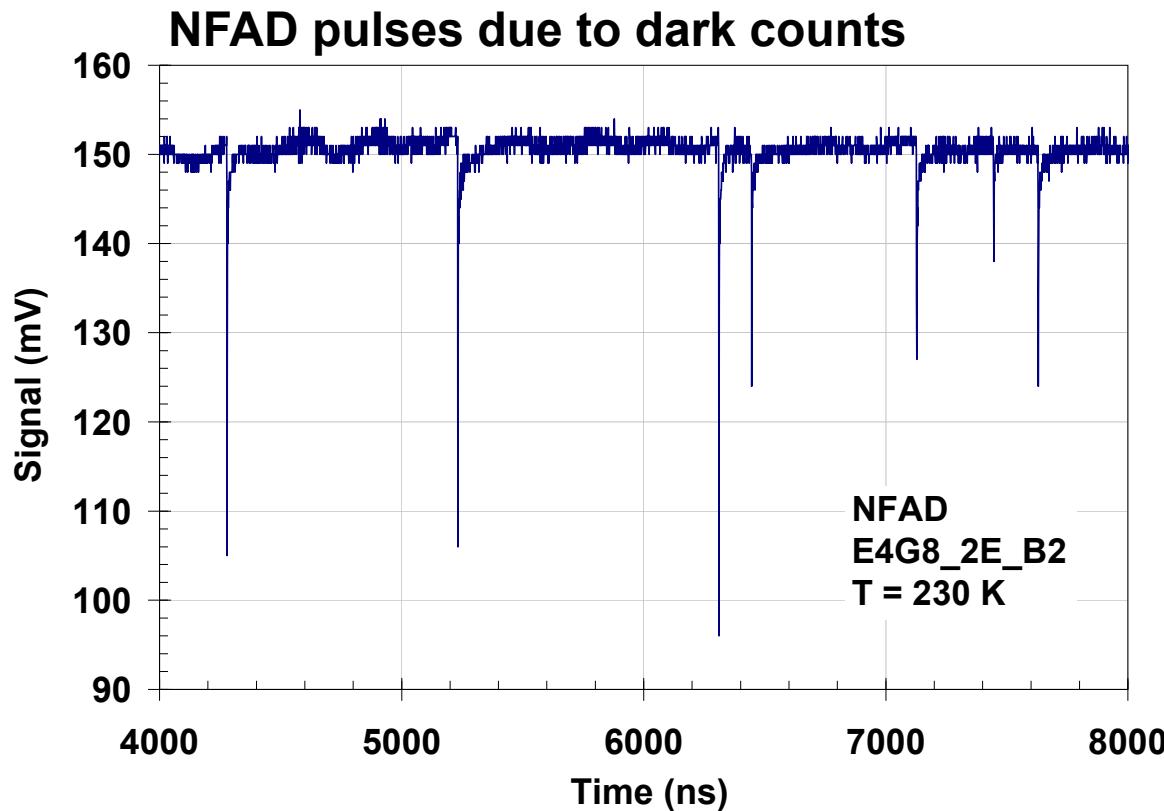
$$Q = C_d V_{ex} \rightarrow (100 \text{ fF})(2 \text{ V}) \sim 1 \times 10^6 \text{ e}^-$$



First generation of NFAD devices exhibited desired behavior



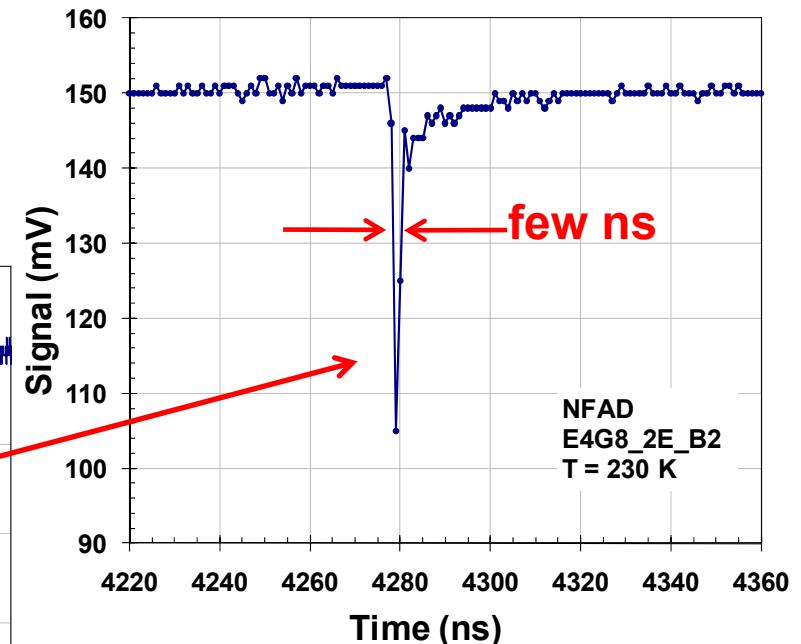
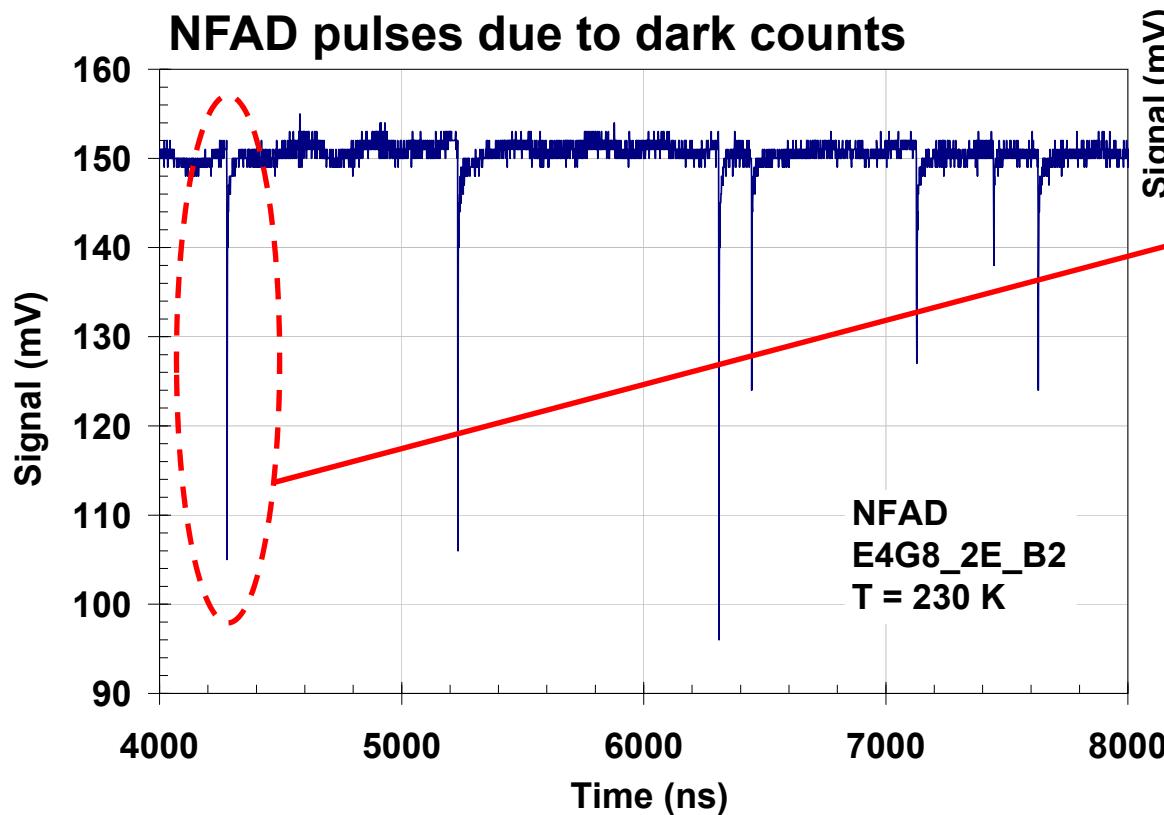
- Operate with simple bias T
- Sharp detection pulses with fixed DC bias



$R_L \sim 90 \text{ k}\Omega$

First generation of NFAD devices exhibited desired behavior

- Operate with simple bias T
- Sharp detection pulses with fixed DC bias

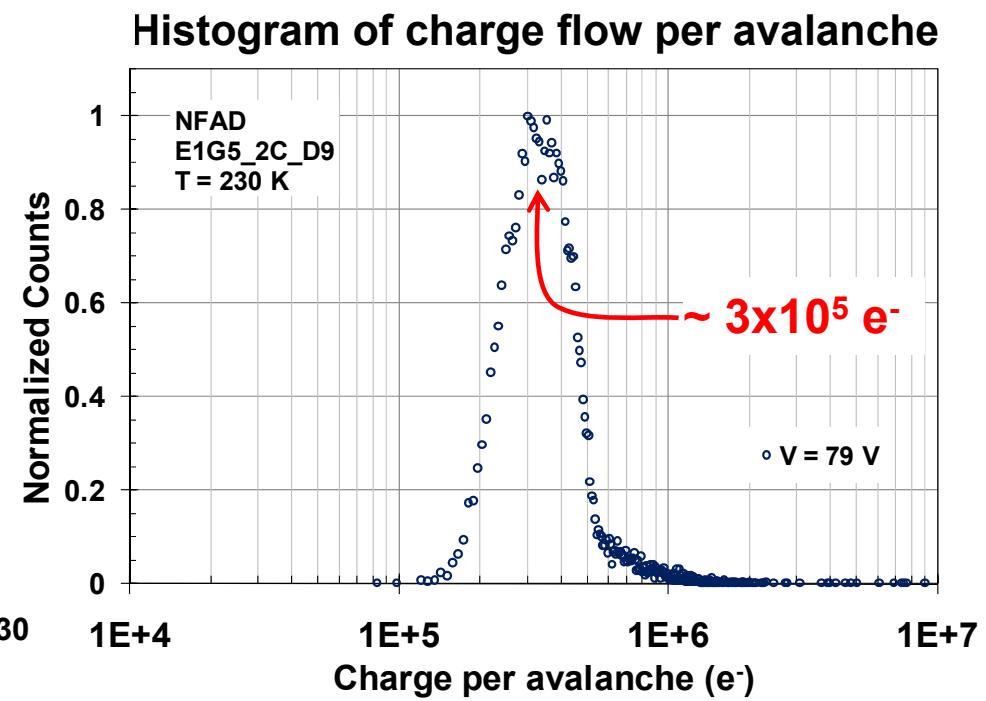
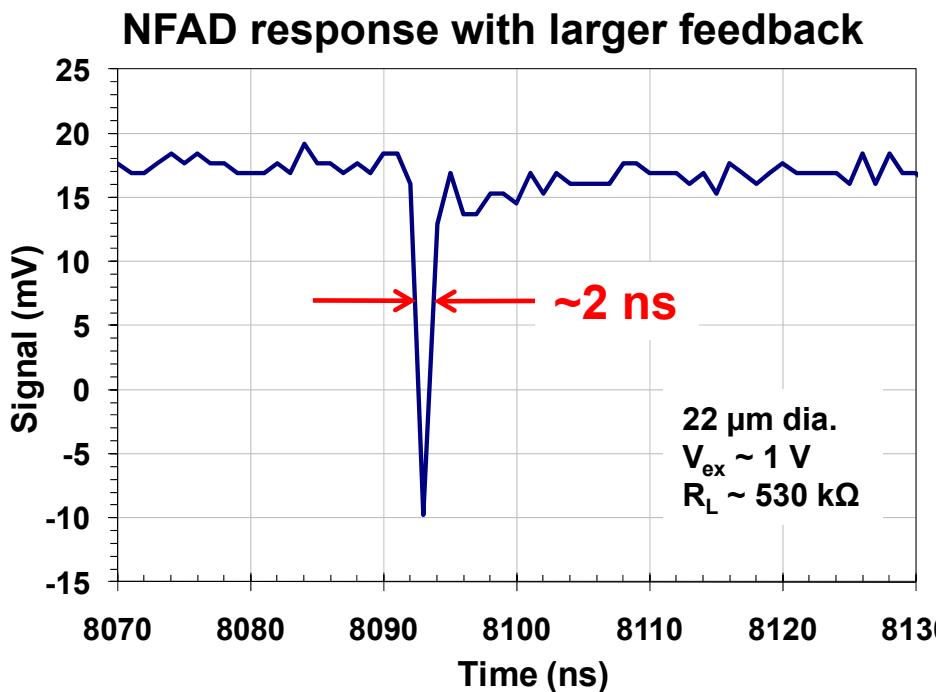


$$R_L \sim 90\text{ k}\Omega$$

Larger negative feedback provides even more effective self-quenching

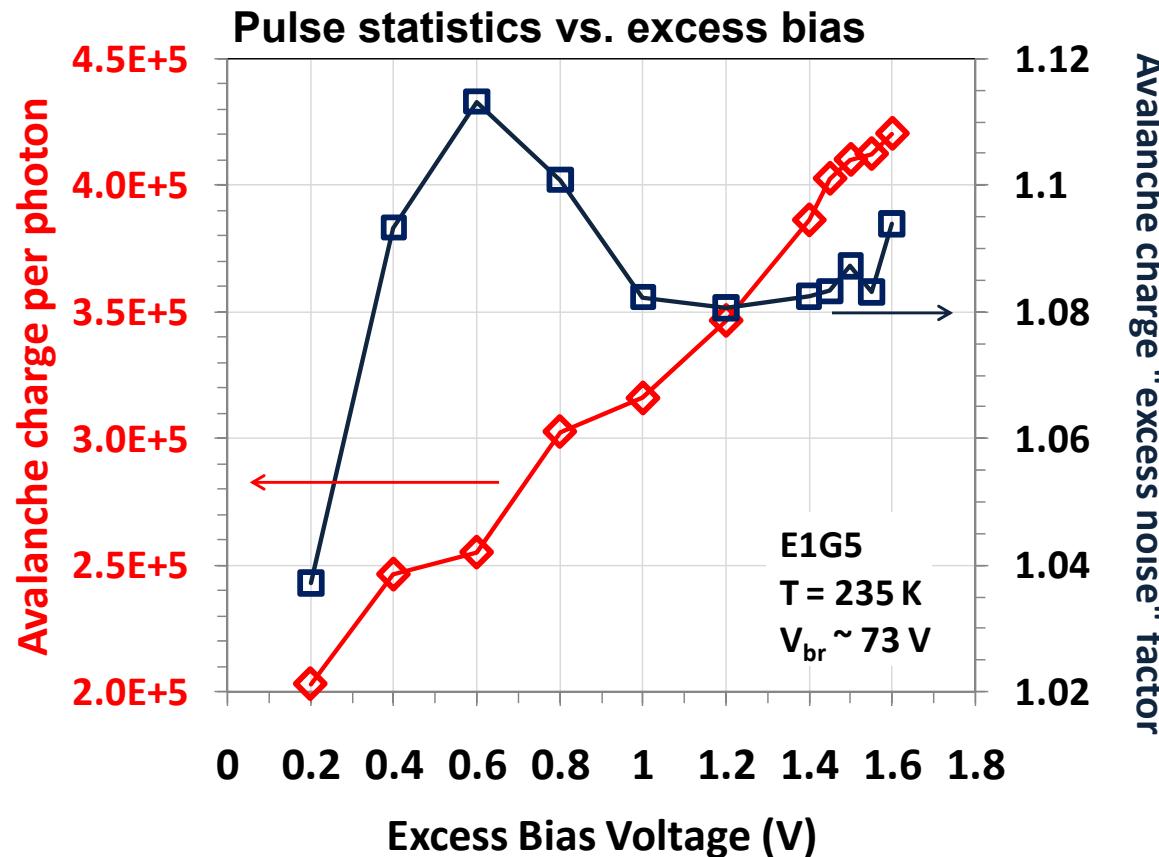
- NFAD avalanche response: pulse width ~ 2 ns, height ~ 25 mV
- Total current flow: $Q \sim 3 \times 10^5 e^-$
- How reproducible are NFAD avalanche properties?

$R_L \sim 500$ k Ω



Statistics of avalanche charge flow

- Analyze large number of pulses (~10,000) for pulse statistics
- Charge “excess noise” $F(Q)$ is a measure of avalanche consistency
 - Directly related to variance σ^2 of the distribution
- Significantly more uniform avalanches than legacy Geiger-mode operation
 - Good prospects for resolving “summed” pulses

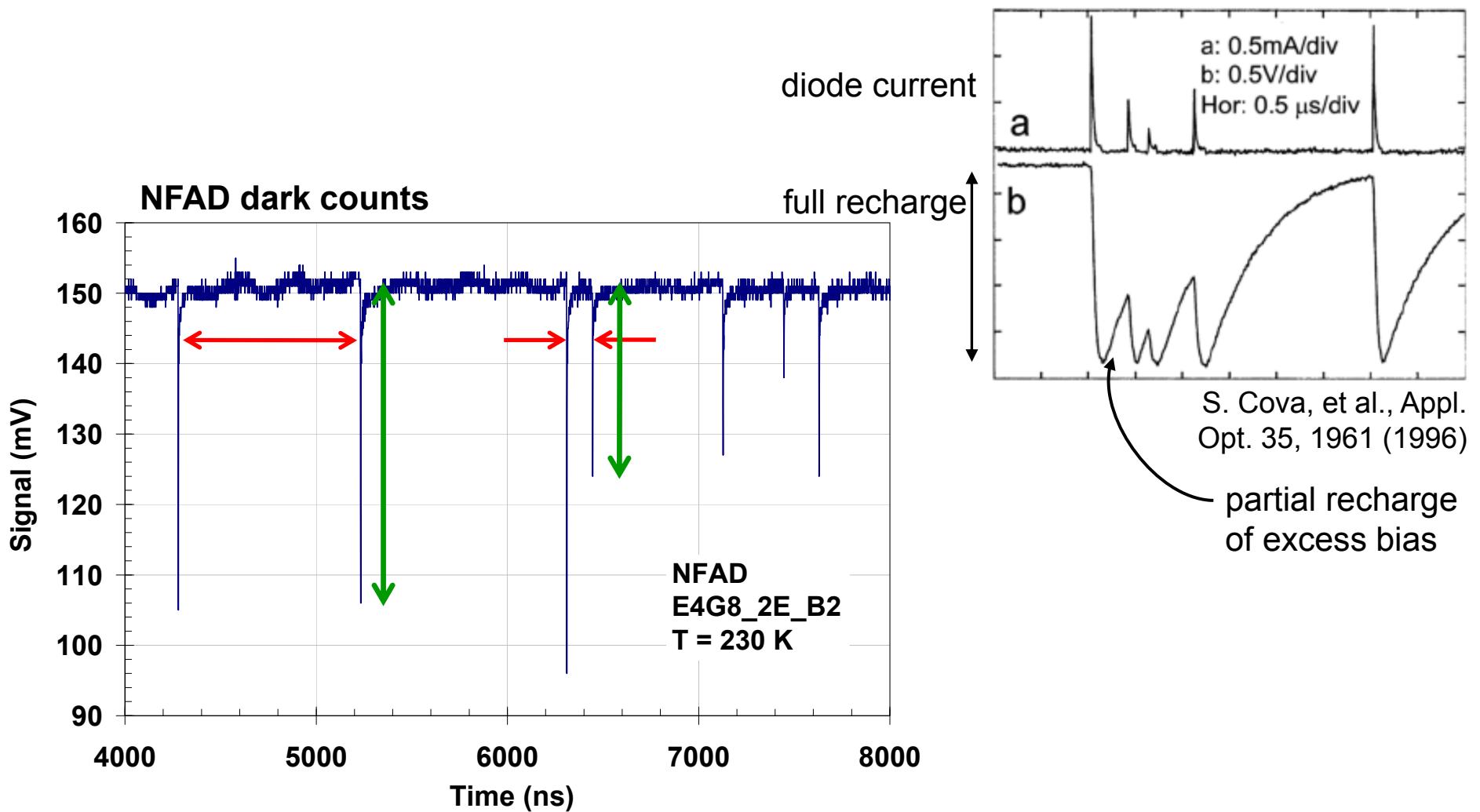


$$F(Q) = \frac{\sigma^2}{\langle Q \rangle^2} + 1$$

$$\sigma / \langle Q \rangle = 0.28 \\ \rightarrow F(Q) = 1.08$$

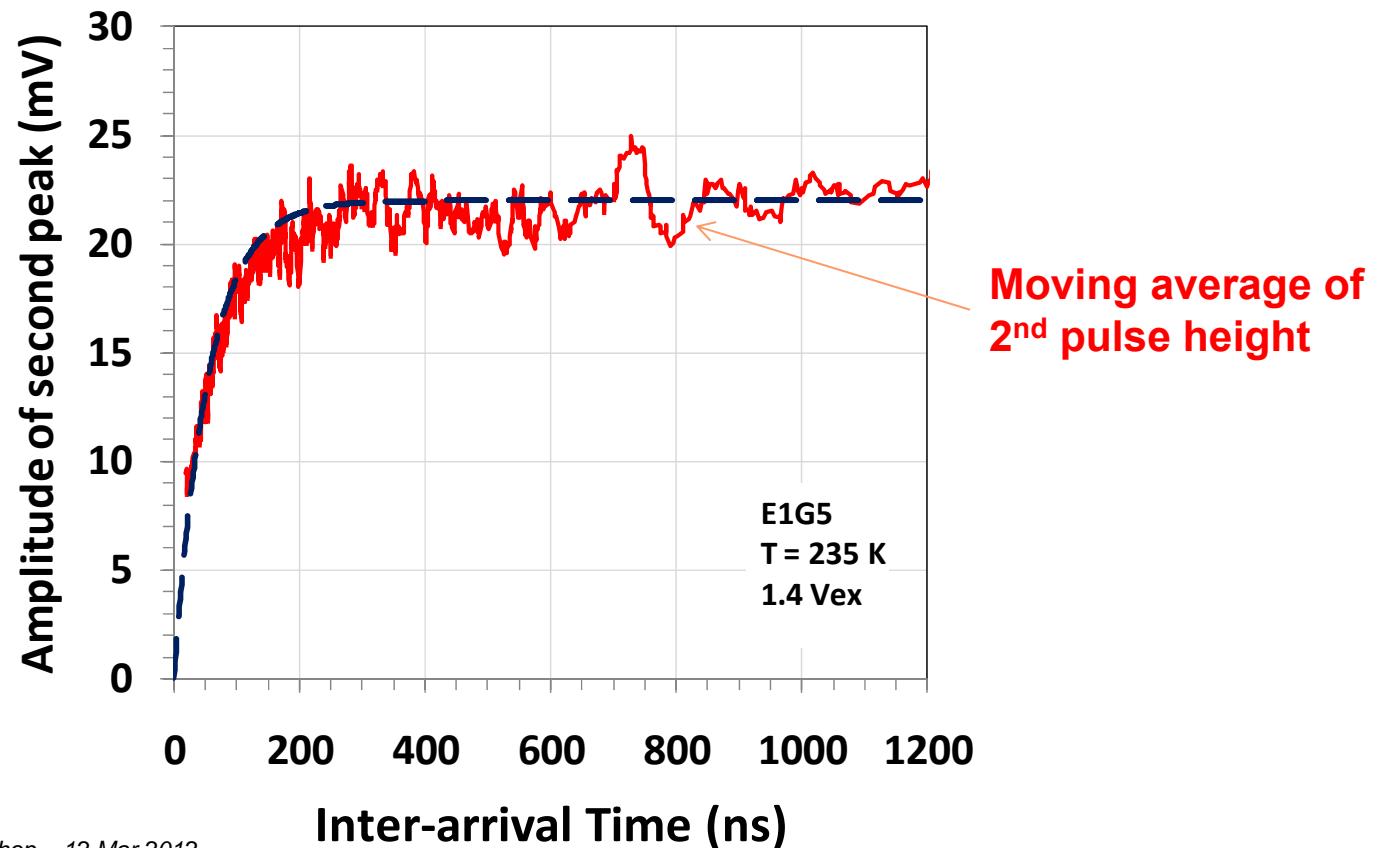
Re-arm time from pulse height correlations

- Look at correlation between **pulse height** and **pulse inter-arrival time**
 - ◆ If pulse is triggered before full re-arming, pulse amplitude will tend to be lower



Re-arming time from pulse height correlations

- Use exponential fit to 2nd pulse height (moving average) vs. interarrival time
- Find time constant $\tau = 55 \text{ ns}$; 95% recharge in $3\tau \sim 165 \text{ ns}$
- Reasonable agreement with expected $\tau = R_L C_d = (800 \text{ k}\Omega)(80 \text{ fF}) \sim 64 \text{ ns}$

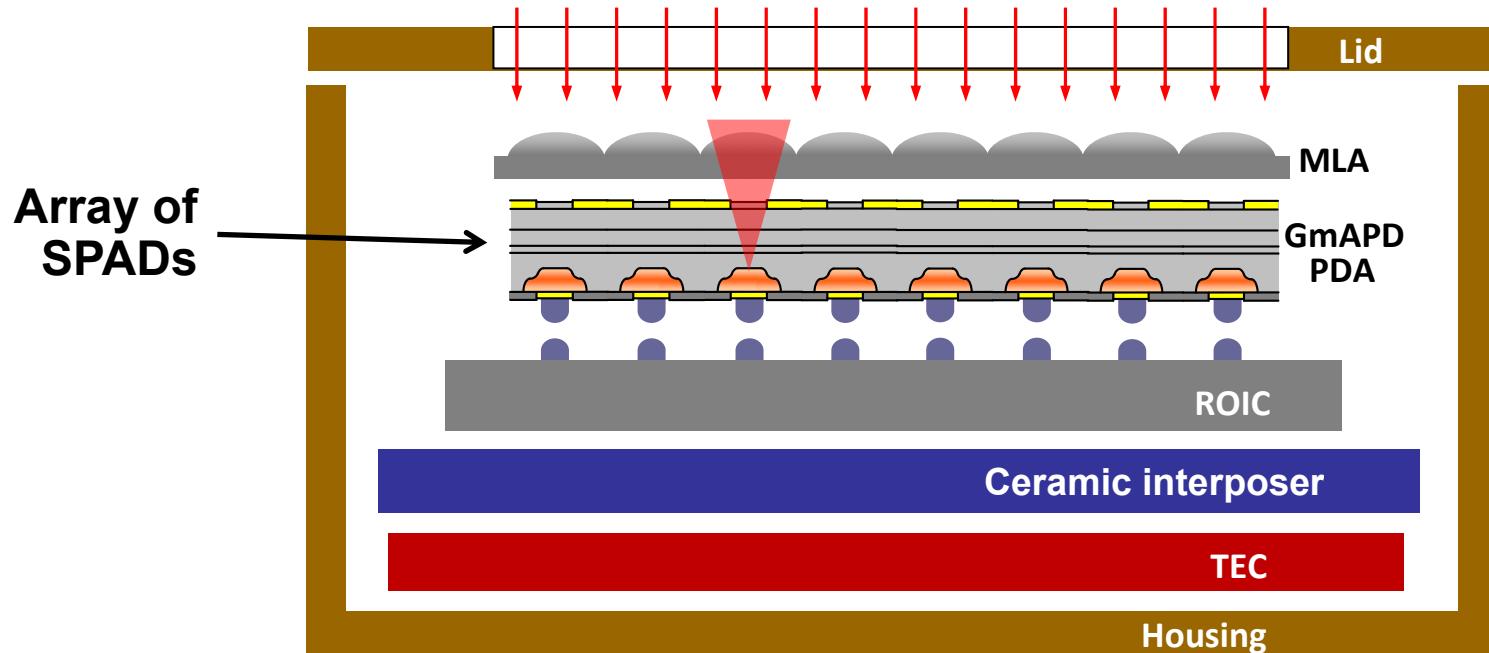


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Scaling SPADs to large-format imaging arrays

- Focal plane array (FPA) employs three-chip stack as imaging sensor engine
 - SPAD photodiode array (PDA)
 - CMOS readout integrated circuit (ROIC)
 - GaP microlens array (MLA)
- Indium bump flip-chip hybridization of PDA to ROIC
- Passive μm -scale MLA alignment and attachment to PDA

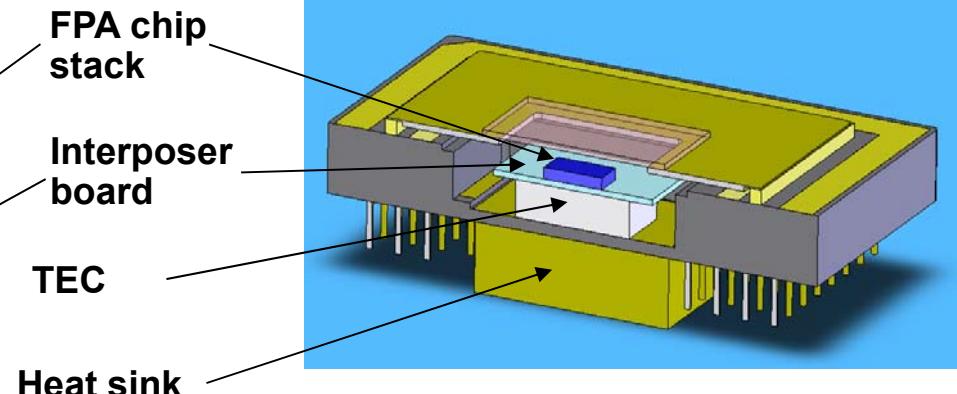
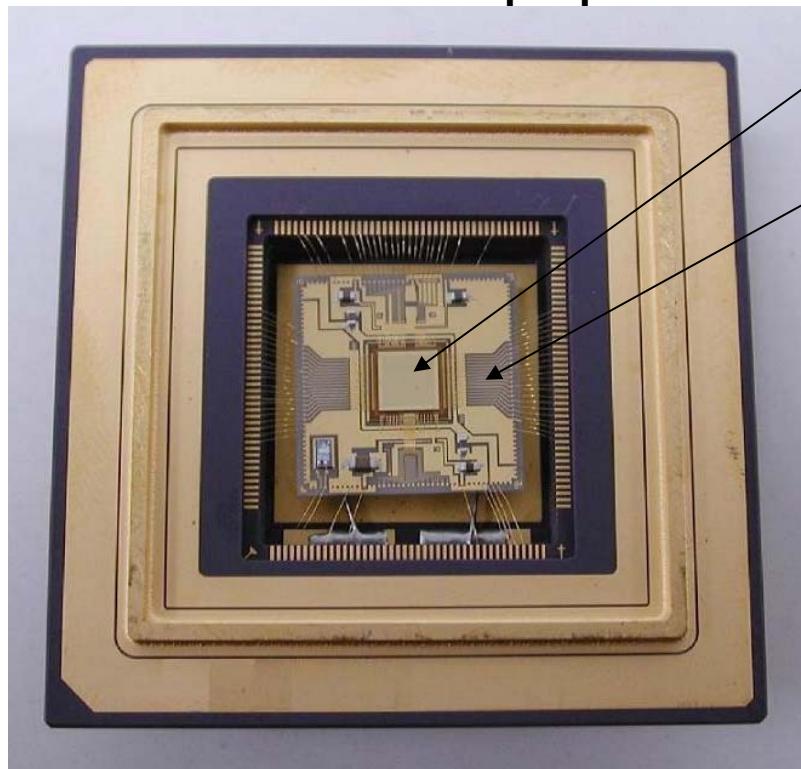


Focal plane array module assembly

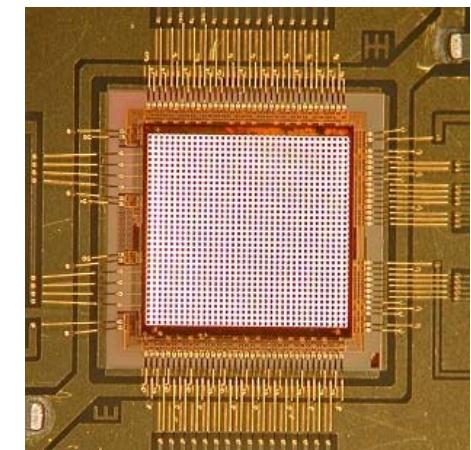
- Manage electrical, thermal, and optical interfaces to FPA
 - 175-connection pin grid array package
 - Thermoelectric cooler (TEC) maintains $\Delta T \sim 55^\circ\text{C}$ with CuW heat sink
 - Microlens array on chip stack provides ~75% fill factor
 - Hermetic lid with sapphire window

Assembled FPA module

32 x 32 format with 100 μm pitch



Chip stack
on interposer



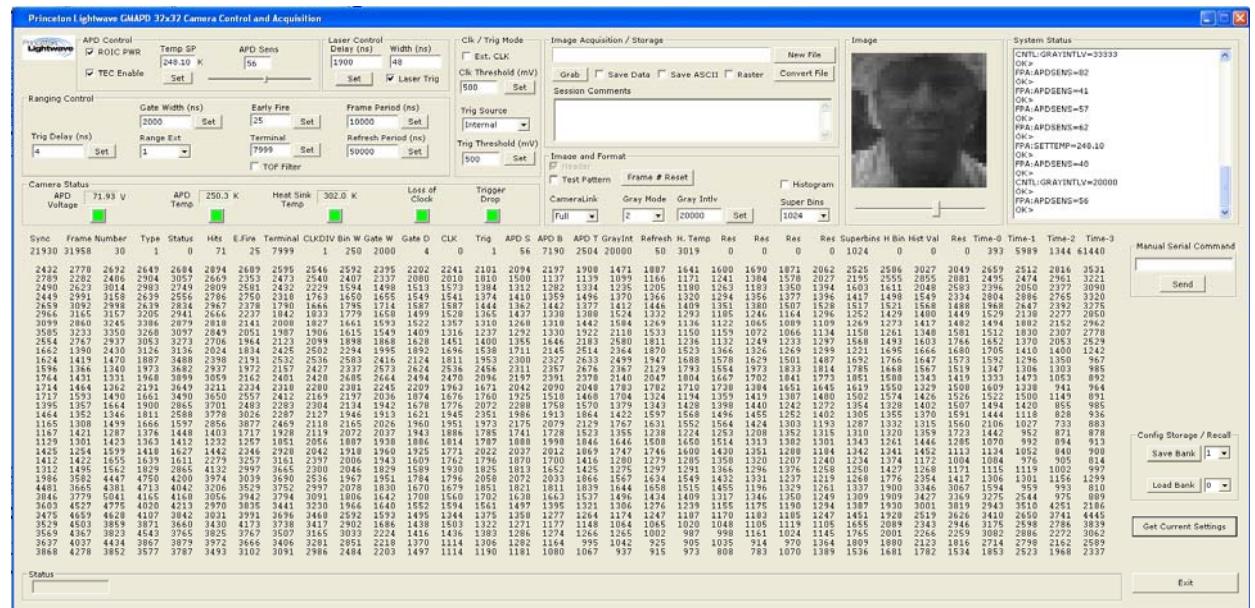
Turn-key FPGA-driven camera system



- Three-board turn-key commercial camera
 - FPA board, FPGA board, and Interface board
- Adjustable frame period (“range gate”) between 4 ns and 10 μ s
- 32 x 32 format (100 μ m pitch) with ~200,000 frames per second

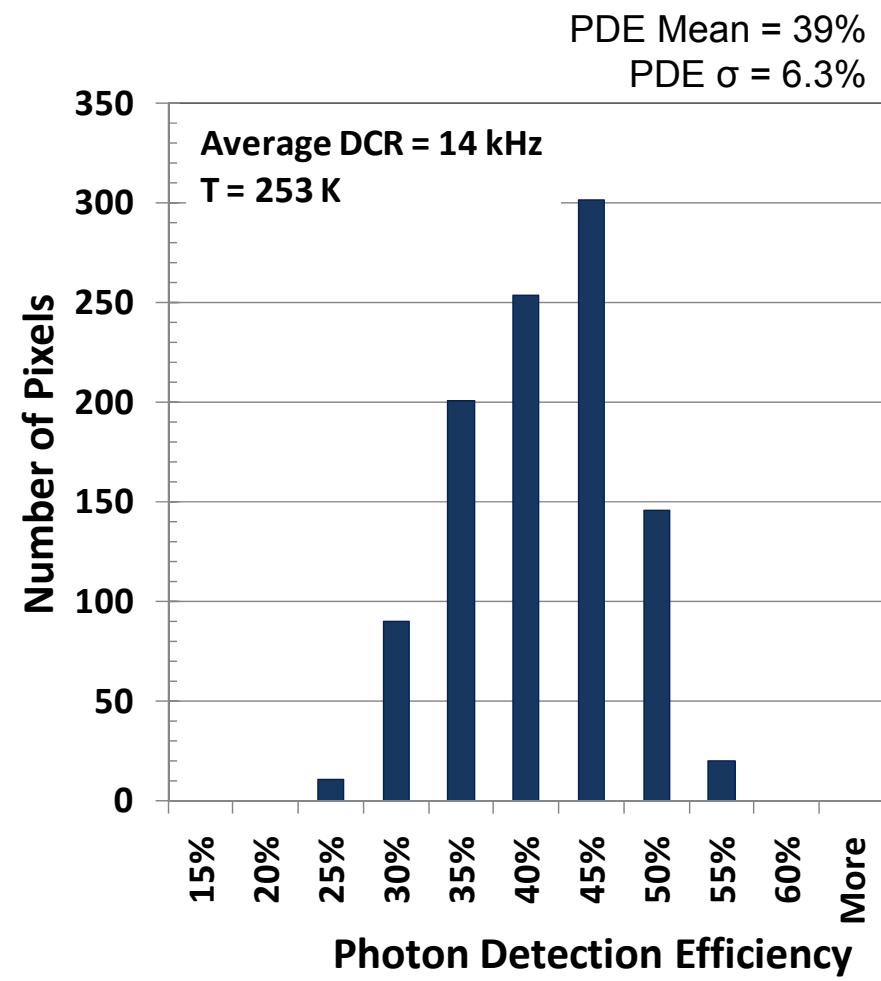
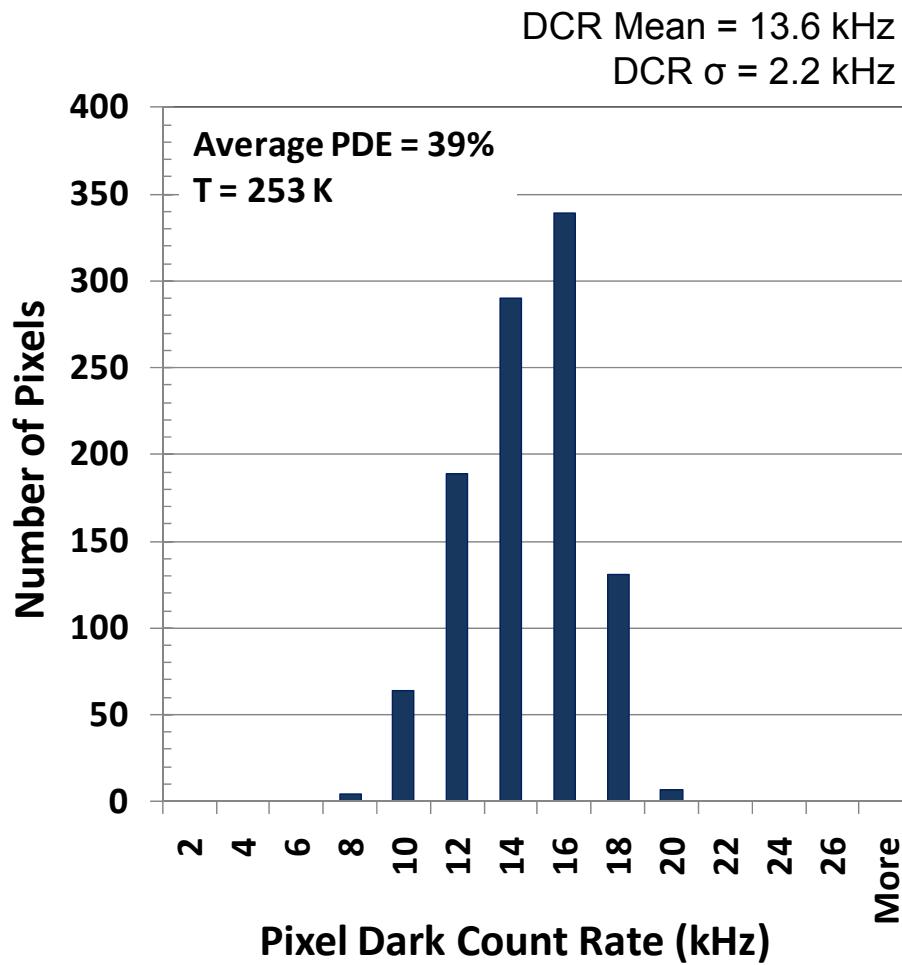


Comprehensive GUI



DCR & PDE distributions

- All 1024 pixels have DCR < 20 kHz for mean PDE = 39%

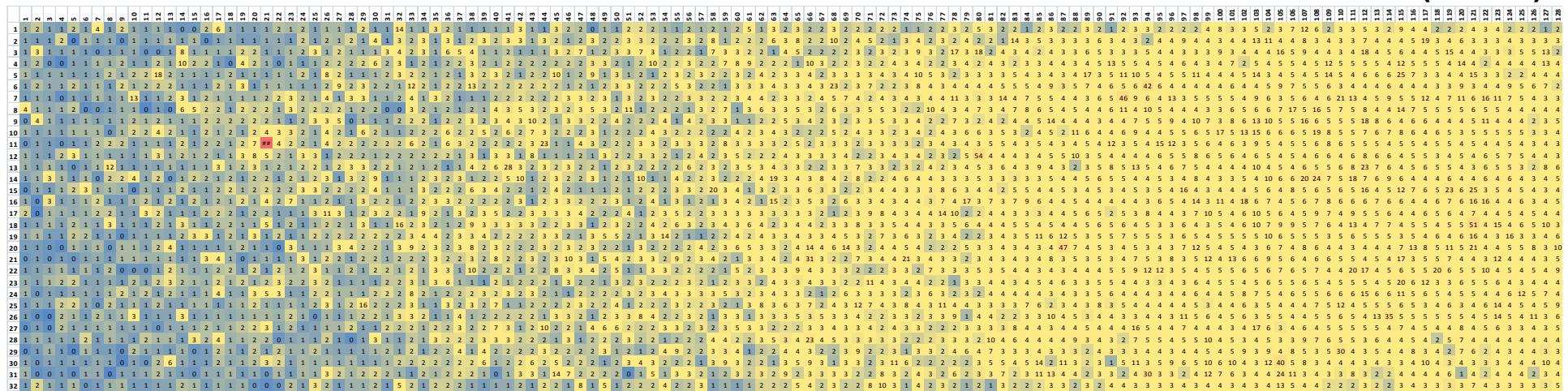


1.5 μm FPAs and larger format FPAs



- 32 x 32 format camera for 1.5 μm at same quality as 1.06 μm
 - ◆ 100% pixel yield
 - ◆ Higher DCR due to narrower bandgap (InGaAs) absorber
- 32 x 128 format (50 μm pitch) at 1.06 μm with >99.9% yield
 - ◆ Extent of performance gradient depends on location on wafer

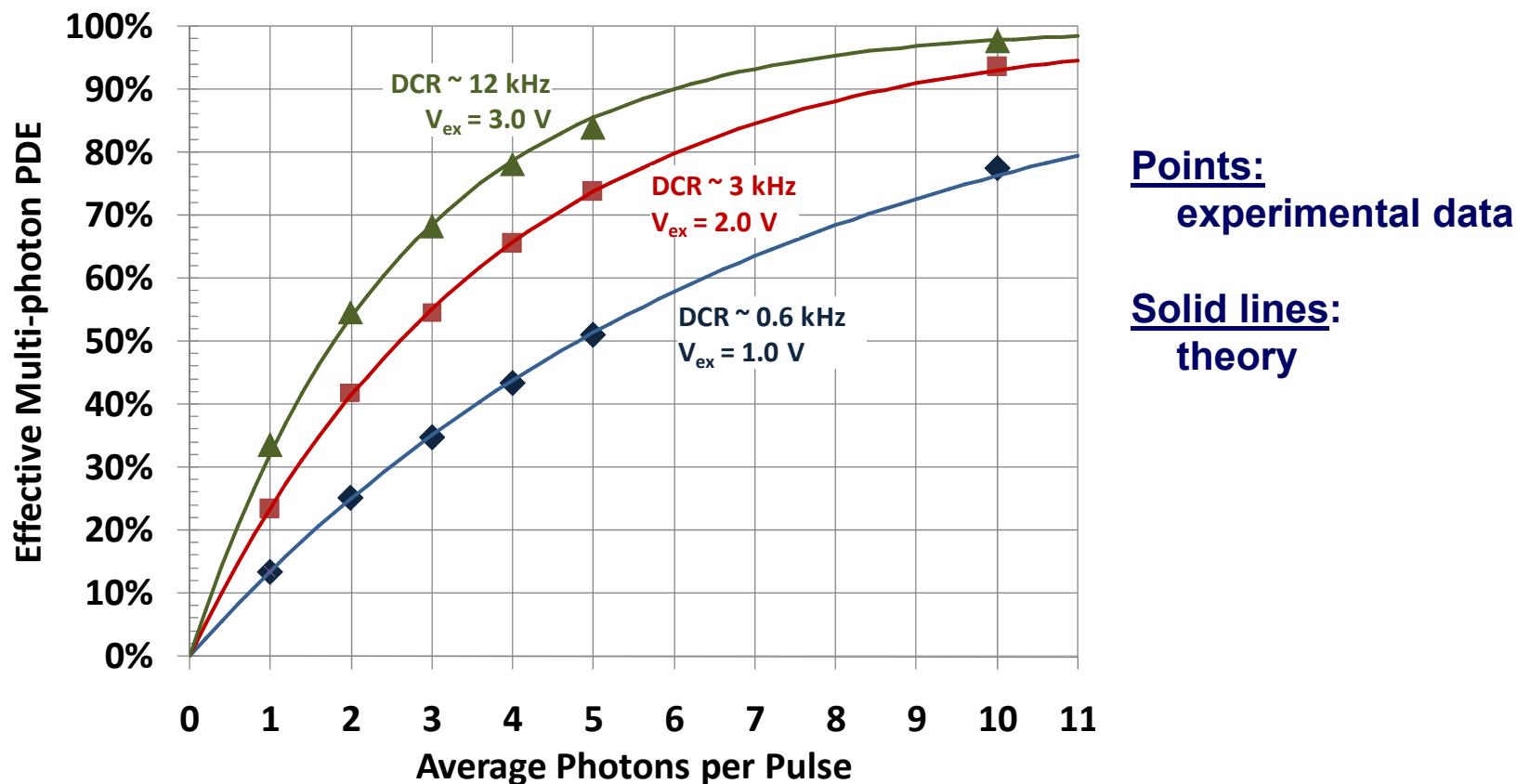
DCR (in kHz)



- Largest format to date developed by MIT-LL: 64 x 256 (50 μm pitch)

Multi-photon pulse detection efficiency (PuDE)

- Measure PuDE as a function of mean photon number μ
- Good agreement with theory:
$$\text{PuDE}(\mu) = \sum_N \frac{\mu^N e^{-\mu}}{N!} \{1 - (1 - \text{PDE})^N\}$$
 - ◆ Single photon sensitivity provides high detection probability for pulses of 5 - 10 photons

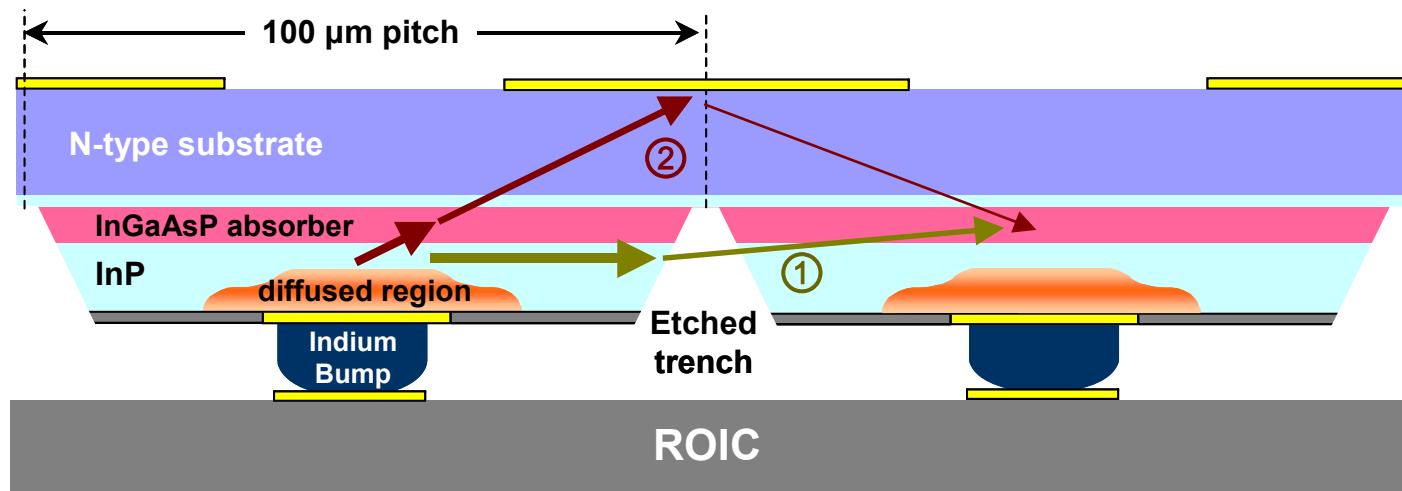


Crosstalk in SPAD arrays is challenge for scaling

- Consider optical cross-talk contributions
 - Avalanches can emit crosstalk photons due to hot carrier luminescence
 - Path ① : direct line-of-sight to nearest neighbor pixels
 - Path ② : reflection from back-side surface of PDA
- Use etched trenches to mitigate line-of-sight crosstalk



Photo of GmAPD 32 x 32 array



Crosstalk as function of pixel position

- Crosstalk falls off with distance from primary avalanche (on average)
 - Count all events within $\sim 500 \mu\text{m}$ radius and within 10 ns of primary avalanche
 - Nearest neighbor pixels show <1% crosstalk probability per pixel
 - Consistent “signature” shows that certain relative pixel positions have higher crosstalk

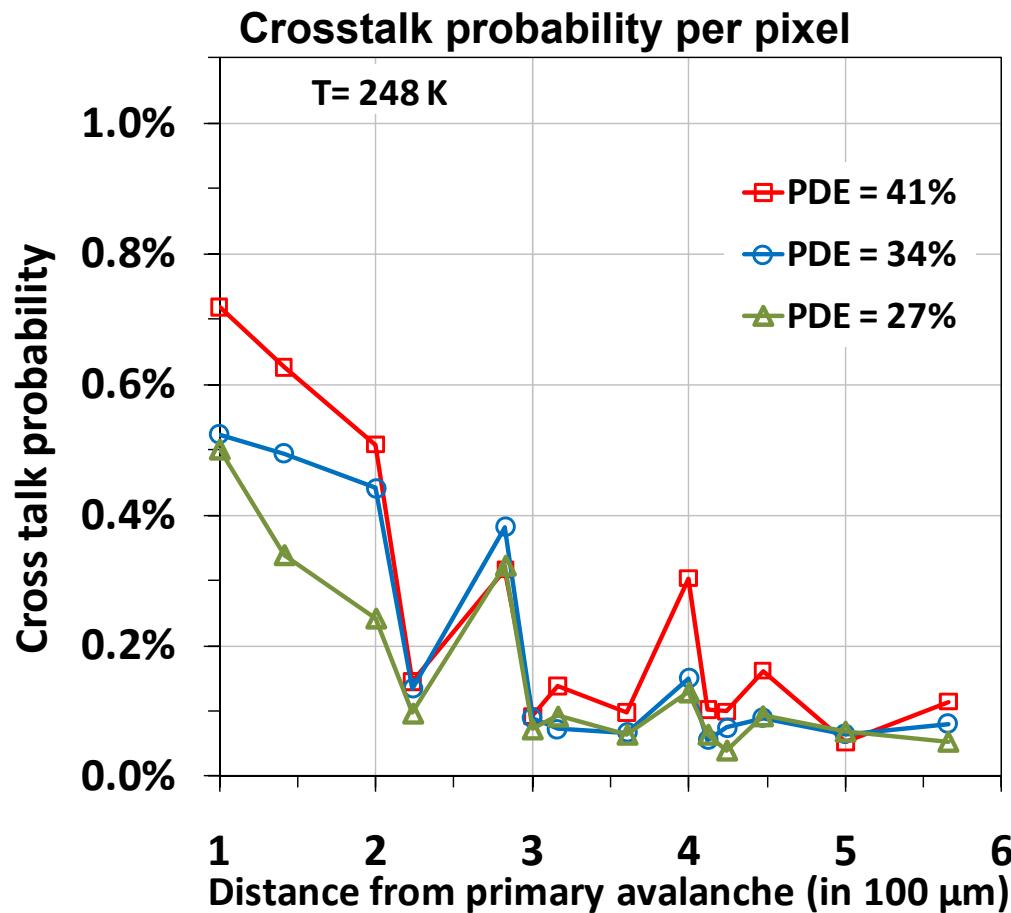


Illustration of relative distances from primary avalanche

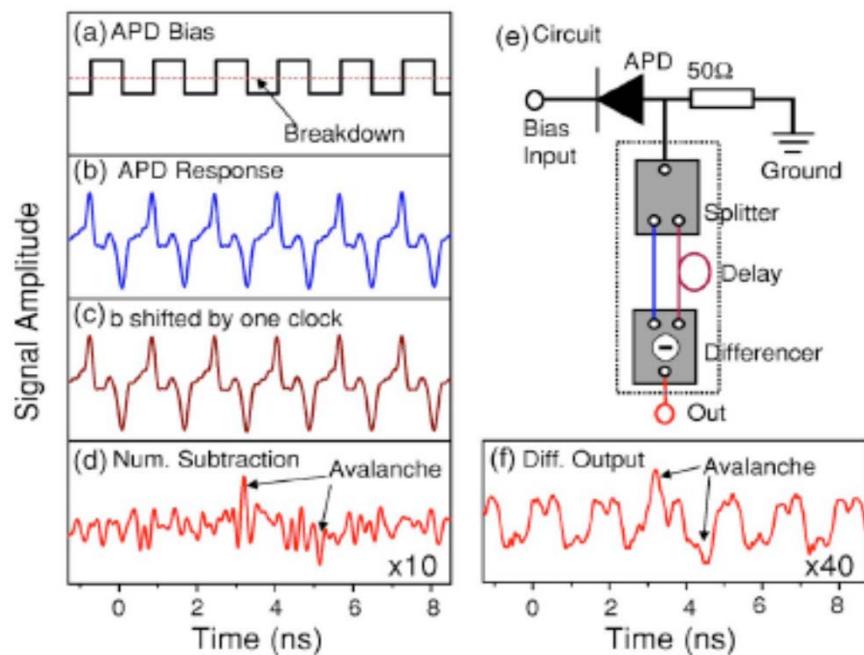
			3			
	2.8	2.2	2	2.2	2.8	
	2.2	1.4	1	1.4	2.2	
3	2	1	0	1	2	3
	2.2	1.4	1	1.4	2.2	
	2.8	2.2	2	2.2	2.8	
			3			

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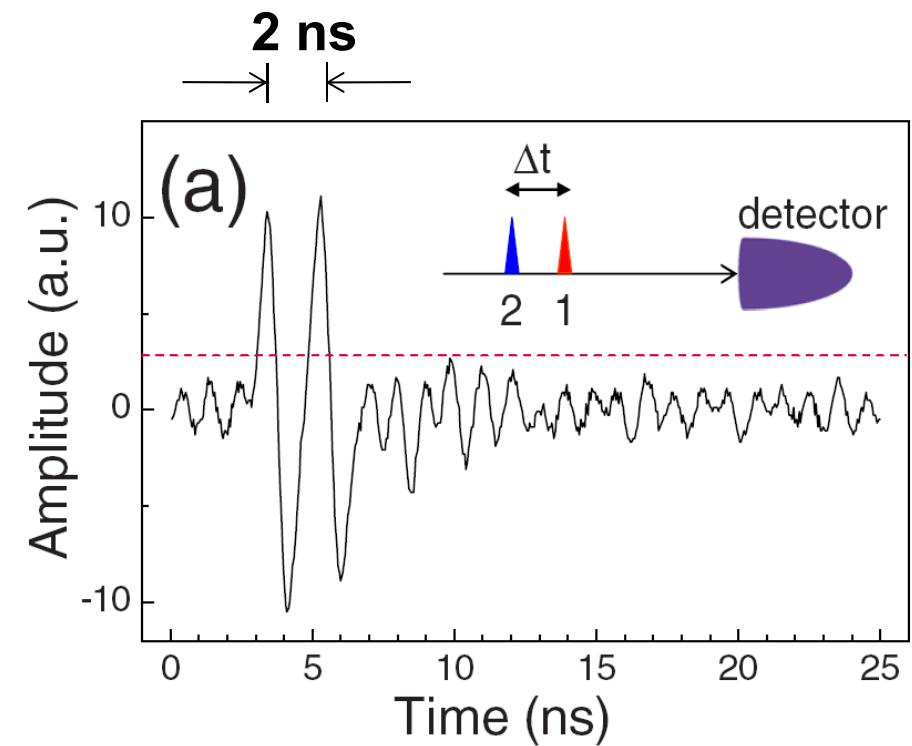
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Nanosecond-scale photon counting with SPADs

- Toshiba self-differencing technique with 1 GHz gating
- Key point: proof-of-feasibility for SPADs counting every ~ 2 ns



Z. Yuan, et al., Appl. Phys. Lett. 91, 041114 (2007)



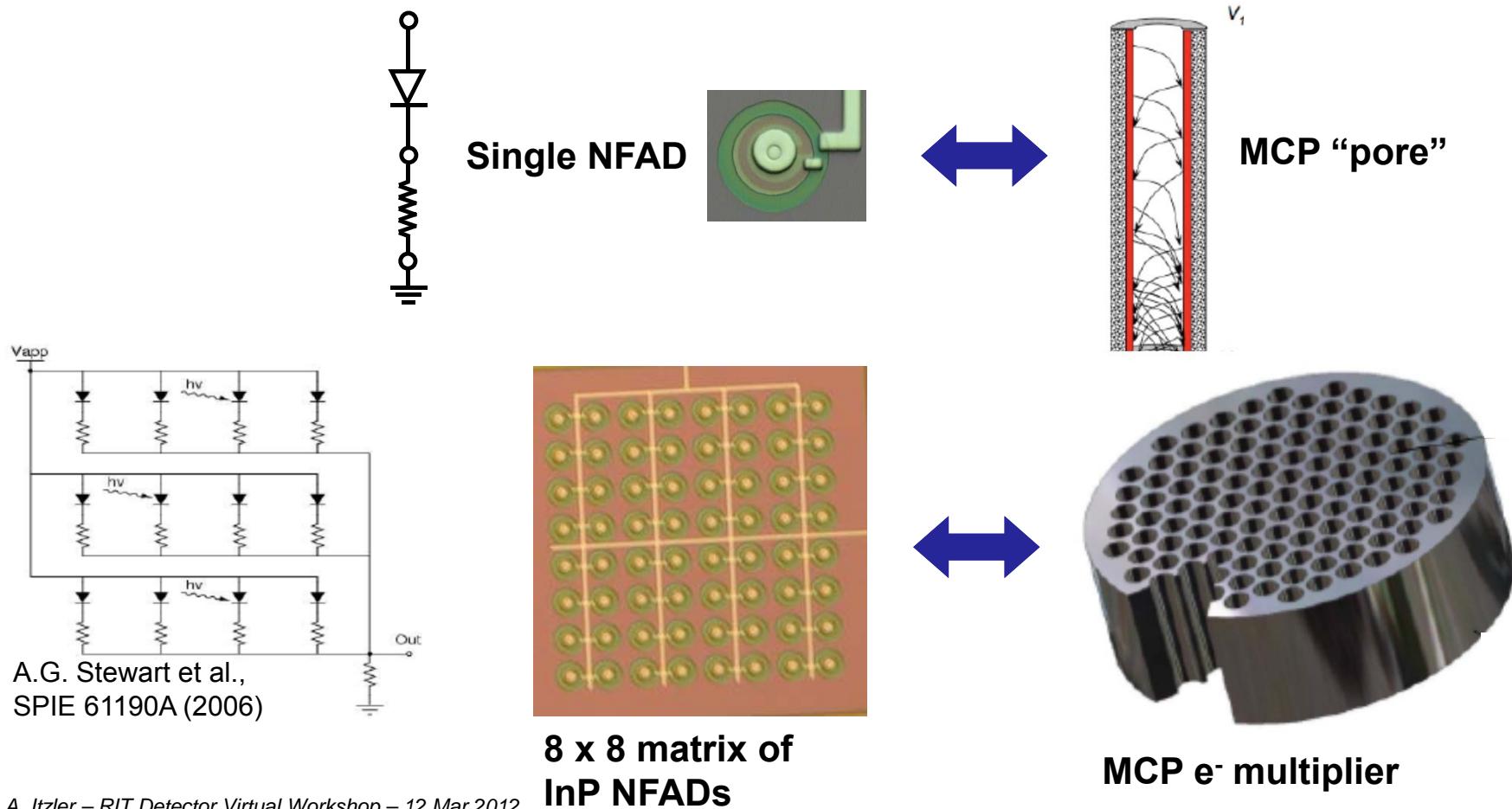
A. R. Dixon, et al., Appl. Phys. Lett. 94, 231113 (2009)

Prospects for advances in high-rate counting

- **Timing jitter limitations**
 - ◆ for communications apps, ~100 ps jitter will limit rates to < 10 GHz
- **Inherent device bandwidth limitations**
 - ◆ same challenges as 10 GHz linear APDs (transit time / RC / avalanche build-up)
- **Challenges of non-periodic (free-running) operation**
 - ◆ All GHz-rate techniques to date require periodic operation
- **Benefits in evolving to multiplexed solutions**

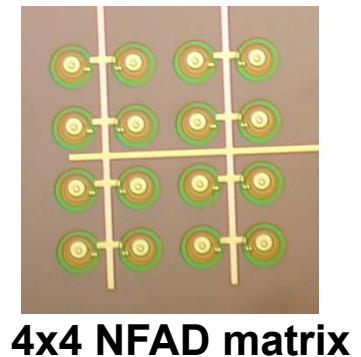
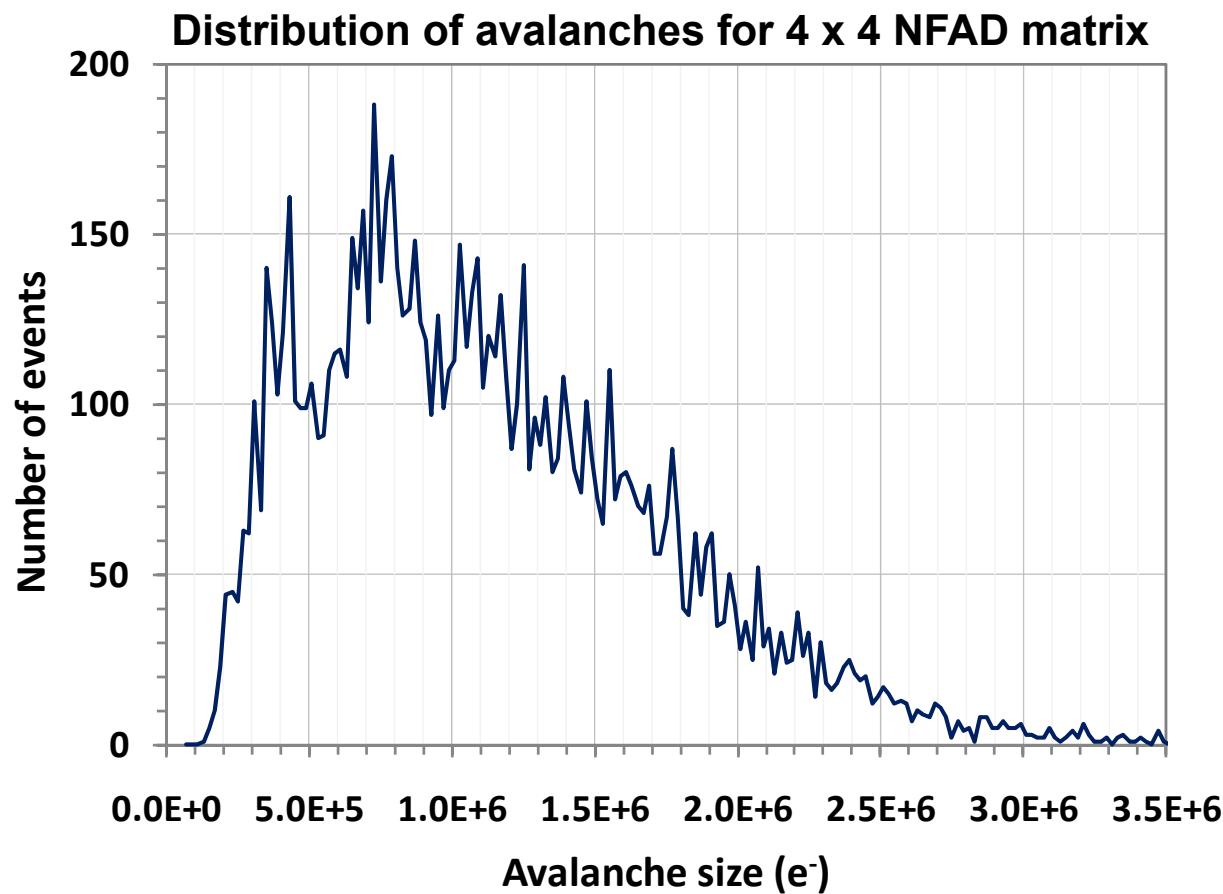
NFADs as solid state photomultiplier (SSPM)

- Single NFAD device independently avalanches, self-quenches, and resets
- NFADs exhibit reasonably uniform pulse responses
- Connect a “matrix” of NFAD devices in parallel
→ “solid state” equivalent to microchannel plate (MCP) photomultiplier



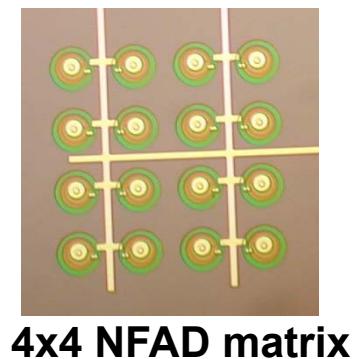
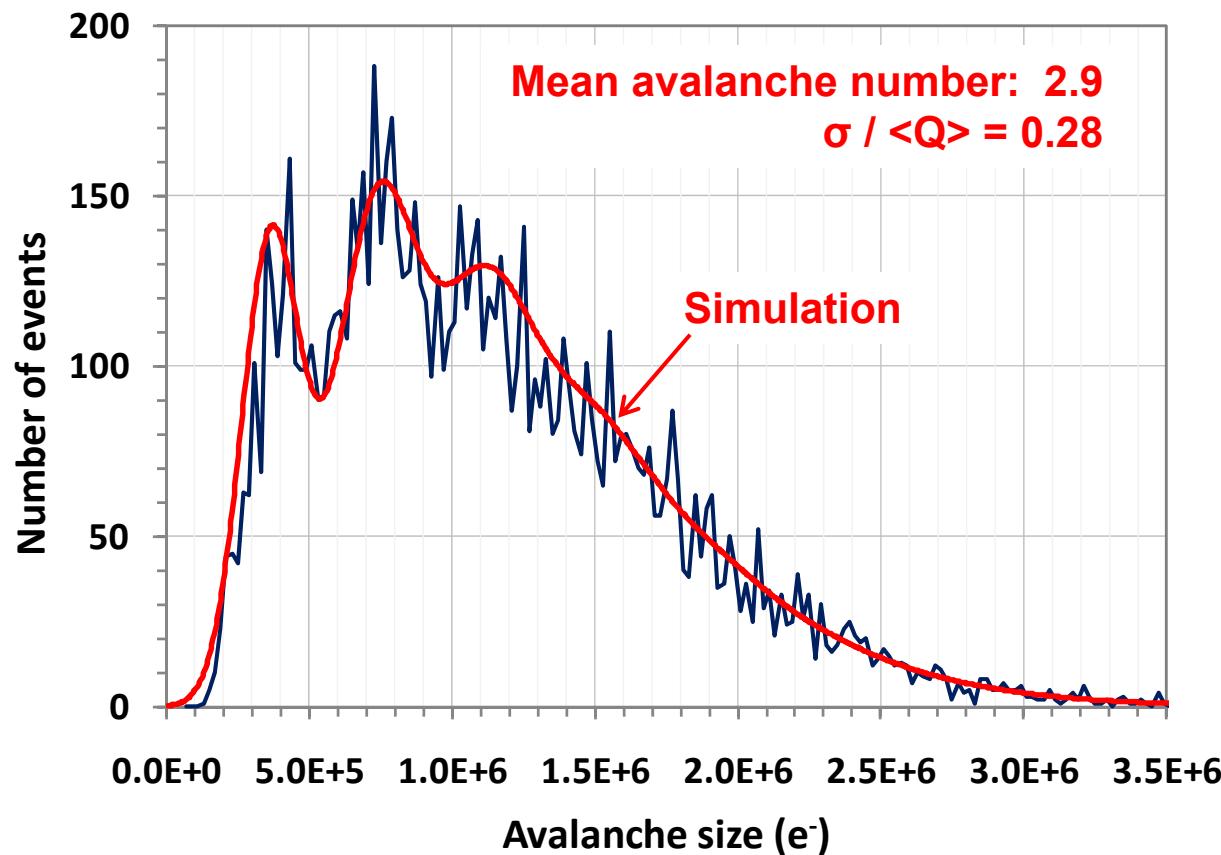
First demonstration of NFADs as SSPM

- “Matrix” of NFADs can provide photon number resolution
 - ◆ Measured distribution of avalanche response peaks shows multi-avalanche structure



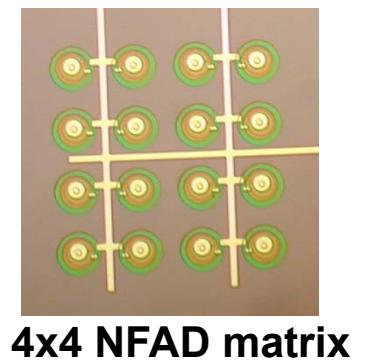
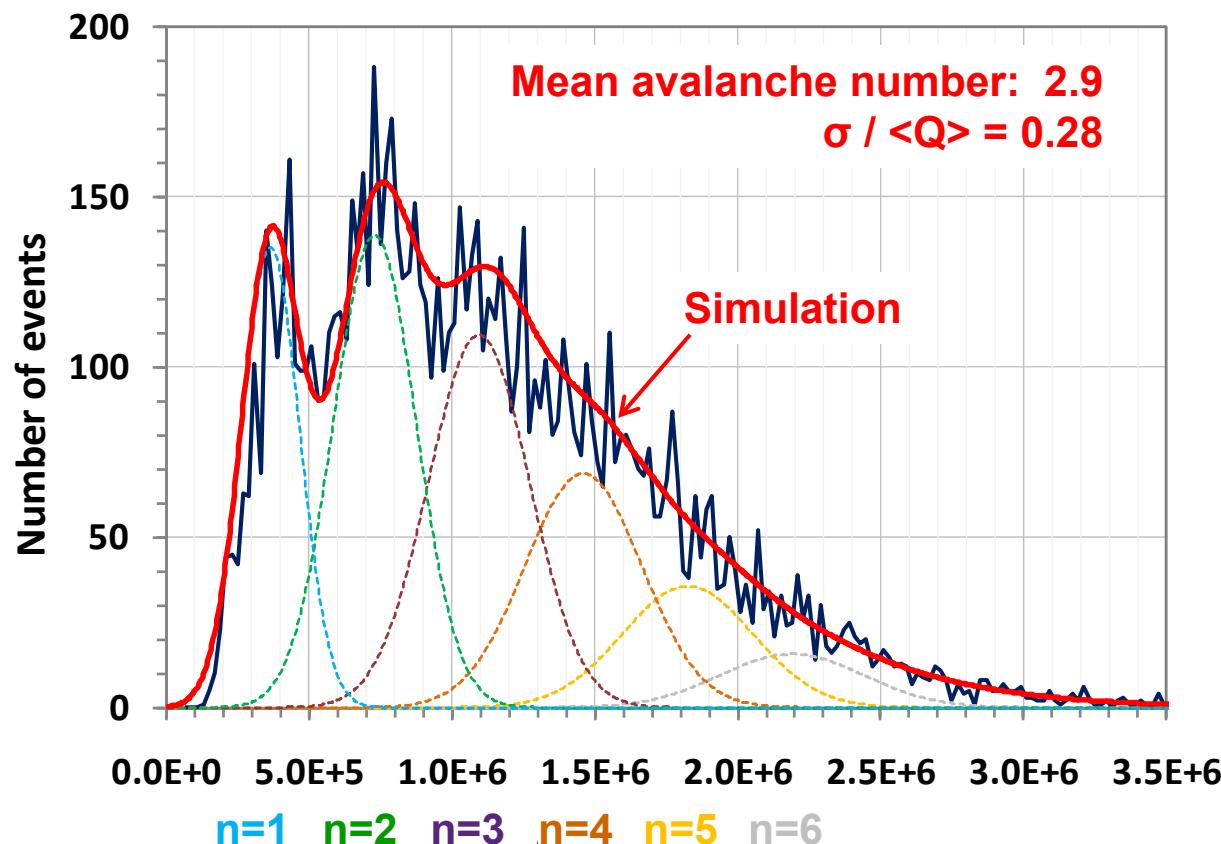
First demonstration of NFADs as SSPM

- “Matrix” of NFADs can provide photon number resolution
 - Measured distribution of avalanche response peaks shows multi-avalanche structure
- Simple model provides very good description of response
 - Assume Gaussian distribution for peak height variation ($\sigma / \langle Q \rangle = 0.28$)
 - Use Poisson statistics for incident photon number



First demonstration of NFADs as SSPM

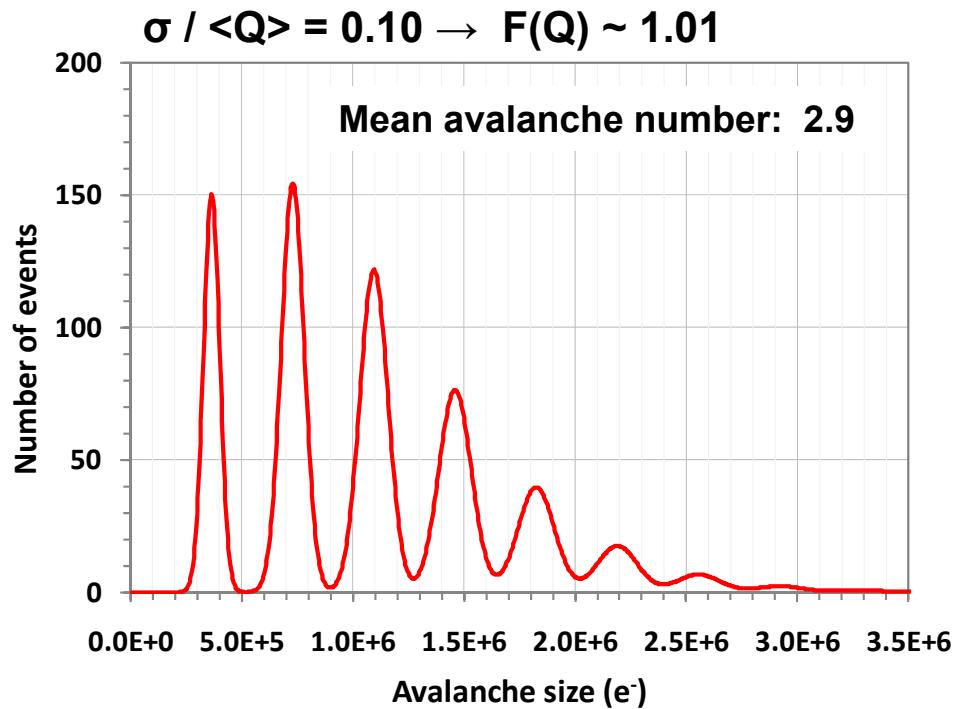
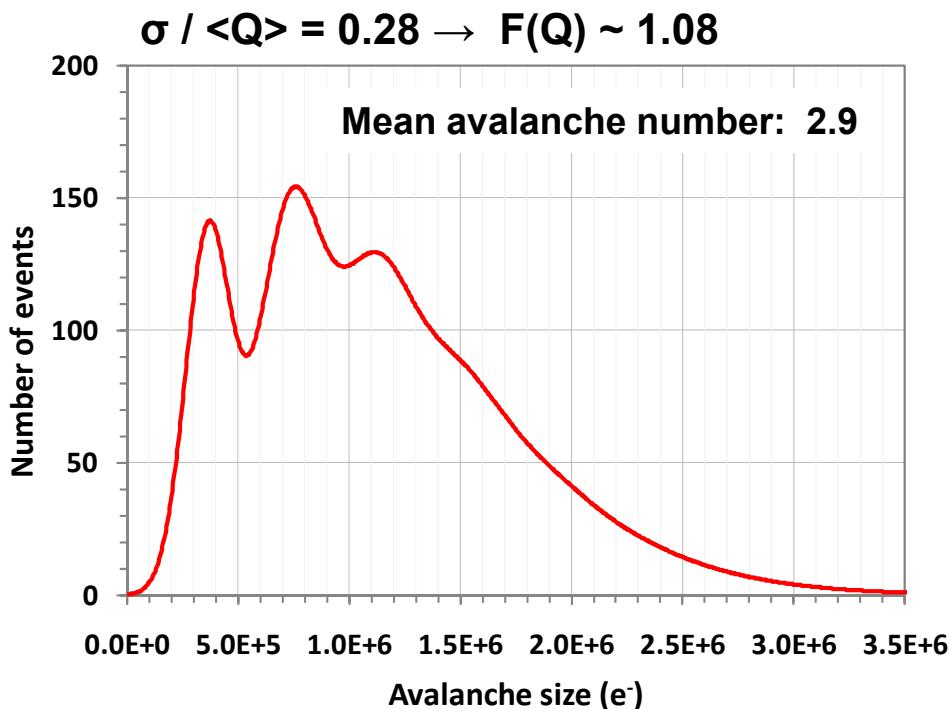
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“n”-avalanche
peaks spaced in
increments of
 $3.65 \times 10^5 e^-$

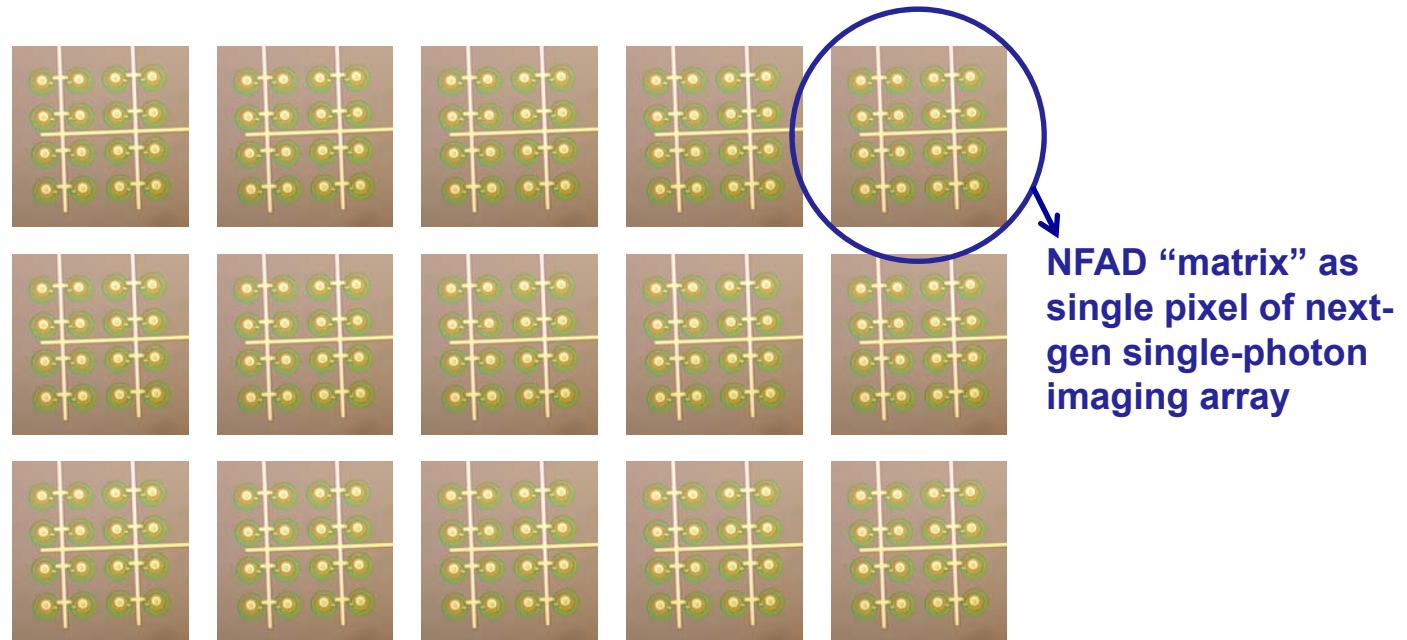
Achieving better photon number resolution

- Better photon number resolution will require more uniform avalanches
 - ◆ Fully resolved peaks between $n = 1$ and $n = 2$ requires $\sigma / \langle Q \rangle \sim 0.10$
- Need further tailoring of feedback and reduction of parasitics
 - ◆ Also work to improve device uniformity
- Also lots of work to do on fill factor



Potential for next-generation NFAD imager

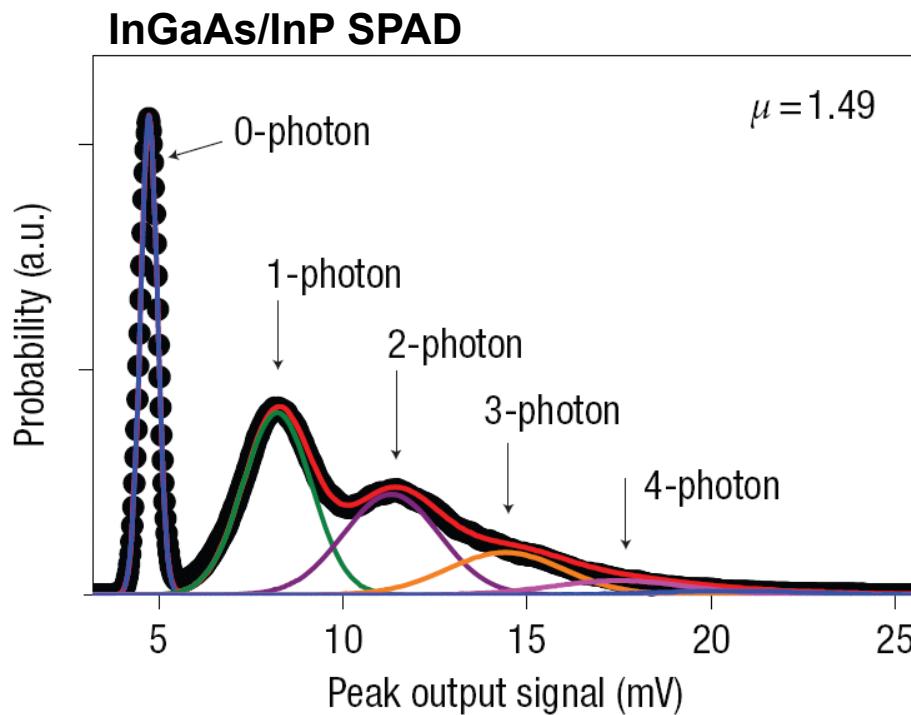
- **Next-gen single-photon imager with NFAD “matrix” at each pixel**
 - ◆ Provide pixel-level photon number resolution (PNR)
 - ◆ Degree of PNR determined by number of matrixed elements



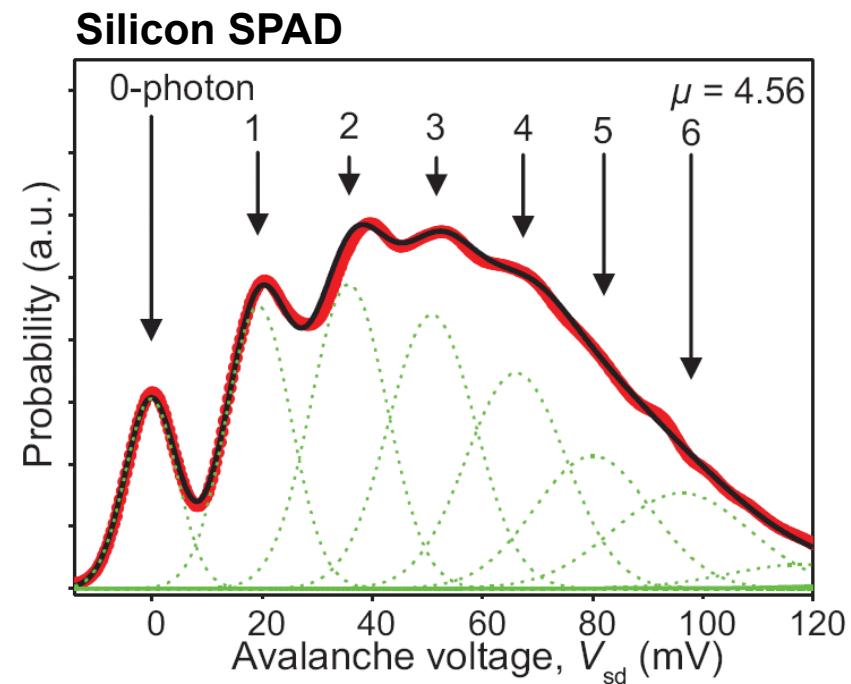
- **Also pursuing “active” NFADs with “two-state” feedback element**
 - ◆ High resistance for quenching, low resistance for re-charging

Photon number resolution with self-differencing

- **SPAD can have analog response with sensitivity to photon number**
 - Demonstrated with Toshiba self-differencing circuit
 - Histogram shape dictated by (i) Poisson distributed input, (ii) σ of charge flow per photon
- **Key is to restrict avalanche flow** (very short sub-ns gates in this case)



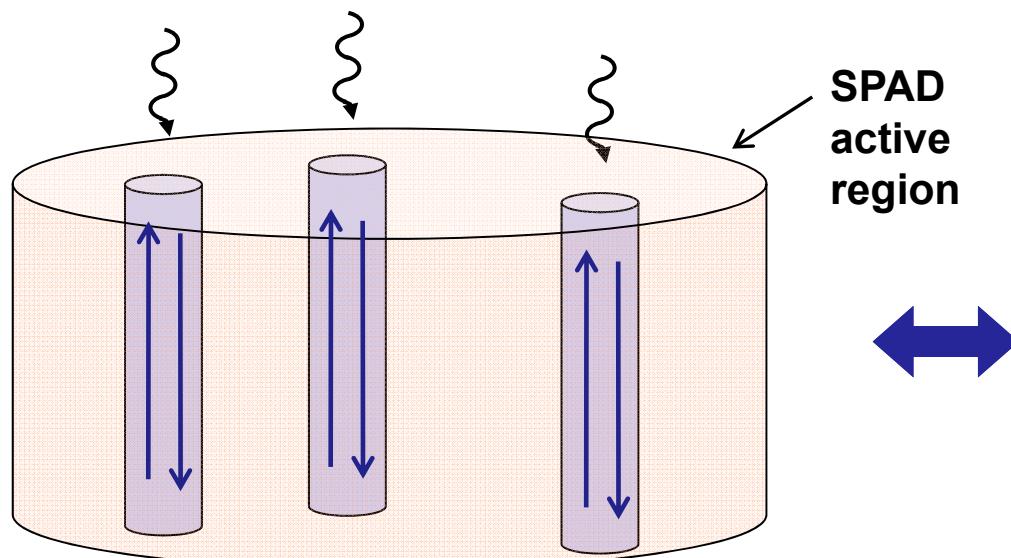
Kardynal, et al., *Nature Photonics*, 15 June 2008
doi:10.1038/nphoton.2008.101



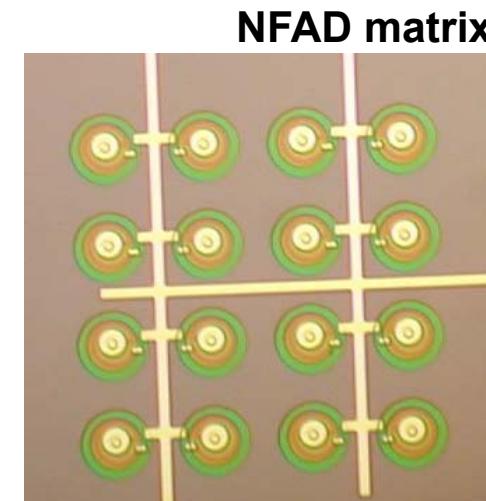
Single Photon Workshop 2011, 29 June 2011
Braunschweig, Germany

PNR through fabricated NFAD micro-pixellation

- PNR in discrete SPAD likely due to individual avalanche “filaments”
 - Sufficient filament uniformity with fast quenching before lateral spreading
- NFAD matrix provides similar “micropixellation” by fabrication
 - Sufficient avalanche uniformity from negative feedback
- Avalanche filament control converges on linear mode operation



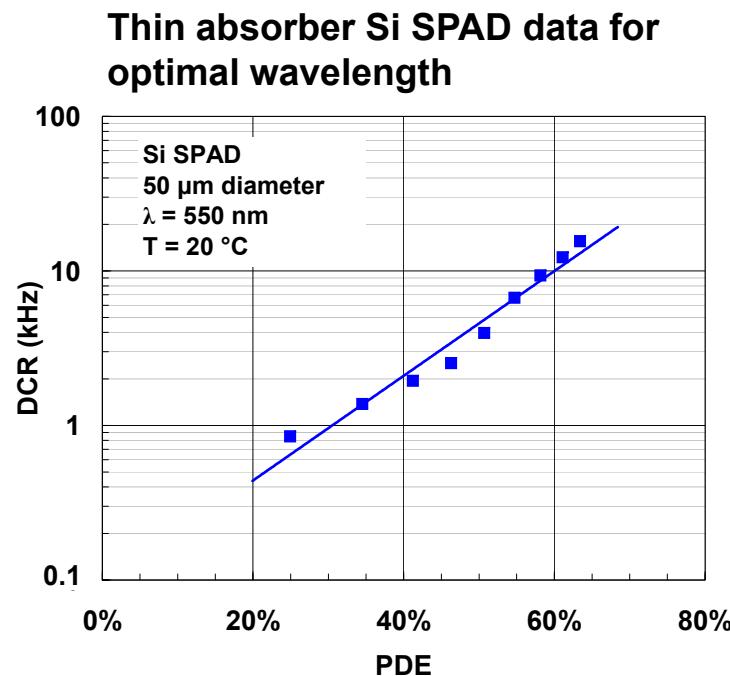
Distinct avalanche “filaments”
providing PNR is single SPAD



NFAD matrix can provide
“filaments” by design

Comparison of InGaAsP SPADs and Si SPADs

- **What can we project for InGaAsP SPADs based on more mature Si SPADs?**
- **Compare at different temperatures to compensate for difference in E_g**
 - ◆ Si outperforms InP by ~10X in DCR at same PDE
 - ◆ Best hold-off times for Si ~ 10 ns (1% afterpulsing, 20°C), ~10X better than InP at -60°C
 - Afterpulsing comparison is approximate due to strong circuit-dependence



Data from M. Ghioni and S. Cova, Politecnico di Milano

	Si	InGaAs/InP
Temperature	20 °C	-70 °C
Diameter	50 μm	
Wavelength	550 nm	1550 nm
DCR vs PDE	10 kHz at 60% 2 kHz at 40% 0.5 kHz at 20%	10 kHz at 40% 2 kHz at 20% 1 kHz at 10%
Min hold-off for 1% AP (free-run)	~ 10 ns	~ 100 ns
Jitter (FWHM)	30 – 50 ps	50 – 100 ps

Summary: What lies ahead for InGaAsP SPADs?

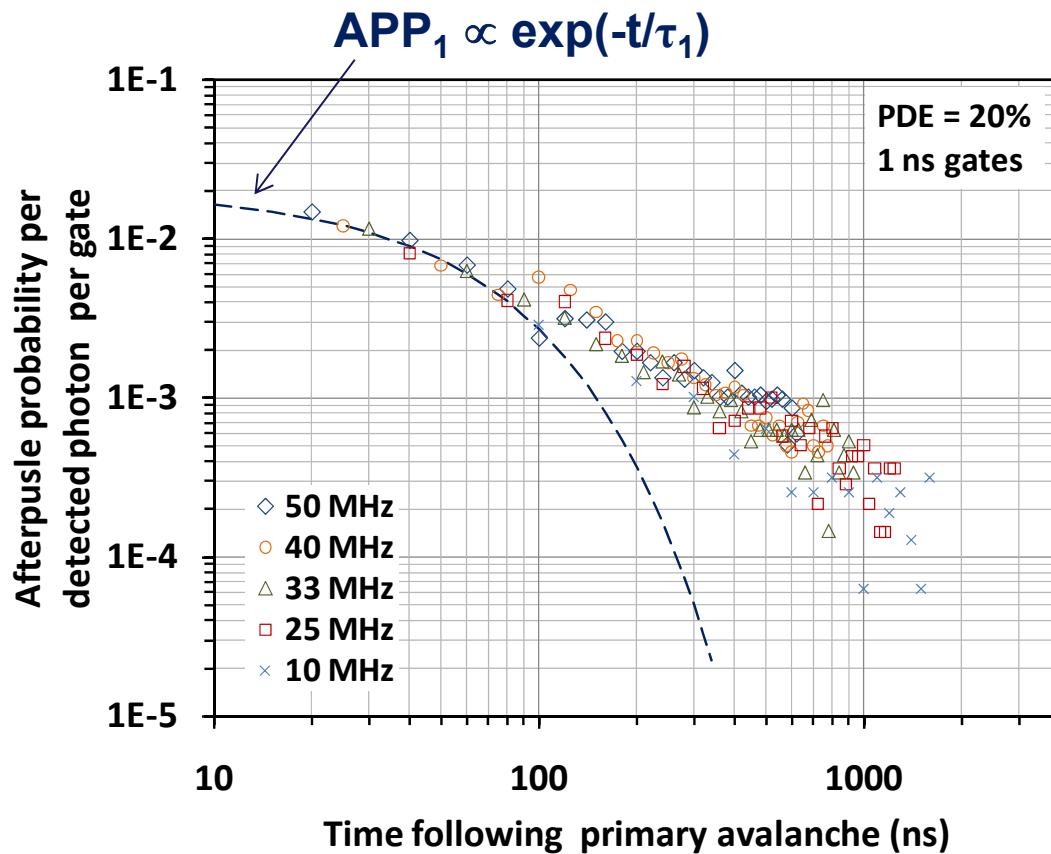


- **High-rate counting up to ~5 GHz for discrete detectors**
 - ◆ 0.5 GHz counting demonstrated with sub-ns periodic gating
 - ◆ Discrete detector counting limited to ~few GHz by fundamental APD dynamics
 - ◆ To reach even higher rates, use multiplexed solutions
- **Potential for analog behavior with SPADs/NFADs**
 - ◆ Photon number resolution (PNR) is feasible even in discrete SPADs
 - ◆ Micropixellation provides potential for more extensive PNR
 - ◆ Convergence of linear mode and Geiger-mode through negative feedback
- **Scaling to larger format arrays (e.g., Mpixel) is achievable**
 - ◆ Increased pixel count is challenging, but no fundamental limits
 - ◆ Further pitch reduction increasingly difficult due to single-photon crosstalk
- **Improvement in basic parameters requires materials advances**
 - ◆ DCR and afterpulsing directly related to material defect density
 - ◆ Higher PDE accessible if DCR and afterpulsing are tolerable at higher bias
- **Smart design concepts will progress faster than materials improvements**

BACK-UP SLIDES

Legacy approach to afterpulse fitting

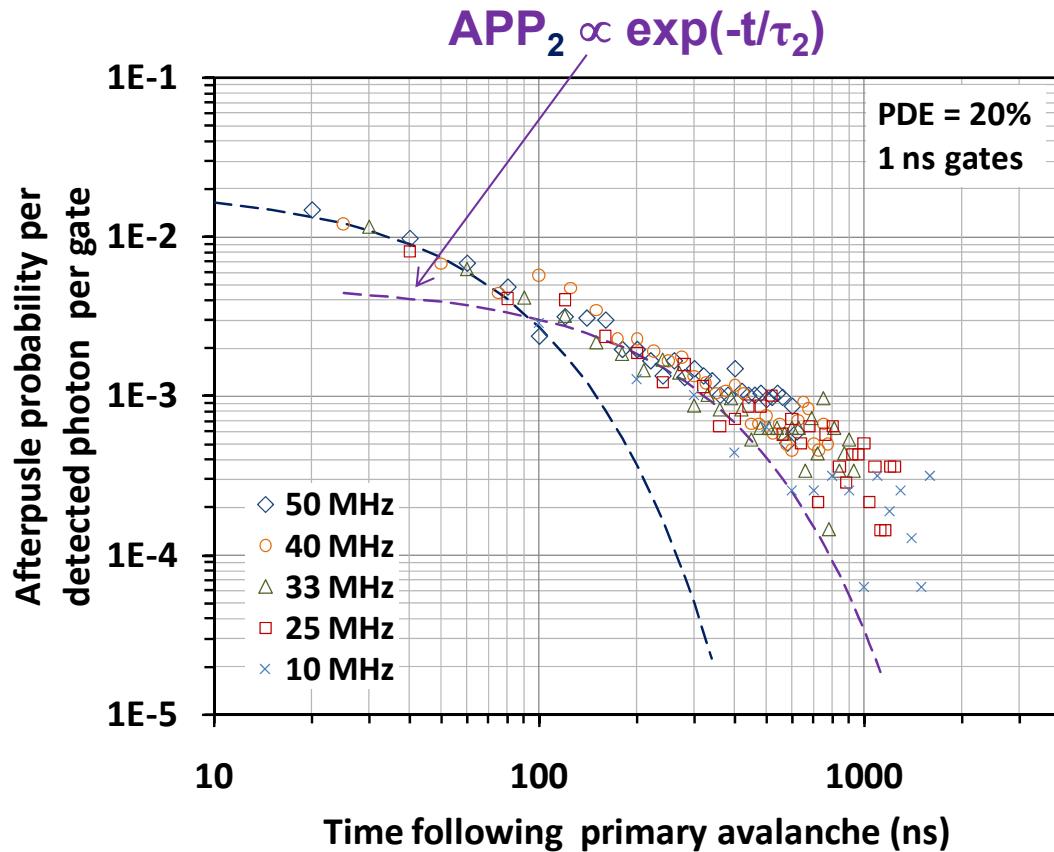
- Try to fit afterpulse probability (APP) data with exponential fit
 - ◆ Physically motivated by assumption of single dominant trap



Single exponential curve generally fits range of ~5X in time

Legacy approach to afterpulse fitting

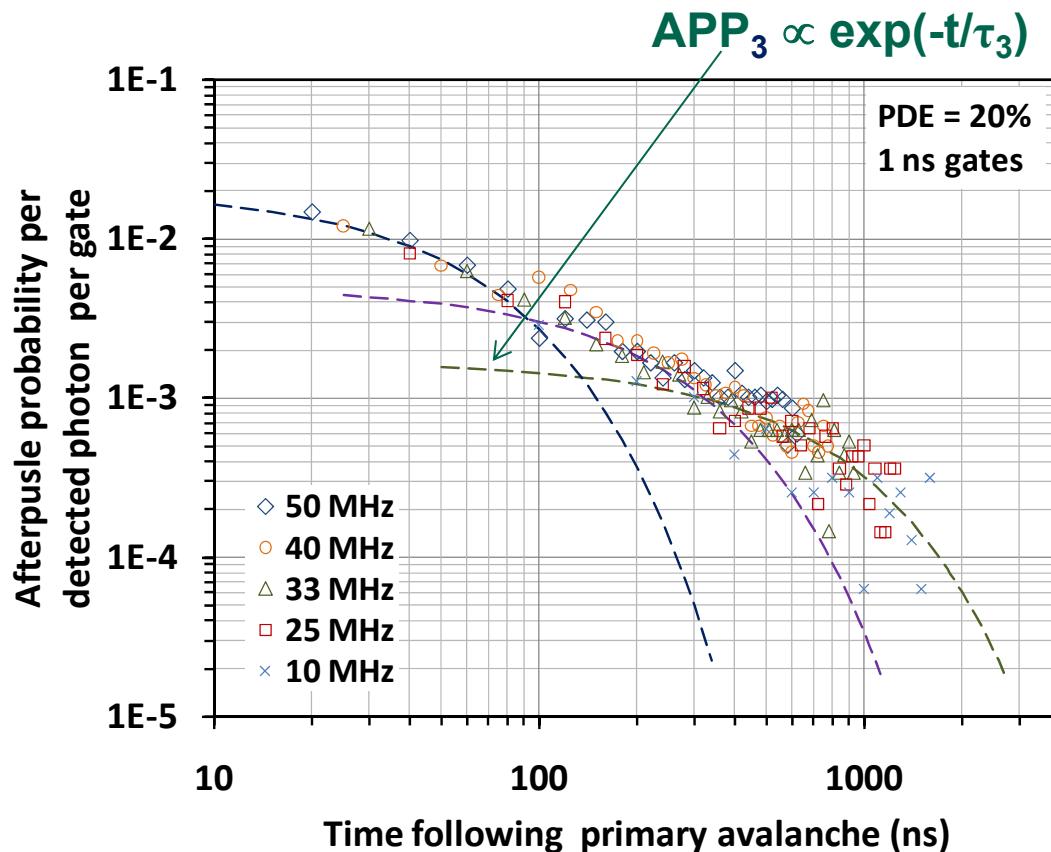
- Try to fit afterpulse probability (APP) data with exponentials
 - Physically motivated by assumption of single dominant trap
- Single exponential not sufficient; assume second trap



Single exponential curve generally fits range of ~5X in time

Legacy approach to afterpulse fitting

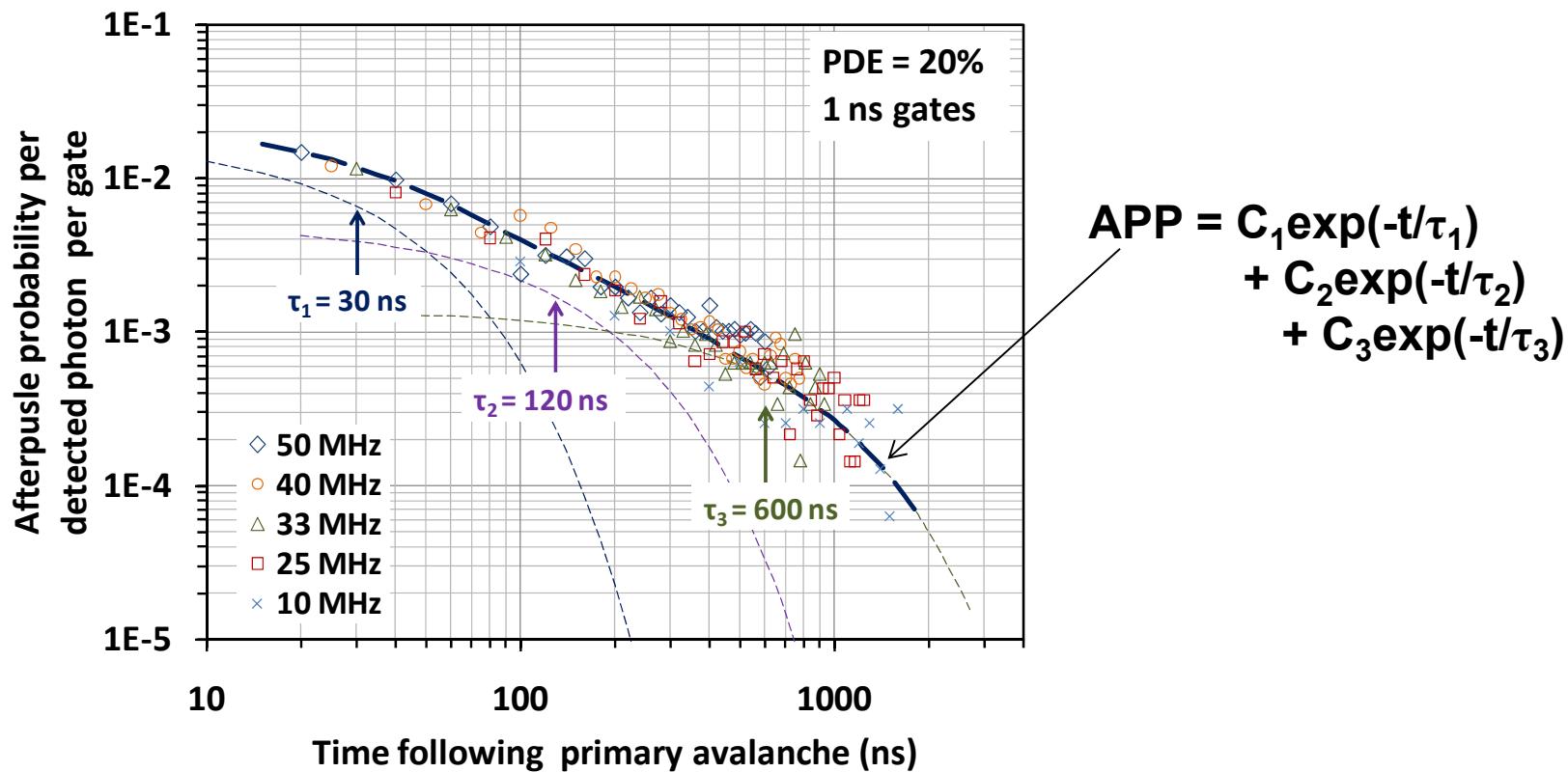
- Try to fit afterpulse probability (APP) data with exponentials
 - Physically motivated by assumption of single dominant trap
- Single exponential not sufficient; assume second trap
- Still need third exponential to fit full data set



Single exponential curve generally fits range of ~5X in time

Legacy approach to afterpulse fitting

- Can always achieve reasonable fit with several exponentials
- ...but choice of time constants is completely arbitrary!
→ depends on range of times used in data set
- Our assertion: No physical significance to time constants in fitting
→ simply minimum set of values to fit the data set in question



Modeling results for APP

- Develop model for APP with distribution of detrap rates $R \equiv 1/\tau$
 - APP related to change in trap occupation: $dN/dt \sim R \exp(-t R)$
 - Integrate over detrapping rate distribution $D(R)$
 $\rightarrow \text{APP} \sim \int dR D(R) R \exp(-t R)$
- APP behavior fit well by $T^{-\alpha}$ for 10 ns to 10 μ s

